

REVIEW

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Hydrosilanes. From laboratory curiosity to semiconductors

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Hydrosilanes represent a versatile class of silicon compounds that bridge fundamental main-group chemistry with technologically relevant materials science. Since the early discovery of monosilane in the nineteenth century, the chemistry of silicon hydrides has evolved from a laboratory curiosity into a cornerstone of modern semiconductor processing and silicon materials synthesis. This review provides a comprehensive overview of hydrosilane chemistry, focusing on three central aspects: (i) synthetic approaches to mono- and oligohydrosilanes, (ii) their functionalization through silanide intermediates and related transformations, and (iii) their application as molecular precursors for silicon-based materials and deposition technologies.

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Introduction

Hydrosilanes are a class of silicon-based compounds that have gained significant attention due to their unique chemical reactivity and broad applications in material science and nanotechnology. Although silicon chemistry shares some conceptual similarities with the more extensively explored realm of carbon chemistry, it boasts its own distinct characteristics and complexities. Unlike their carbon-based counterparts, hydrosilanes exhibit distinctive properties owing to the weaker Si–Si bonds and the polar nature of Si–H bonds. These properties

make hydrosilanes highly reactive and suitable for various applications, including silicon deposition, semiconductor processing, hydrogen storage, and the development of next-generation optoelectronic materials. Their role in forming advanced silicon-based nanostructures has also sparked interest in fields such as catalysis and biomedical research.

Recent advances in hydrosilane chemistry have focused on improving their synthetic accessibility, stability, and processability. Methods such as reductive coupling, dehydrogenative coupling, plasma synthesis, and chloride-induced disproportionation have been explored to optimize their production. Additionally, applications in printable electronics, thin-film solar cells, and silicon-based nanostructures have further driven research in this field. Several reviews and reference works have summarized aspects of hydrosilane chemistry over the past decades. Early comprehensive treatments can be found in clas-

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sical sources such as the *Gmelin Handbook of Inorganic Chemistry*, as well as survey articles and encyclopedia entries published during the 1980s and 1990s.^{1,2} These works primarily focused on the fundamental properties, preparation, and industrial relevance of simple silanes. Later contributions,³ including chapters in *Comprehensive Inorganic Chemistry II*,⁴ expanded on these topics but remained largely centered on established synthetic methodologies and basic silicon hydride chemistry.

More recently, a review by Gerwig, Böhme, and Friebe has revisited the field with emphasis on hydrosilanes; however, this work mainly addresses hydrosilanes themselves and does not cover the broader chemistry of higher hydrosilanes, their functionalization, and their emerging roles as precursors for modern deposition technologies.⁵ Therefore, despite the availability of these valuable contributions, a comprehensive and updated overview connecting classical hydrosilane chemistry with recent developments in functionalization and materials applications remains highly desirable.

Consequently, this review summarizes the broad field of hydrosilanes in terms of their synthesis (i), their functionalization (ii) and, if investigated, their applicability with respect to several deposition techniques (iii).

This review does not deal with hydrosilanes, which have only one hydride R_3SiH (e.g.: $(Me_3Si)_3SiH$, Ph_3SiH , or $HPh_2SiSiPh_2H$ etc.), as in these cases the organic substituents largely dominate the chemical reactivity. Furthermore, molecular species of the type R_2SiH_2 (e.g.: $(Me_3Si)_2SiH_2$, Ph_2SiH_2 , or Et_2SiH_2 etc.) are likewise excluded for the same reason. However, R_2SiH_2 units within higher silicon hydrides and Si–Si bonded systems are implicitly included in this review. For reviews about hydrosilylation the reader is referred to two very recent publications.⁶ For a summary of inorganic tetrylenes the reader is referred to the excellent review of Rivard.⁷

Historical development

The classical approach is the reaction of silicides with diluted acids. The pioneers in this field were F. Wöhler and H. Buff,

who synthesized SiH_4 by the reaction of diluted acids with aluminium silicides.⁸ In 1902, H. Moissan and S. Smiles identified Si_2H_6 as another product formed by this reaction.⁹ Between 1919 and 1921 A. Stock and K. Somieski pioneered the field of organosilanes and aminosilanes with the synthesis of methylsilane¹⁰ and aminosilanes with trisilylamine.¹¹ In the following years they showed that also higher homologs of the series Si_nH_{2n+2} were formed.¹⁰ G. Fritz was able to obtain the first silylphosphane in 1953 by pyrolysis of PH_3 and SiH_4 ¹² and in 1955 B. J. Aylett, H. J. Emeléus and A. G. Maddock were able to obtain evidence of the existence of trisilylphosphane.¹³ The next milestone in the synthesis of hydrosilanes was achieved by F. Fehér and co-workers, who used the same methodology and implemented procedures for a targeted isolation up to Si_8H_{18} on a preparative scale. His scientific life is excellently portrayed in M. Baudler's reminiscence.¹⁴ M. A. Ring and D. M. Ritter were the first to report the synthesis of silyl potassium $KSiH_3$.¹⁵ E. Amberger and H. Boeters were the first to isolate and report the properties of trisilylphosphane in 1962.¹⁶

A change in the paradigm was the targeted synthesis of the first cyclic hydrosilane derivatives by E. Hengge and co-workers in 1973.¹⁷

In 1993 W. Sundermeyer reported the synthesis of branched silylgermanes, demonstrating the structural diversity accessible in mixed silicon–germanium hydride systems.¹⁸

13 years later T. Shimoda and co-workers demonstrated that these higher silanes have an application as precursors for liquid phase deposition (LPD).¹⁹ This landmark development resulted in a boom of this chemistry with many groups in academia and industry working on the implementation of solution-based deposition in several industrial processes. In 2015, M. Wagner and co-workers reported the synthesis of silafullerenes, expanding the structural landscape of silicon-based cluster chemistry.²⁰

In 2017 H. Stueger and co-workers published the synthesis of 2,2,3,3,4,4-hexasilylpentasilane, which is to date the highest isolated hydrosilane on preparative scale.²¹ Recently our group pioneered the use of functionalized hydrosilanes as precursors for LPD.²² In summary this can be seen as a showcase example of an ideal workflow in science. Starting from the very funda-



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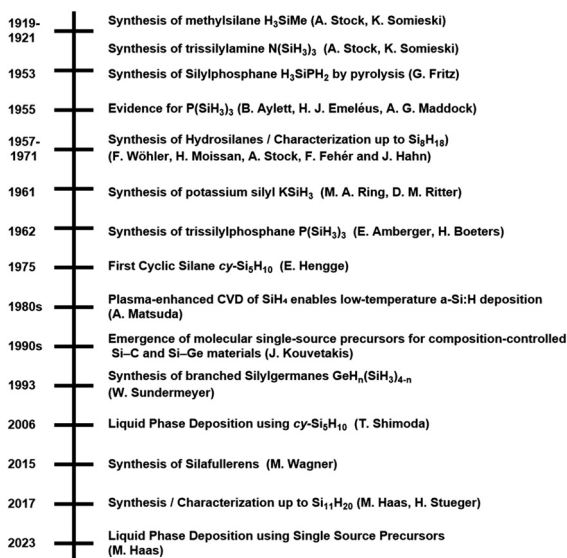


Fig. 1 Historical development.

mental studies to the several applications. In Fig. 1 the historical development of this research topic is summarized.

Silane synthesis

Hydrolysis of silicides

The hydrolytic decomposition of silicides with aqueous acids was first observed by Wöhler and Buff in 1857, marking the first documented formation of a silicon- and hydrogen-containing compound.⁸ Subsequently, in 1902, Moissan and Smiles were the first to characterize SiH₄ along with higher hydrosilanes following the decomposition of magnesium silicide with aqueous HCl.⁹ This discovery laid the foundation for the use of silicide hydrolysis as a commonly applied method for silane synthesis. The reaction produces monosilane (SiH₄)



Michael Haas

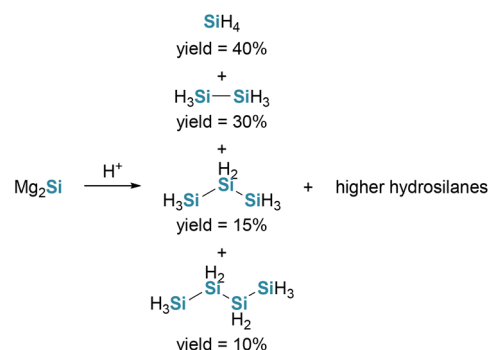
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alongside disilane (Si₂H₆) and minor amounts of higher hydrosilanes. The yield and product distribution are highly dependent on factors like purity of Mg₂Si, the solvent and acid used, and overall reaction conditions. Stock implemented extensive studies on this topic and successfully isolated and characterized higher silanes, including tetrasilane (Si₄H₁₀), pentasilane (Si₅H₁₂) and hexasilane (Si₆H₁₄) (see Scheme 1). The application of preparative gas chromatography further enabled the separation and identification of both linear and branches silanes up to octasilane (Si₈H₁₈).^{23–25} Fehér expanded upon these studies by investigating the hydrolysis of Mg₂Si using sulfuric and phosphoric acid, leading to the formation and identification of silanes up to pentadecasilane (Si₁₅H₃₂). Moreover, distinct linear silanes up to heptasilane (Si₇H₁₆), as well as branched species such as 2-silyltrisilane, 2-silyltetrasilane and 2-silylpentasilane, were isolated and characterized.²⁶

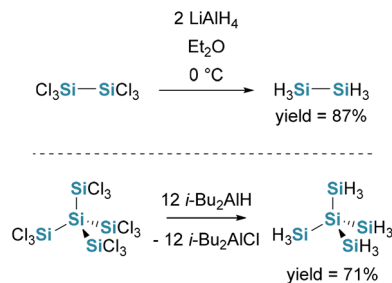
Johnson reported that using ammonium bromide (NH₄Br) in liquid ammonia instead of aqueous HCl increased silane yields to 80–90%.²⁷

Hydrogenation of chlorosilanes

The hydrogenation of chlorosilanes with mild reducing agents such as lithium aluminium hydride (LiAlH₄) or diisobutylaluminium hydride (i-Bu₂AlH) is a well-established method for synthesizing hydrosilanes on a laboratory scale (see Scheme 2). However, this approach is limited by the availability of chlorosilane precursors and side reactions involving Si–Si bond cleavage (especially LiAlH₄ results in the cleavage of silyl groups).



Scheme 1 Synthesis of monosilane and oligohydrosilanes with product distribution according to the work of Stock et al.



Scheme 2 Formation of oligohydrosilanes via the hydrogenation of chlorosilanes.



Finholt *et al.* first reported this reaction in 1947, demonstrating the formation of disilane (Si_2H_6) *via* the reduction of hexachlorosilane (Si_2Cl_6) with LiAlH_4 (see Scheme 2). The yield of hydrosilanes varies significantly depending to reaction conditions and chlorosilane employed.²⁸ In 1973, Höfler reported the formation of neopentasilane, short NPS, (*neo*- Si_5H_{12}) *via* the hydrogenation of dodecachloroneopentasilane (*neo*- $\text{Si}_5\text{Cl}_{12}$) with LiAlH_4 , though low yields were observed due to Si–Si bond cleavage. The use of *i*- Bu_2AlH instead of LiAlH_4 improved selectivity and increased product yields.²⁹

The Litz–Ring process (see Scheme 3), while primarily employed for the reduction of tetrachlorosilane (SiCl_4) to monosilane using alkali metal hydrides regenerated *in situ* by molten-salt electrolysis, has also been investigated for related hydride-mediated silicon transformations. The process enables continuous, high-yield production of ultra-pure monosilane and was demonstrated at pilot scale with strong industrial relevance for low-cost, high-purity silicon production for semiconductors.³⁰

Hengge *et al.* reported the synthesis of the cyclic hydrosilanes, cyclopentasilane (*cy*- Si_5H_{10}) and cyclohexasilane (*cy*- Si_6H_{12}) *via* the hydrogenation of their respective cyclic chlorosilanes using LiAlH_4 , achieving excellent yields (see Scheme 4).³¹

In 2013, Kroke and co-workers reported the successful crystallization of cyclopentasilane, enabling its structural characterization by X-ray diffraction (see Fig. 2).³²

An alternative approach involves the reduction of $[\text{Si}_6\text{Cl}_{14}]^{2-}$ complexes, which are generated from HSiCl_3 through a redistribution reaction, facilitated by alkylated amines such as tetraethylenediamine (TEEDA) or pentaethyldiethylenetriamine (PEDETA) and the presence of a base like ethyldiisopropylamine (EDIPA). The resulting hexacoordinate species can then be hydrogenated with LiAlH_4 , yielding *cy*- Si_6H_{12} (see Scheme 5).³³ Wagner and co-workers have further explored the rich amine-mediated chemistry of chlorosilanes and related

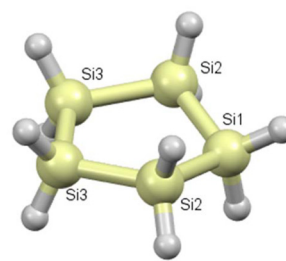
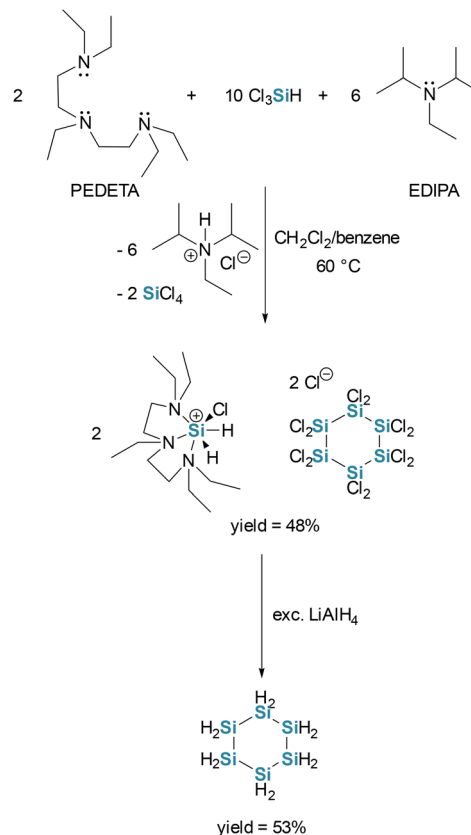
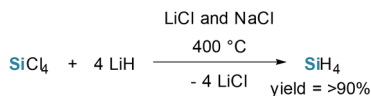


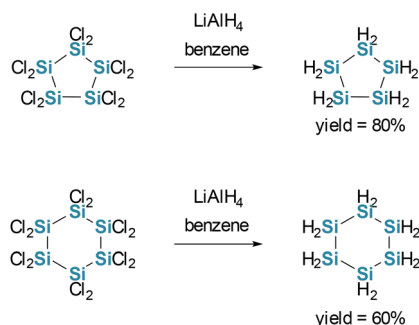
Fig. 2 Crystal structure of Si_5H_{10} adapted from original literature by Kroke and co-workers.



Scheme 5 Synthesis of cyclohexasilane *via* the reduction of the $[\text{Si}_6\text{Cl}_{14}]^{2-}$ complexes.



Scheme 3 Simplified Litz–Ring process.

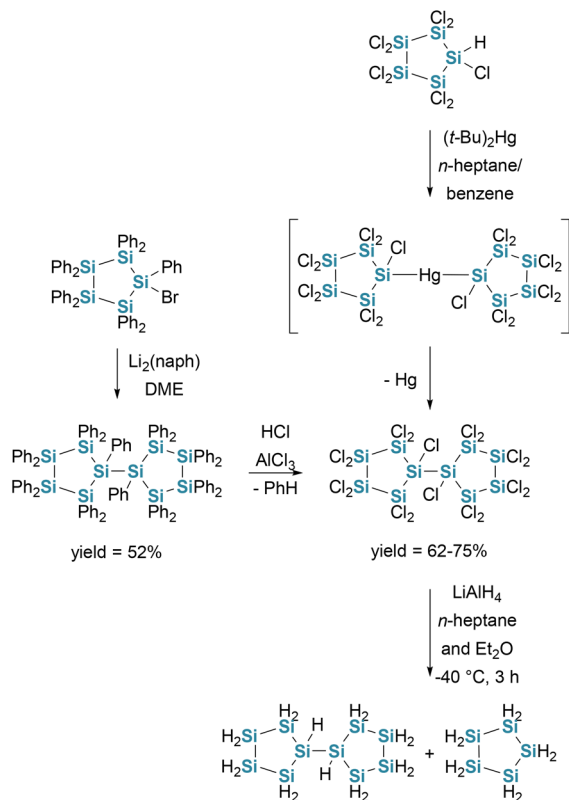


Scheme 4 Hydrogenation of cyclic chlorosilanes.

silicon cluster species; a comprehensive overview of this chemistry can be found in their review.³⁴

The first synthesis of an unsubstituted bicyclic halosilane, bi(cyclopentasilanyl), was reported by Stueger, Lassacher and Hengge in 1995.³⁵ The key intermediate bis(nonachlorocyclopentasilanyl) is obtained either by Hg-mediated coupling of nonachlorocyclopentasilane using (*t*- Bu) $_2\text{Hg}$ in *n*-heptane or by catalytic phenyl abstraction from the perphenylated bicyclic compound with HCl/AlCl_3 , both routes affording $\text{Si}_{10}\text{Cl}_{18}$ in good yields. Subsequent hydride reduction with LiAlH_4 at -40 °C selectively converts the Si–Cl functionalities into Si–H bonds, yielding the unsubstituted bicyclic $\text{Si}_{10}\text{H}_{18}$ (see



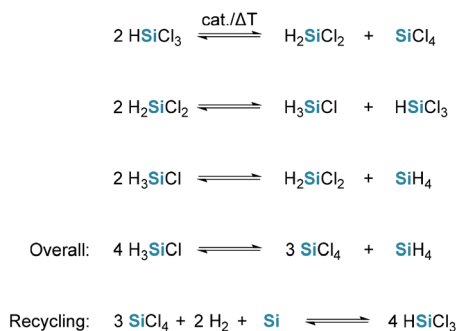


Scheme 6 Synthesis of bicyclic hydrosilane. Yields of the final product not reported since it could not be separated from the side-product (cyclopentasilane, $\text{cy-Si}_5\text{H}_{10}$).

Scheme 6). This reduction is accompanied by the partial cleavage of the central Si–Si bond, leading to approximately 15% cyclopentasilane ($\text{cy-Si}_5\text{H}_{10}$) as a side product.

Disproportionation of chlorosilanes

The disproportionation is the main large-scale method used nowadays for the production of monosilane (SiH_4). Trichlorosilane (HSiCl_3) undergoes disproportionation in the presence of a catalyst (e.g. AlCl_3 , ZnCl_2 , BCl_3 , FeCl_3). The reaction leads to the formation of SiH_4 in high purity alongside SiCl_4 . The process is continuous and operates in a closed-loop system, allowing recycling of SiCl_4 (see Scheme 7).³⁶



Direct synthesis of Si and H₂

It is also possible to synthesize monosilane and also higher hydrosilanes from silicon powder and hydrogen in the presence of catalytic amounts of H_2S or various sulfides (see Scheme 8). The product distribution is controlled by the H_2 pressure. However, this method requires high temperatures and pressures, making it less practical compared to other methodologies.³⁷

Catalytic dehydrogenative coupling

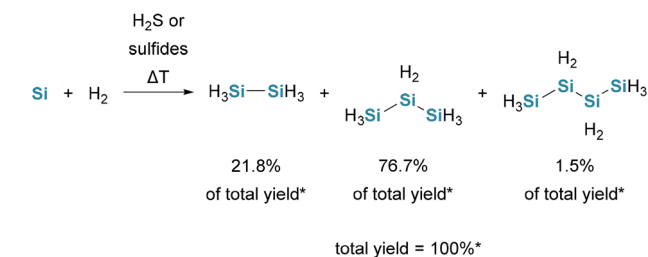
The formation of Si–Si bonds from monosilane (SiH_4) can be achieved through dehydrogenative coupling reactions, in which primary and secondary organomonosilanes undergo hydrogen abstraction in the presence of a catalyst (see Scheme 9). Such reactions typically require transition metal complexes from group 4 to 10 which work as catalysts.³⁸

Harrod was the first to report the catalytic formation of higher hydrosilanes from SiH_4 in 1988.³⁹ Building on this work, Okumura *et al.* demonstrated the synthesis of disilane (Si_2H_6) and trisilane (Si_3H_8) via catalytic condensation of SiH_4 using platinum, rhodium and ruthenium-based complexes.⁴⁰ Moreover, *n*-tetrasilane was afforded via catalytic conversion of SiH_4 , Si_2H_6 and Si_3H_8 .⁴¹ However, a significant challenge associated with these approaches is the concurrent formation of insoluble polymeric byproducts, which can negatively impact selectivity and complicate product isolation.

Wurtz-type coupling

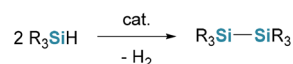
A Wurtz-type approach to hydrosilane synthesis was introduced by Craig *et al.* in 1962, involving the reaction of iodosi-lane (H_3SiI) with a liquid sodium/mercury amalgam at room temperature (see Scheme 10).⁴²

This method resulted in the formation of disilane with a reported yield of 67%.⁴² However, the broader application of this method remains limited, as alkali metals tend to also react with Si–H bonds.



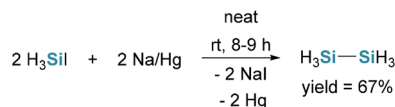
Scheme 7 Large-scale production of SiH_4 .

Scheme 8 Reaction of Si-powder and hydrogen at high temperatures. *Product distribution and total yield when CuS is used as the catalyst.



Scheme 9 Schematic equation for dehydrogenative coupling of silanes.





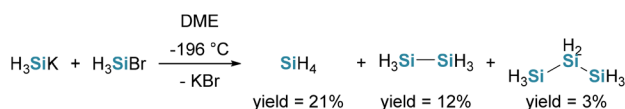
Scheme 10 Synthesis of disilane (Si_2H_6) via Wurtz-type coupling.

An alternative route to higher hydrosilanes involves the nucleophilic substitution of halosilanes with silanide anions at low temperatures (see Scheme 11).^{43,44} A detailed discussion on the synthesis of silanides follows in Functionalization with group 1 (synthesis of silanides).

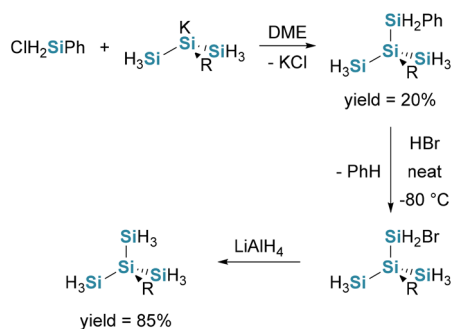
This method not only enables the formation of linear oligomers but also the synthesis of branched silanes, such as neopentasilane (*neo*- Si_5H_{12}) and neohexasilane ($\text{Si}(\text{SiH}_3)_3(\text{Si}_2\text{H}_5)$) (see Scheme 12). These branched species can be obtained through the reaction of phenylchlorosilane with a mixture of different potassiumsilanides ($\text{KSiH}(\text{SiH}_3)_2$, $\text{KSi}(\text{SiH}_3)_3$ and $\text{KSi}(\text{SiH}_3)_2(\text{Si}_2\text{H}_5)$) followed by sequential bromination and reduction of the resulting phenyl-substituted oligosilanes using HBr and LiAlH_4 , respectively. Nevertheless, the separation and isolation of the individual products was not reported.⁴⁵

Building on Fehér's work on silanide synthesis (see Functionalization with group 1 (synthesis of silanides)), Sundermeyer and co-workers investigated the protonation of higher silanides ($\text{KSi}_n\text{H}_{2n+1}$) with phenylsulfonic acid (PhSO_3H) resulting in a mixture of various branched hydrosilanes with the general formula ($\text{SiH}_{4-n}(\text{SiH}_3)_n$).^{46,47}

However, they noted that a selective synthesis of higher silanides could not be achieved under the investigated conditions,



Scheme 11 Formation of mono-, di-, and trisilane via Wurtz-type coupling.



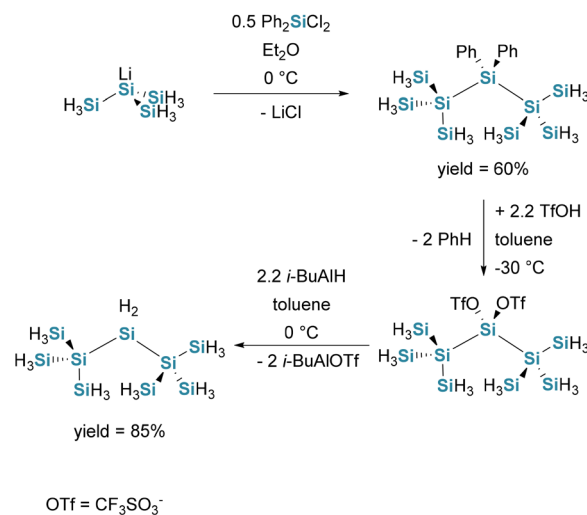
Scheme 12 Formation of branched silanes in a 3-step synthesis.

consequently the reactions were leading to mixtures or less well-defined products.

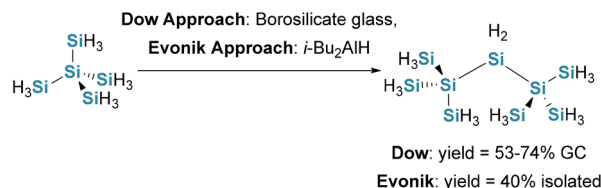
Stueger *et al.* demonstrated that $\text{LiSi}(\text{SiH}_3)_3$ (prepared from isolated neopentasilane) reacts selectively with SiCl_2Ph_2 to form the branched nonasilane ($\text{SiH}_3)_3\text{SiSiPh}_2\text{Si}(\text{SiH}_3)_3$. Subsequent dephenylation using triflic acid, followed by hydrogenation with *i*- Bu_2AlH , resulted in the formation of 2,2,4,4-tetrasilylpentasilane in good overall yield (see Scheme 13).^{48,49}

In addition, an alternative synthesis of 2,2,4,4-tetrasilylpentasilane was achieved independently by two groups. While Dow Corning employed borosilicate glass surfaces to promote the conversion of neopentasilane,⁵⁰ the groups led by Stueger and Haas, as well as Evonik, demonstrated that 2,2,4,4-tetrasilylpentasilane also forms in the presence of a Lewis acid (see Scheme 14).⁵¹

In addition, Haas *et al.* turned to an alternative method inspired by earlier work of Gilman and Harrell.⁵² In this approach, 0.5 equiv. of dibromoethane ($\text{BrCH}_2\text{CH}_2\text{Br}$) were added to $\text{LiSi}(\text{SiH}_3)_3$ at -80 °C, leading the formation of 2,2,3,3-tetrasilyltetrasilane (a branched octasilane) shown in Scheme 15 accompanied by minor amounts of 2,2,3,3,4,4-hexasilylpentasilane (a branched undecasilane). This reaction is driven by an initial halogen-metal exchange, forming $\text{BrSi}(\text{SiH}_3)_3$ as key intermediate.²¹

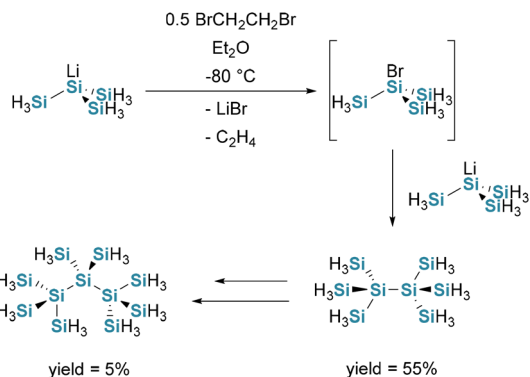


Scheme 13 Synthesis of $(\text{SiH}_3)_3\text{SiSiPh}_2\text{Si}(\text{SiH}_3)_3$ and subsequent treatment with TfOH and *i*- BuAlH .



Scheme 14 Alternative synthesis of 2,2,4,4-tetrasilylpentasilane.





Scheme 15 Synthesis of branched octasilane with minor amounts of branched undecasilane.

Moreover, Stueger and co-workers successfully obtained crystals of the branched undecasilane appropriate for X-ray diffractometry (see Fig. 3).²¹

Impact of energy on SiH₄

An alternative route to higher hydrosilanes involves energy-induced transformation of monosilane, such as by pyrolysis, photolysis, or electrical discharge (see Scheme 16). These approaches rely on the homolytic cleavage of Si–H and Si–Si bonds, promoting the stepwise build-up of longer-chained silanes.

The most straightforward method employs thermal energy. As early as 1950, Fritz demonstrated that disilane could be synthesized through the pyrolysis of monosilane. Continued pyrolysis of disilane leads to the formation of trisilane, while further thermal treatment of trisilane results in the generation of tetrasilane, indicating that this process enables chain elongation through successive decomposition and recombination steps.^{53,54}

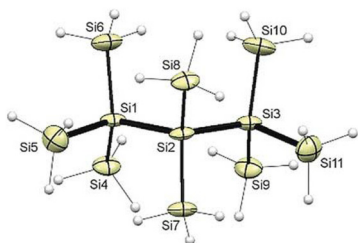
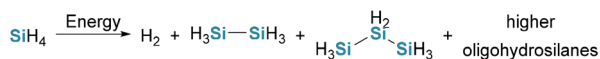


Fig. 3 Crystal structure from 2,2,3,3,4,4-hexasilylpentasilane (a branched undecasilane). Reproduced from Haas *et al.*²¹ with permission from Angewandte Chemie International Edition, © 2017.



Scheme 16 Impact of energy on SiH₄. Total yield and product distribution depends on the energy source and reaction conditions.

In addition to thermal activation, monosilane can also be exposed to silent electrical discharge within an ozonizer. This method yields a mixture of disilane, trisilane, and smaller amounts of higher homologues.^{2,55} A further photochemical approach involves the irradiation of SiH₄ with ultraviolet light. When mercury is employed as a photosensitizer, a distribution of di-, tri-, and higher silanes can be generated.⁵⁶

Silafullerenes

A major conceptual advance in silicon hydride chemistry was achieved with the realization of silafullerenes, more precisely endohedral silafullerenes (see Fig. 4), by Wagner and co-workers in 2015–2021.^{20,57} Building on earlier theoretical predictions that halide ions could template silicon cages, they reported the synthesis of the dodecahedral silicon cluster [Cl@Si₂₀H₂₀][−], the silicon analogue of the smallest fullerene C₂₀H₂₀ (see Scheme 17).

The synthesis proceeds *via* controlled stepwise reduction of perchlorinated precursor, ultimately converting all exohedral Si–Cl bonds into Si–H functionalities while preserving an encapsulated chloride ion at the centre of the cage. Although formally ionic compounds and therefore isolated as a salt with a counter-cation, the cluster is structurally and chemically dominated by twenty-terminal Si–H bonds. As such, these silafullerenes represent a unique class of molecular hydrosilanes, bridging classical neutral hydrosilanes and anionic silicon clusters, and they offer a hydrogen-terminated silicon surface that is amenable to further functionalization while being stabilized by the endohedral Cl[−] template.

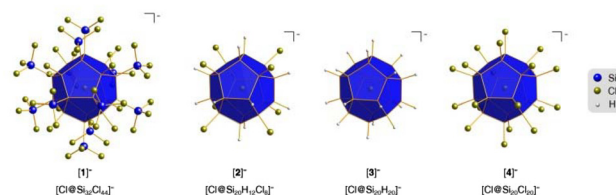
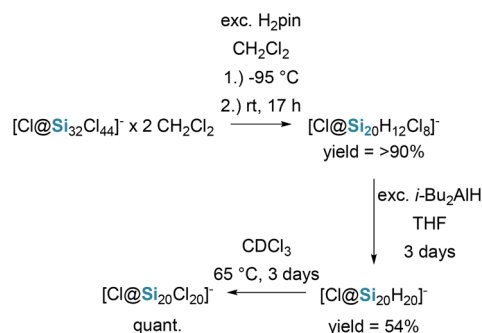


Fig. 4 Crystal structures from silafullerenes by Wagner *et al.* Reproduced from ref. 57 with permission from Journal of American Chemical Society, © 2021.



Scheme 17 Formation of silafullerenes by Wagner *et al.*



Silane derivatization

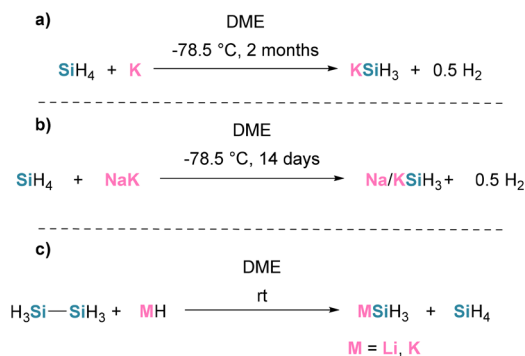
Functionalization with group 1 (synthesis of silanides). In recent years, alkali silanides MSiH_3 ($\text{M} = \text{Li}, \text{Na}, \text{K}, \text{Rb}, \text{Cs}$) have emerged as promising complex hydrides for solid-state hydrogen storage, showing reversible hydrogenation/dehydrogenation with their parent MSi phases and practical capacities near ambient conditions.⁵⁸ Recent studies have demonstrated favourable thermodynamics that enable hydrogen uptake and release under moderate operating windows, and catalytic approaches have further improved kinetics while maintaining reversibility.⁵⁹ Collectively, these advances position MSiH_3 as viable candidates that have been actively tested and refined for practical hydrogen storage applications.⁶⁰

Furthermore, alkali metal silanides with the general formula MSi_xH_y ($\text{M} = \text{Li}, \text{Na}, \text{K}, \text{Rb}, \text{Cs}$) serve as versatile precursors for subsequent functionalization, enabling the incorporation of diverse heteroatoms while preserving the Si-H functionality. The scope and methodology of these transformations are discussed in detail in this review.

In 1961, Ring and Ritter reported the formation of potassium silanide (KSiH_3) by reducing monosilane with potassium metal in DME. Reaching 75–100% consumption of silane required about two months (see Scheme 18, path a). A Na/K alloy greatly accelerated the process, achieving 92% SiH_4 consumption in 14 days (see Scheme 18, path b). They also showed that KH reacts with disilane to give quantitative conversion within one day, whereas lithium hydride (LiH) affords only 12% conversion after 48 hours (see Scheme 18, path c). Although isolated yields were not determined directly, subsequent reactions of KSiH_3 proceeded in essentially quantitative yield.¹⁵

Hagenmuller and Pouchard prepared sodium silanide (NaSiH_3) by introducing SiH_4 into a finely dispersed suspension of Na in DME. Under these conditions, both reactants partially (approx. 20%) dissolve within 6 hours in equimolar proportions, affording a yellowish solution. However, the resulting NaSiH_3 solution is unstable and undergoes decomposition under the synthesis conditions.⁶¹

In 1966 Kennedy *et al.* reported a significant improvement in the production of potassium silanide by reacting disilane



Scheme 18 Synthesis of MSiH_3 via reduction (path a–c). No yields were reported.

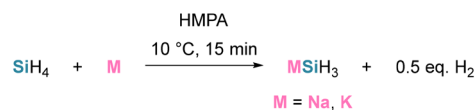
with potassium sand at -78°C , achieving complete conversion to KSiH_3 within 24–48 h.⁴³

Subsequent studies by Amberger and Römer demonstrated that using a K/Na alloy (5 : 1 w/w) in DME or diglyme affords full conversion to KSiH_3 at room temperature within 3 days. In contrast, THF and 2,2-dimethyl-1,3-dioxolane give slower reactions. While triglyme accelerates the conversion further, the resulting KSiH_3 solutions are less stable than those obtained in DME or diglyme. Notably, the addition of diethyl ether (Et_2O) to solutions of KSiH_3 induces precipitation of a white, crystalline solid that retains its reactivity under N_2 or vacuum and can be fully redissolved thereafter.⁶²

Cradock, Gibbon, and van Dyke later showed that hexamethylphosphoramide (HMPA) enables complete conversion to NaSiH_3 and KSiH_3 at 10°C within just 15 minutes. However, isolation of the free silanides from HMPA proved unsuccessful due to the high boiling point of the solvent and the high solubility of the products, which prevented precipitation upon addition of nonpolar solvents (see Scheme 19).⁶³

Amberger, Römer, and Layer undertook a detailed study of alkali-metal reactivity in DME and diglyme, establishing a clear increase in rate down group 1 ($\text{Na} < \text{K} < \text{Rb} < \text{Cs}$). Relative to sodium, caesium reduced the time required to reach full conversion by up to 92%. Under otherwise comparable conditions, diglyme generally afforded faster conversions than DME (see Scheme 20, path a and b). Mixed-metal systems offered additional benefits: an Rb/Na alloy shortened reaction times relative to rubidium alone (see Scheme 20, path c). By contrast, an Na/Hg amalgam was distinctly sluggish, reaching only 17% conversion after 23 days (see Scheme 20, path d). Isolation of discrete MSiH_3 ($\text{M} = \text{Na}, \text{K}, \text{Rb}, \text{Cs}$) was not attempted; instead, the reactive solutions were directly subjected to subsequent functionalization.⁶⁴

Bürger and Eujen were the first in 1974 to study the generation of higher silanides in more detail. They used K or KSiH_3 and reacted it with varying equivalents of silanes with the formula $\text{Si}_n\text{H}_{2n+1}$ ($n = 1-3$) and were able to prove *via* nuclear magnetic resonance (NMR) spectroscopy the existence of $\text{KSiH}_n(\text{SiH}_3)_{3-n}$ ($n = 1-3$). When reacting KSiH_3 with an excess of SiH_4 they observe next to KSiH_3 the formation of KSi_2H_5 (see Scheme 21, path a). On the other hand, upon the reaction of K with di- or trisilane, or KSiH_3 with trisilane they report the formation of the higher silanides $\text{KSiH}_n(\text{SiH}_3)_{3-n}$ ($n = 1-3$) (see Scheme 21, path b). Furthermore, they note that when an excess of trisilane is used the main product is $\text{KSi}(\text{SiH}_3)_3$ (see Scheme 21, path c), and an excess of K leads to cleavage of Si-Si-bonds. Finally, when they reacted the formed silanides with HCl, they always observe SiH_4 and Si_2H_6 next to small amounts of the expected silanes $\text{Si}_n\text{H}_{2n+2}$.⁶⁵



Scheme 19 Synthesis of MSiH_3 in HMPA. Isolation of the silanide failed.



Table 2 Results of the reactions between $\text{KSiH}_3 + x\text{Si}_3\text{H}_8$ with the composition of the reaction solution at the respective time in mol%

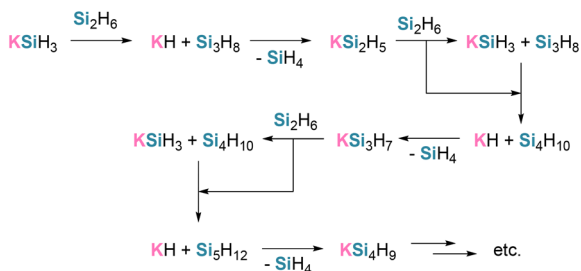
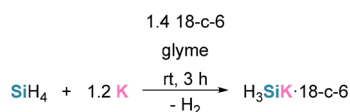
Molar ratio x	0.5	1.0	1.5	2.0	2.5	3.0
Reaction time [h]	0.25	0.33	24	48	72	72
KH	—	—	2.7	3.9	2.0	—
KSiH_3	42.6	2.5	—	—	—	—
KSi_2H_5	50.8	61.5	Trace	Trace	—	—
$\text{KSiH}(\text{SiH}_3)_2$	6.6	34.5	91.0	22.3	2.5	2.2
$\text{KSi}(\text{SiH}_3)_3$	—	1.5	6.3	73.8	95.5	97.8

Table 3 Results of the reactions between KSiH_3 and the respective silane (A = iso- Si_4H_{10} , B = n - Si_4H_{10} , C = Si_5H_{12}) with their compositions at the respective time in mol%

Reaction	$\text{KSiH}_3 + 2\text{A}$	$\text{KSiH}_3 + 2\text{B}$	$\text{KSiH}_3 + 2\text{C}$			
Reaction time [h]	1	72	1	72	24	48
KH	2.2	3.6	1.8	4.2	7.1	1.8
KSiH_3	Trace	—	Trace	—	—	—
KSi_2H_5	Trace	—	Trace	—	—	—
$\text{KSiH}(\text{SiH}_3)_2$	82.6	1.5	85.9	1.7	66.9	3.4
$\text{KSi}(\text{SiH}_3)_3$	15.2	94.9	12.3	94.1	26.0	94.8

polymer, $(\text{K}_{0.09}\text{SiH}_{1.19})_n$. On the basis of these observations, a mechanism (see Scheme 23) was proposed in which stepwise nucleophilic substitutions at silicon generate KH and higher silanes as intermediates; these silanes undergo competing silylation and metalation. Because the intermediate silanes (other than SiH_4) re-enter the reaction network, the sequence converges to mixtures of $\text{KSiH}_n(\text{SiH}_3)_{3-n}$, SiH_4 , and the potassium containing polymeric silicon hydride.⁶⁹

Fieselmann and Dickson showed that adding 18-c-6 to the reaction of SiH_4 with potassium in glyme markedly accelerates formation of $[\text{K}(18\text{-c-6})\text{SiH}_3]$, reducing the reaction time to hours (see Scheme 24). Under these conditions the silanide precipitates as a white solid; after 3 h, monitoring of hydrogen

**Scheme 23** Proposed mechanism by Fehér and Krancher towards the formation of higher silanides.**Scheme 24** Formation of KSiH_3 complexed with 18-c-6, no yields reported.

evolution indicated that 87% of the SiH_4 had been consumed. The resulting silanide was subsequently subjected to electrophilic functionalization (see Scheme 48).⁷⁰

F. Fehér, Krancher, and M. Fehér (1991) revisited the Na/ SiH_4 system and established that reactions of SiH_4 with sodium in ether solvents invariably yield mixtures of sodium silanides $\text{NaSiH}_{3-n}(\text{SiH}_3)_n$ ($n = 0-3$), rather than exclusively NaSiH_3 (see Scheme 25, path a). Product distributions determined by benzyl chloride trapping followed by GC analysis, together with direct NMR characterization of the silanide solutions, contradict earlier claims by Hagenmuller and Pouchard of sole NaSiH_3 formation.^{61,71} The sodium silanides proved markedly more stable in solution than previously suggested, showing no detectable degradation over weeks at room temperature. In DME, the steady-state composition contained approximately twice as much NaSiH_3 as NaSi_2H_5 ; in diglyme, the ratio increased to about 4.5:1. Minor $\text{NaSiH}(\text{SiH}_3)_2$ was consistently observed, with only trace amounts of $\text{NaSi}(\text{SiH}_3)_3$. Substantial NaH formation was detected only at -30°C , and the overall conversion of SiH_4 to sodium silanides at room temperature was 54–60%. Further investigations examined the effects of used sodium, reaction vessel size, solvent volume, reaction time, and temperature; full details are provided in the original publication. Attempts to isolate discrete sodium silanides by concentrating the solutions promoted redistribution toward higher silanides (see Table 4), whereas evaporation to dryness gave only NaH and polysilanes, indicating complete silanide decomposition (see Scheme 25, path b). The related reaction of KSiH_3 with excess of SiH_4 in DME exhibited a pronounced concentration dependence: dilute solutions favored the distribution $\text{KSi}_2\text{H}_5 > \text{KSiH}_3 > \text{KSiH}(\text{SiH}_3)_2$, whereas more concentrated mixtures reacted approximately twice as fast but

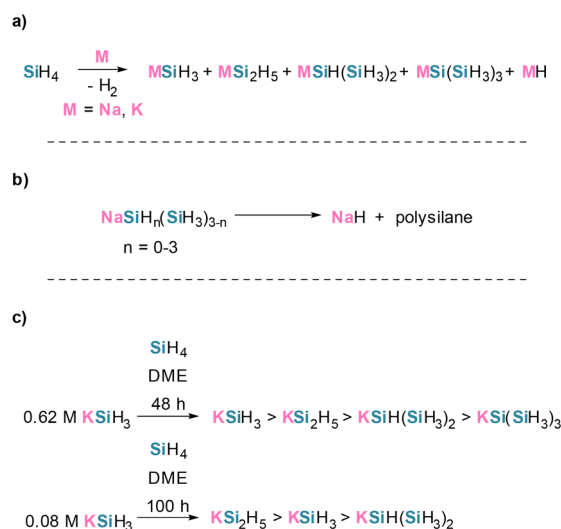
**Scheme 25** a) Monosilane reacting with Na or K forming different silanides $\text{MSiH}_n(\text{SiH}_3)_{3-n}$ ($n = 0-3$). (b) Attempted isolation of formed silanides leading to degradation. (c) Concentration dependency of formed silanides.

Table 4 Results of the silanide solution composition before and after concentrating the solution

Silanide	Composition of the starting solution [mol%]	Composition of the solution after concentrating it [mol%]
NaSiH ₃	65	25.7
NaSi ₂ H ₅	30.4	16.1
NaH(SiH ₃) ₂	4.6	30.3
NaSi(SiH ₃) ₃	Trace	27.9

afforded $\text{KSiH}_3 > \text{KSi}_2\text{H}_5 > \text{KSiH}(\text{SiH}_3)_2 > \text{KSi}(\text{SiH}_3)_3$ (see Scheme 25, path c).⁷¹

Lobreyer, Oeler, and Sundermeyer (1991) designed a purpose-built reactor (design details in Fig. 5) that enabled complete consumption of 15 g of potassium to form KSiH_3 at 65 °C in only 105 minutes in diglyme and 150 minutes in DME. The yield of KSiH_3 was quantitative with respect to potassium.^{46,72} This represented a substantial acceleration over the fastest previously reported procedure, which required 11–12 hours to consume 15 g of potassium.⁶⁸

In a follow-up study, Lobreyer *et al.* attempted to prepare NaSiH_3 in diglyme using the same reactor. Instead, they consistently obtained mixtures of sodium silanides $\text{NaSiH}_n(\text{SiH}_3)_{3-n}$ ($n = 0-3$). Spectroscopic analysis after functionalization with *p*-toluenesulfonic acid (PTSA) indicated approximately 50% conversion to $\text{NaSi}(\text{SiH}_3)_3$. Analogously, direct reaction of potassium metal with SiH_4 in the specialized reactor furnished higher potassium silanides $\text{KSiH}_{3-n}(\text{SiH}_3)_n$ ($n = 0-3$) in approx. 90% yield relative to the potassium input, as determined by titration. For both K and Na, extended reaction times at 100 °C afford greater quantities of $\text{K}/\text{NaSiH}_n(\text{SiH}_3)_{3-n}$ ($n = 0, 1$); concentrating the solution by solvent removal likewise promotes formation of higher silanides. Using K at 70 °C yields exclusively KSiH_3 with no evidence of the build-up reaction. The resulting solutions were subsequently engaged in follow-up transformations with C-, P-, and Sn-based electrophiles (see Schemes 53, 129 and 73).⁴⁷

Stueger *et al.* accessed iso-tetrasilanides by the reaction of methyllithium (MeLi) with neopentasilane.⁷³ Later Lainer *et al.* succeeded in the isolation of iso-tetrasilanide through the addition of tetramethylethylenediamine (TMEDA) (see Scheme 26, path a). Full removal of solvent leads to decomposition, but the isotetrasilanide precipitates from the reaction solution, enabling isolation.

Analogously, neopentasilane with $\text{MO}t\text{Bu}$ ($M = \text{Li, Na, K, Rb, Cs}$) in THF, and with $\text{LiN}(\text{iPr})_2$ in Et_2O (see Scheme 26, path b and c) also led to the isotetrasilanides.^{48,74} For $M = \text{K}$, identical outcomes were obtained in Et_2O and DME as in THF.⁴⁸ Attempts at isolation or recrystallization led to yellow, insoluble polymers; however, ethereal solutions were stable for several hours and could be employed for downstream functionalization (see Scheme 55). Formation of iso-tetrasilanides was quantitative as determined *via* NMR-spectroscopy.⁴⁸

In 2015, Leich, Spaniol, and Okuda introduced a concise, high-yield route to the α -polymorphs of potassium silanide, α - KSiH_3 and α - KSiD_3 , *via* hydrogenolysis/deuterolysis of the tri-

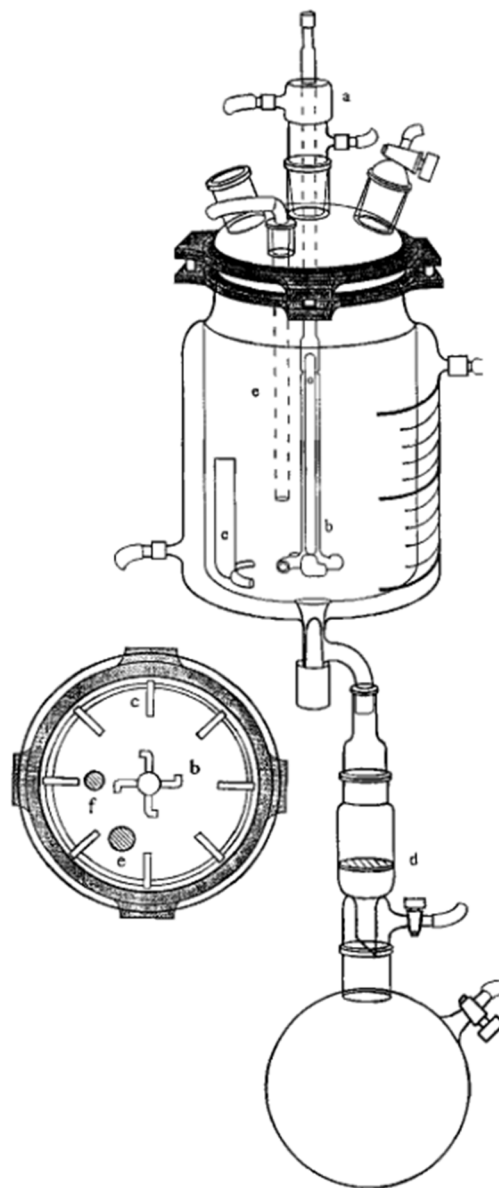
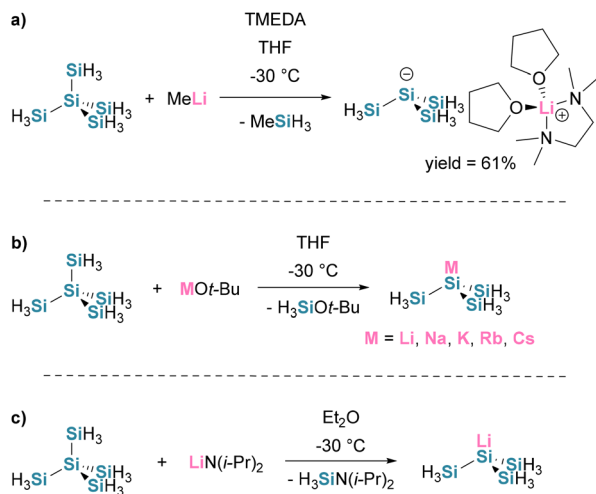


Fig. 5 Reactor design developed by Lobreyer, Oeler, and Sundermeyer. (a) Stirrer bearing, (b) gas-sparging (hollow) stirrer, (c) vortex breaker, (d) G4 frit, (e) gas inlet, (f) temperature probe. Reproduced from ref. 46 with permission from European Chemical Society. © 1991.

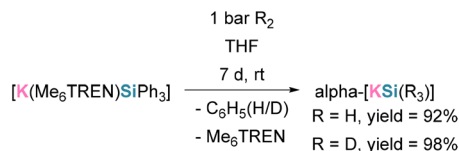
phenylsilyl complex $[\text{K}(\text{Me}_6\text{TREN})\text{SiPh}_3]$ ($\text{Me}_6\text{TREN} = \text{tris}[2\text{-(dimethylamino)ethyl}]\text{amine}$), affording isolated yields of up to 98% (see Scheme 27).⁷⁵

Schuhknecht *et al.* broadened the hydrogenolysis strategy by using the chelating ligand 1,4,7,10-tetramethyl-1,4,7,10-tetraaminocyclododecane (Me_4TACD). The triphenylsilyl precursors $[(\text{L})\text{MSiPh}_3]_n$ ($M = \text{Li, Na, K, Rb, Cs}$; $L = \text{Me}_4\text{TACD}$) underwent hydrogenolysis with H_2 (Scheme 28, path a) to give the corresponding hydridosilanide complexes $[(\text{L})\text{MSiH}_3]_m$ in yields up to 93% for $M = \text{Na, K, and Rb}$. In the lithium system, only small amounts (<10%) of $[(\text{L})\text{LiSiH}_3]_m$ could be isolated; extensive ligand decomposition was observed alongside

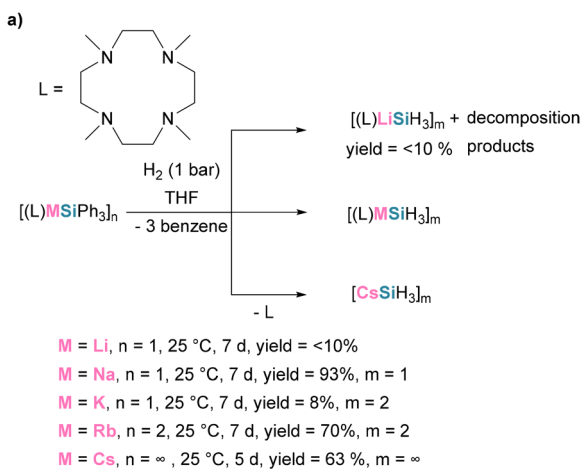




Scheme 26 Synthesis of isotetrasilanides *via* different routes (path a–c). Yields according to NMR-spectroscopy are quantitative.



Scheme 27 Generation of silanide through hydrogenolysis/deuterolysis.



Scheme 28 Generation of silanides through a hydrogenolysis reaction (path a) and a redistribution route (path b).

neutral silanes $H_{n+1}SiPh_{3-n}$ ($n = 0-3$). For cesium, hydrogenolysis afforded the ligand-free, polymeric trihydridosilanide $[CsSiH_3]_\infty$.

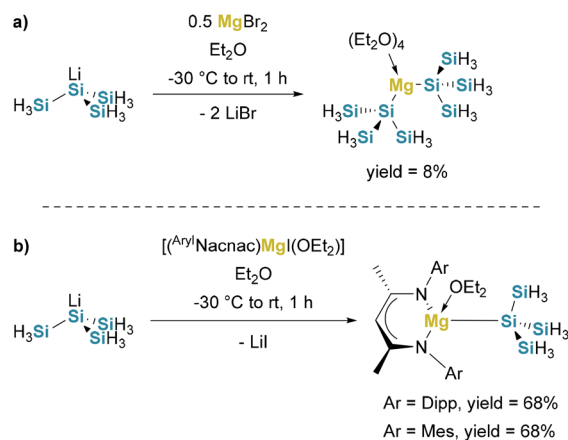
Alternatively, $[(L)MSiH_3]_m$ ($M = Li, Na, K, Rb$) can be prepared *via* a redistribution route (Scheme 28, path b): catalytic amounts of $[(L)MSiPh_3]_n$ promote scrambling of $HSiPh_3$ in solution to generate H_2SiPh_2 and SiH_4 *in situ*; subsequent reaction of SiH_4 furnishes the hydridosilanide complexes. This indirect route is particularly advantageous for $M = Li$, substantially improving the final yield relative to direct hydrogenolysis.⁷⁶

Functionalization with group 2 (synthesis of silanides). The field of silanide chemistry has been dominated by studies of alkali metal derivatives, whereas alkaline earth metal analogues have been almost entirely overlooked. It was only in very recent work that these compounds were shown to be stable and isolable.

Lainer *et al.* prepared the magnesium silanide $Mg[Si(SiH_3)_3]_2$ in low yield by salt metathesis of the isotetrasilanide $LiSi(SiH_3)_3$ with $MgBr_2$ (see Scheme 29, path a); however, the product is unstable and decomposes over several days at room temperature. In contrast, reaction of $LiSi(SiH_3)_3$ with $[(^{Aryl}NacNac)MgI(OEt_2)]$ afforded the corresponding ligand-supported magnesium silanide $[(^{Aryl}NacNac)MgSi(SiH_3)_3]$ ($Aryl = 2,6$ -diisopropylphenyl (Dipp), $2,4,6$ -trimethylphenyl (Mes)) in good yields (see Scheme 29, path b). This complex remains stable after solvent removal, when stored at low temperature. Single-crystal X-ray diffraction of $[(^{Dipp}NacNac)MgSi(SiH_3)_3] \cdot Et_2O$ (see Fig. 6) provided the first crystallographic characterization of a higher silanides.⁷⁴

Functionalization with group 3 (synthesis of silyltetrels)

Silylboranes. In silicon device manufacturing, p-type films are typically deposited by co-flowing diborane with silane in chemical vapor deposition (CVD), with the B_2H_6/SiH_4 ratio, temperature, and plasma conditions governing boron incorporation into polycrystalline, amorphous, or epitaxial silicon.^{77,78} In contrast, molecules that already contain Si–B



Scheme 29 Synthesis of magnesium isotetrasilanides by Lainer *et al.* (path a and b).



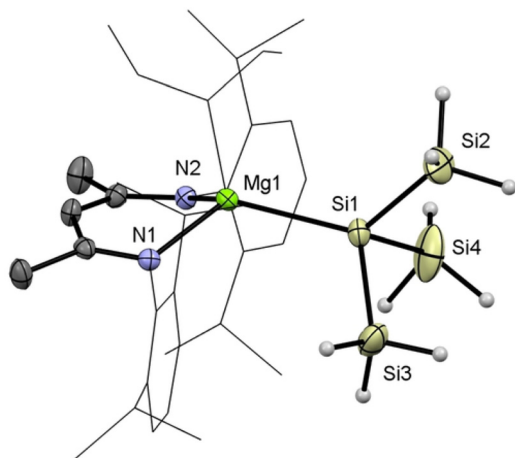
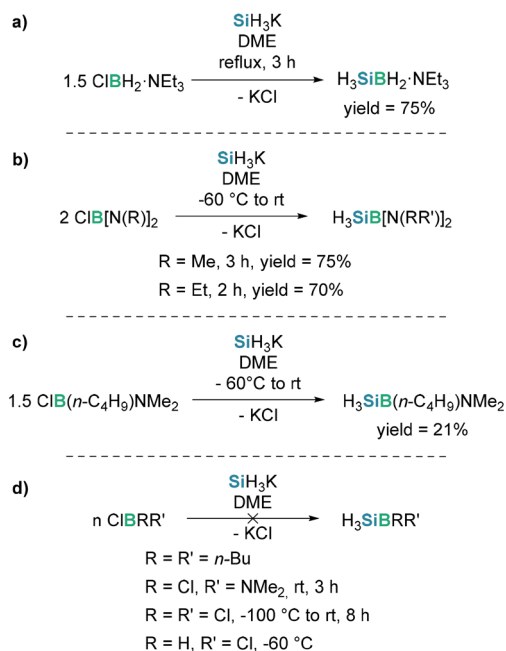


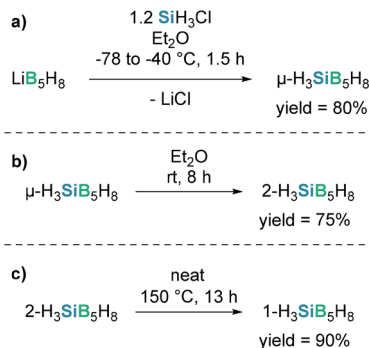
Fig. 6 Crystal structure of the magnesium isotetrasilanide $[(\text{DIPP})_2\text{NaCNac}]\text{MgSi}(\text{SiH}_3)_3 \cdot \text{Et}_2\text{O}$ from ref. 74 published by wiley under CC-BY 4.0. © 2022.

bonds while retaining Si–H provide cleaner, single-source feedstocks that co-deliver silicon and boron and, ideally, evolve only hydrogen as a byproduct, thereby minimizing carbon/halogen contamination and facilitating precise control of dopant concentration.⁷⁹

Amberger and Römer employed KSiH_3 to access a range of silyl boranes *via* salt metathesis with chloroboranes. While several new $\text{SiH}_3\text{-BR}_2$ derivatives were obtained (see Scheme 30, path a–c), reactions with $\text{ClB}(n\text{-Bu})_2$, Cl_2BNMe_2 , BCl_3 , and HBCl_2 did not yield isolable target compounds (see Scheme 30, path d). From these results they concluded that isolable silyl boranes require compensation of the electron



Scheme 30 Synthesis of silylboranes using SiH_3K (path a–d).

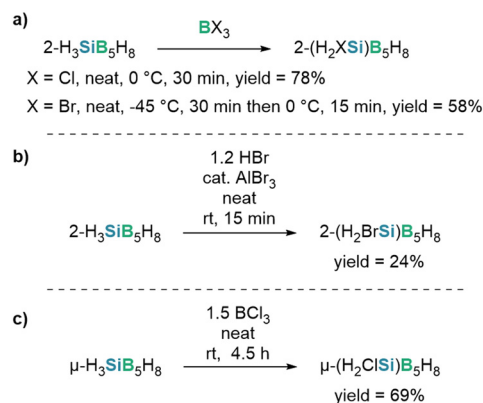


Scheme 31 Generation of μ -silylpentaborane and its isomerization reactions (path a–c).

deficiency at boron by neighbouring donor substituents capable of pi donation (*e.g.*, amino groups), whereas purely inductive electron release from alkyl substituents is insufficient; consistent with this, $\text{H}_3\text{SiB}(n\text{-Bu})_2$ could not be isolated.⁶²

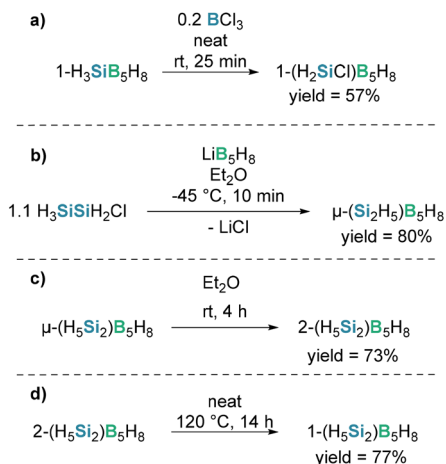
Gaines and Iorns prepared the silylborane $\mu\text{-H}_3\text{SiB}_5\text{H}_8$ in 80% isolated yield by reacting LiB_5H_8 with H_3SiCl , representing the first fully hydrogenated silicon–borane compound (see Scheme 31, path a). Stirring $\mu\text{-H}_3\text{SiB}_5\text{H}_8$ with diethyl ether at ambient temperature for 8 h afforded $2\text{-H}_3\text{SiB}_5\text{H}_8$ (see Scheme 31, path b).⁸⁰ In a subsequent study, heating of $2\text{-H}_3\text{SiB}_5\text{H}_8$ to 150 °C for 13 h gave $1\text{-H}_3\text{SiB}_5\text{H}_8$, identified as the most stable isomer (see Scheme 31, path c).^{80,81} Geisler and Norman selectively halogenated the silyl substituent in silyl-substituted pentaboranes using BCl_3 , BBr_3 , and HBr (see Scheme 32, path a–c). Under otherwise comparable conditions, BCl_3 -mediated chlorination of $\mu\text{-H}_3\text{SiB}_5\text{H}_8$ required longer reaction times than chlorination of $2\text{-H}_3\text{SiB}_5\text{H}_8$ (Scheme 32, path a and c).⁸²

Geisler, Soice, and Norman investigated BCl_3 -mediated halogenation of the silyl substituent in silylpentaboranes (see Scheme 33, path a).⁸³ For $1\text{-H}_3\text{SiB}_5\text{H}_8$, the halogenation rate was indistinguishable from that of $2\text{-H}_3\text{SiB}_5\text{H}_8$, whereas the μ isomer required higher temperatures and longer reaction



Scheme 32 Halogenation reactions of 2- and μ -silylpentaborane (path a–c).



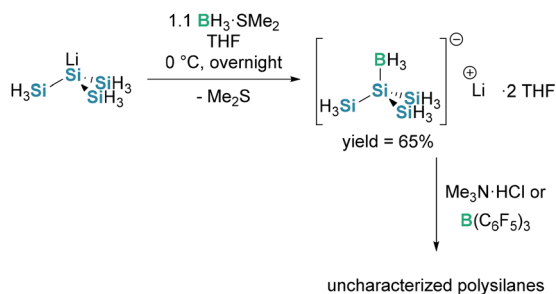


Scheme 33 Halogenation of 1-silylpentaborane and generation of disilylpentaborane and its isomers (path a–d).

times to reach full conversion (see Scheme 33, path c and d).^{82,83} They also synthesized μ -disilylpentaborane by treating LiB_5H_8 with $\text{Si}_2\text{H}_5\text{Cl}$ (see Scheme 33, path b). The μ isomer rearranged to the 2 isomer upon stirring in Et_2O at room temperature for 4 h, and to the 1 isomer only under more forcing conditions (120°C , 14 h) (see Scheme 33, path c and d). This behaviour parallels that of the corresponding monosilylpentaboranes; in both series, the thermodynamic stability follows $\mu < 2 < 1$.^{80,81,83}

Lainer *et al.* synthesized the lithium hypersilyl borate $[(\text{H}_3\text{Si})_3\text{SiBH}_3]\text{Li}$ in a single step by treating the isotetrasilane $\text{LiSi}(\text{SiH}_3)_3$ with $\text{Me}_2\text{S}\cdot\text{BH}_3$. The obtained salt is notably robust, remaining unchanged for extended periods as a solid or in solution at ambient temperature (see Scheme 34). Attempts to access cationic or neutral derivatives by hydride abstraction with $\text{B}(\text{C}_6\text{F}_5)_3$ or with $\text{Me}_3\text{N}\cdot\text{HCl}$ were unsuccessful; in both cases, uncharacterized polysilanes formed. The structure of the new hypersilyl borate was confirmed by single-crystal X-ray diffraction (see Fig. 7).⁸⁴

Silylallane. Hagenmuller and Pouchard (1964) reported the synthesis of $\text{Al}(\text{SiH}_3)_3$ by salt metathesis of NaSiH_3 with $\text{AlCl}_3\cdot\text{DME}$; however, the product is highly labile and decomposes at 0°C or upon exposure to a stream of H_2 (see



Scheme 34 Synthesis of lithium hypersilyl borate and attempted hydride abstraction reactions.

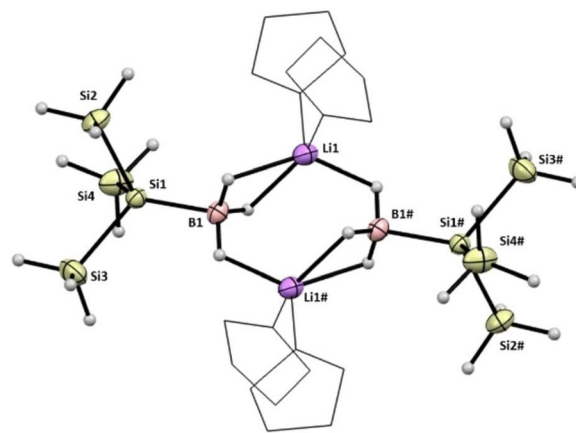
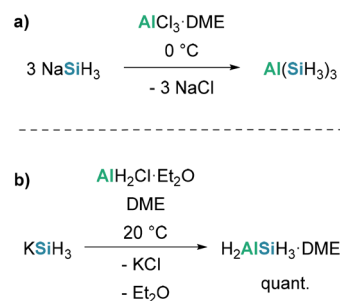


Fig. 7 Crystal structure of hypersilyl borate $[(\text{H}_3\text{Si})_3\text{SiBH}_3]\text{Li}$ from ref. 84 published by Wiley under CC-BY 4.0. © 2024.

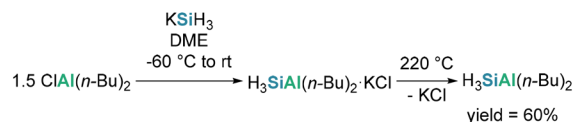
Scheme 35, path a).⁶¹ In related work, Semenenko and Taisumov obtained H_2AlSiH_3 by reacting KSiH_3 with $\text{AlH}_2\text{Cl}\cdot\text{Et}_2\text{O}$ (see Scheme 35, path b).⁸⁵ Amberger and Römer synthesized the silylallane $\text{H}_3\text{SiAl}(n\text{-Bu})_2$ by salt metathesis of KSiH_3 with $\text{ClAl}(n\text{-Bu})_2$ (see Scheme 36). After solvent removal, the material was obtained as the contact adduct $\text{H}_3\text{SiAl}(n\text{-Bu})_2\cdot\text{KCl}$. Separation of KCl required heating to 220°C , affording pure $\text{H}_3\text{SiAl}(n\text{-Bu})_2$.⁸⁶ Notably, $\text{H}_3\text{SiAl}(n\text{-Bu})_2$ exhibits high thermal stability; in contrast, related silylboranes already undergo slow decomposition at ambient temperature.^{62,86}

Functionalization with group 4 (synthesis of silyltetres)

Organosilanes. Organosilanes and related derivatives, such as silicon carbide coatings are increasingly important across semiconductor, aerospace, aircraft engines, and mechanical



Scheme 35 Generation of trisilylallane by Hagenmuller and Pouchard (path a) and monosilylallane by Semenenko and Taisumov (path b). For path (a) no yields were reported.



Scheme 36 Synthesis of silylallane by Amberger and Römer.



engineering. In semiconductor fabrication, alkylsilanes act as precursors for surface passivation, enable area-selective deposition, and improve device stability,⁸⁷ they also strengthen dielectric layers through siloxane networks⁸⁸ and promote adhesion between photoresists and SiO₂ or other substrates.⁸⁹ Furthermore high-purity alkylsilanes are critical for high-quality coatings and can function as anti-reflective layers to suppress reflections and enhance photolithography efficiency.⁹⁰

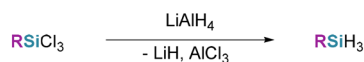
For the synthesis of organosilanes two prevalent methods are used in the literature, either the reduction of silyl halides or *via* transformations of inorganic silanes.

Reduction of silyl halides is the most commonly used approach for the synthesis of alkylsilylhydrides. Most frequently LiAlH₄ is used for the reduction, though other common reductants like lithium hydride, sodium hydride, triethyl aluminium (AlEt₃) and diisobutylaluminium hydride can be employed as well (see Scheme 37).^{28,91}

Consequently using di- to tetrabromosilylmethane with LiAlH₄ allows for the synthesis of the respective silylmethane.^{92–94} When bromosilylmethanes were treated in standard solvents such, as *n*-Bu₂O, the yields were very poor, however, using tetraline in combination with benzyltriethylammoniumchloride (TEBAC), excellent yields were achieved (see Scheme 38, path b).⁹³

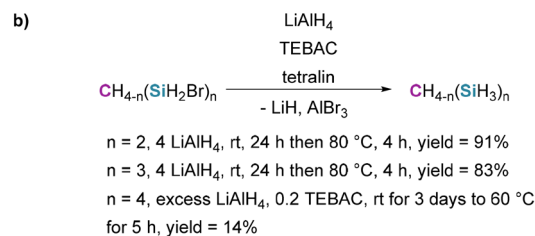
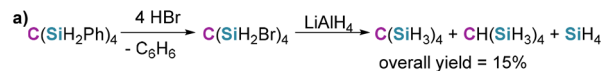
Schmidbaur and co-workers were the first to report tetrasilylmethane (C(SiH₃)₄). The usual choice of a polar solvent was replaced with a two-phase system with phase transfer catalyst, in order to suppress the cleavage of Si–C bonds, but the sideproduct trisilylmethane (HC(SiH₃)₃) was still observed (see Scheme 38, path a).^{94,95} Furthermore they were able to obtain 2,2-disilylpropane from 2,2-dibromosilylpropane Me₂C(SiH₂Br)₂.⁹⁶

While commonly Et₂O is used as the solvent of choice for the synthesis of lower boiling silanes, Kozhevnikov and co-workers were able to obtain methylsilane (MeSiH₃) in excellent yield, using *n*-Bu₂O as solvent (see Scheme 39, path a).⁹⁷ Bellama and co-workers prepared disilylmethane (H₂C(SiH₃)₂), *via* reduction of bistrichlorosilylmethane (H₂C(SiCl₃)₂), in 50% yield (see Scheme 39, path b).⁹⁸

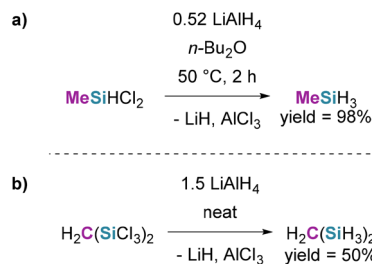


- R = Me, 1.1 LiAlH₄, dioxane, reflux, 30 min, yield = 80–90%
- R = Vinyl, 1.1 LiAlH₄, dioxane, reflux, 30 min, yield = 80–90%
- R = Et, 1.1 LiAlH₄, dioxane, reflux, 30 min, yield = 88%
- R = Pr, Et₂O, reflux, 1 h
- R = *n*-Bu, 1.1 LiAlH₄, dioxane, reflux, 30 min, yield = 80–90%
- R = *i*-Bu, 1.1 LiAlH₄, dioxane, reflux, 30 min, yield = 80–90%
- R = Ph, THF, reflux, 12 h, yield = 23%
- R = Ph, excess LiAlH₄, Et₂O, reflux, 1 h, yield = 86%

Scheme 37 Synthesis of organosilanes *via* reduction with LiAlH₄. The yields for R = Me, vinyl, *n*-Bu and *i*-Bu were only given as range of 80 to 90% by Tannenbaum *et al.* For R = Pr, no detailed yield was given.



Scheme 38 Synthesis of C(SiH₃)₄ starting from C(SiH₂Ph)₄ (path a) and synthesis of CH_{4–n}(SiH₃)_n (path b).



Scheme 39 Synthesis of MeSiH₃ (path a) and H₂C(SiH₃)₂ (path b) *via* reduction with LiAlH₄.

A representative example of metal-hydride reduction of alkylsilyl halides is the conversion of 1,1,3,3-tetrachloro-1,3-disilabutane to 1,3-disilabutane. The tetrachloro precursor is prepared in 41% yield by reacting HCl with elemental Si and MeSiCl₂CH₂Cl using Cu based catalysts,⁹⁹ followed by reduction with LiAlH₄ to afford 1,3-disilabutane (see Scheme 40).¹⁰⁰

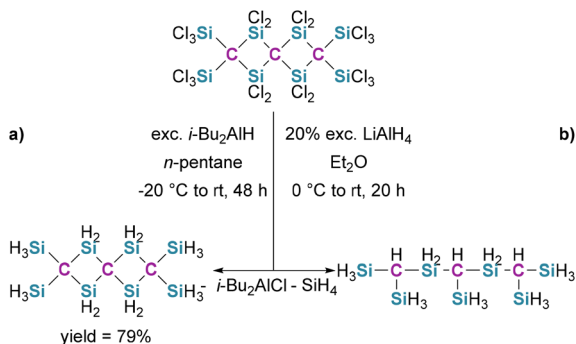
Fritz and co-workers showed that treatment of chlorinated C-spiro-linked 2,4-disilacyclobutanes with LiAlH₄ results in the cleavage of the four membered rings (see Schemes 41 and 42, path b). In contrast, when they employed *i*-Bu₂AlH no cleavage was observed, and the hydrogenated C-spiro-linked 2,4-disilacyclobutanes were obtained (see Schemes 41 and 42, path a).¹⁰¹

Pyrolysis of the methylchlorosilanes methyltrichlorosilane (MeSiCl₃), dichlorodimethylsilane (Me₂SiCl₂) and chlorotrimethylsilane (Me₃SiCl) at 700 °C afford mixtures of linear and cyclic alkylchlorosilanes, for example, 1,3-disilapropane. The chlorine containing pyrolysis products were then reduced with LiAlH₄, though isolation of pure compounds is problematic.¹⁰² Furthermore, pyrolysis of a mixture of SiH₄ and ethylene leads to formation of mixtures of the alkylsilanes ethylsilane (EtSiH₃), diethylsilane (Et₂SiH₂), triethylsilane (Et₃SiH),

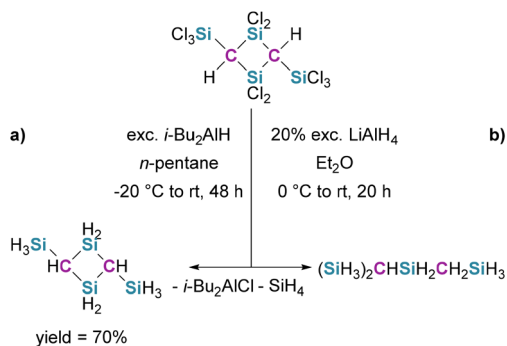


Scheme 40 Synthesis of 1,3-disilabutane by reduction with LiAlH₄. No yield and experimental details were reported for the LiAlH₄ reduction.





Scheme 41 Example of the hydration of a C-spiro linked 2,4-disilyclobutane with LiAlH₄ (path b) and *i*-Bu₂AlH (path a). No yield for the LiAlH₄ reaction was reported.



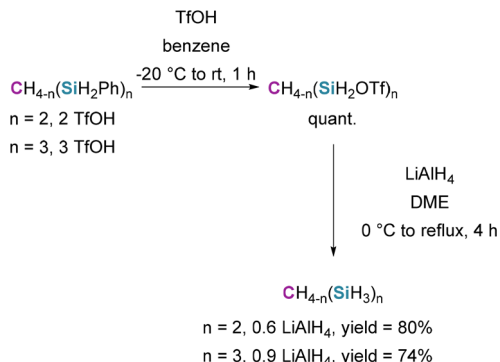
Scheme 42 Hydration of a C-spiro linked 2,4-disilyclobutane with LiAlH₄ (path b) and *i*-Bu₂AlH (path a). No yield for the LiAlH₄ reaction was reported.

though no yields were reported.¹⁰³ The copolyrolysis of disilane with methylsilane (MeSiH₃) afforded methyldisilane (MeH₂SiSiH₃), with dimethylsilane (Me₂SiH₂) it led to formation of 1,1-dimethyldisilane (Me₂SiHSiH₃) and with trimethylsilane (Me₃SiH) it resulted in the formation of 1,1,1-trimethyldisilane (Me₃SiSiH₃), though again no isolation was performed.¹⁰⁴

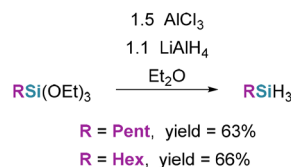
Furthermore, freshly prepared bis- and tristrifluoromethanesulfonatosilylmethanes are effective precursors for di- and trisilylmethanes. Although the formation of these intermediates proceeds in essentially quantitative yield, they undergo decomposition and isomerization at ambient temperature; therefore, immediate reduction is required to achieve optimal yields (see Scheme 43).¹⁰⁵

Westermarck *et al.* employed LiAlH₄ in combination with aluminium chloride (AlCl₃) to reduce alkyltriethoxysilanes to the respective alkylsilanes in good yields (see Scheme 44).¹⁰⁶

Trialkylstannanes can be used together with Lewis-base catalysts for the partial and full reduction of alkylsilylhalides to alkylhydrosilanes. Usually a distribution of products is obtained, depending on the catalyst used, the stannane used and the molar ratio of stannane to silane.^{107–109} When using tributyltin hydride (Bu₃SnH) and catalytic amounts of triphenylphosphine (PPh₃), methylchlorodisilanes show signifi-



Scheme 43 Synthesis of di- and trisilylmethane via reduction.¹⁰⁵

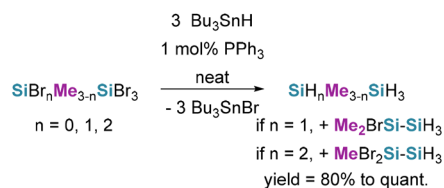


Scheme 44 Reduction of alkyltriethoxysilanes to afford alkylsilanes.

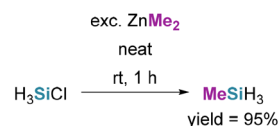
cant Si-Si bond cleavage; in contrast, no cleavage is observed when the analogous methylbromodisilanes are used (see Scheme 45).¹⁰⁷

One of the first reported synthesis of monoalkylsilanes is the synthesis of MeSiH₃ from H₃SiCl, by Stock and Somieski in 1919. But no information about the purity of the obtained MeSiH₃ is given (see Scheme 46).¹⁰

Another approach is the direct hydrosilylation of unsaturated substrates, though early work demonstrated that direct addition of SiH₄ to alkenes or alkynes generally affords product mixtures with low yields under both thermal and photochemical conditions.¹¹⁰ The use of catalysts, for example alkali metal aluminates¹¹¹ and LiAlH₄¹¹² promotes more selec-



Scheme 45 Reduction of methylbromodisilanes with Bu₃SnH and PPh₃. No specific yields were reported for the individual compounds, but yields were given as 80% to quantitative yields for the reductions.



Scheme 46 Synthesis of MeSiH₃ via reaction of H₃SiCl with ZnMe₂.

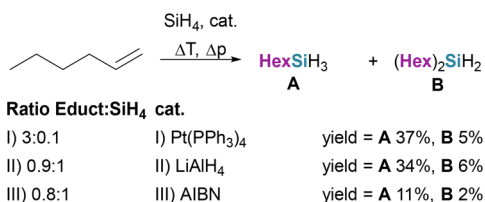


tive addition of SiH_4 to alkenes, significantly improving the selectivity. The best results were achieved by employing $\text{Pt}(\text{PPh}_3)_4$ as catalyst (see Scheme 47).¹¹³

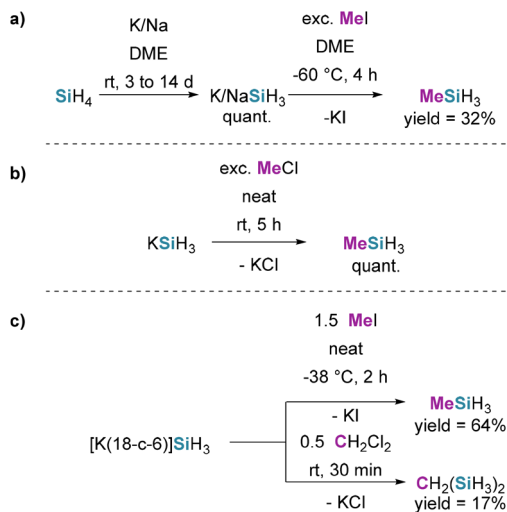
SiH_4 was also employed as feedstock for nucleophilic substitution *via* silyl anions. Conversion of SiH_4 into KSiH_3 allows for subsequent reaction with organic halides, for example MeSiH_3 was obtained by reaction of methyl iodide (MeI) with KSiH_3 (see Scheme 48, path a).¹¹⁴ Ritter and Ring obtained MeSiH_3 in excellent yields by treating KSiH_3 with excess methyl chloride (MeCl) (see Scheme 48, path b).¹⁵ Fiesemann and Dickson improved the yields by using potassium(18-crown-6) silanide ($[\text{K}(18\text{-c-}6)]\text{SiH}_3$) and demonstrated the synthesis of $\text{H}_2\text{C}(\text{SiH}_3)_2$ (see Scheme 48, path c).⁷⁰ Similar to Na and KSiH_3 , RbSiH_3 and CsSiH_3 are suitable for the reaction with MeI as well.⁶⁴

Nucleophilic substitution between KSiH_3 and bromomethylsilane (MeSiH_2Br) only leads to formation of methyl-disilane in poor yields of 5%, a more suitable approach is the reaction between a monohalodisilane with methyl lithium (MeLi) (see Scheme 49, path a and b).⁹²

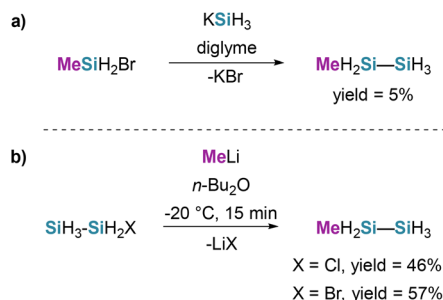
Alkali metal silanides derived from SiH_4 can be converted to alkylsilanes in hexamethylphosphoramide upon treatment with the corresponding alkyl halides, typically in good yields (see Scheme 50).⁶³



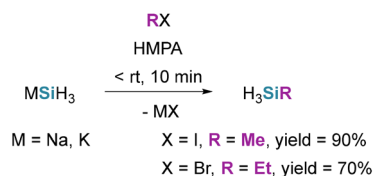
Scheme 47 Synthesis of alkylsilanes *via* addition of SiH_4 to an alkene.



Scheme 48 Synthesis of alkylsilanes by reaction of KSiH_3 with MeX ($\text{X} = \text{Cl}, \text{I}$) (path a–c).



Scheme 49 Synthesis of methyl-disilane (path a and b).



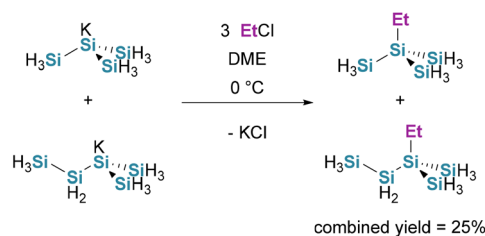
Scheme 50 Synthesis of methyl- and ethylsilane from K - or NaSiH_3 . No detailed procedures with exact amounts of reagents were given for $\text{R} = \text{Me}, \text{Et}$.

Treatment of mixtures of potassium silanides with ethyl chloride (EtCl) afforded the corresponding ethylsilanes in approximately 25% overall yield, notably individual product yields were not reported (see Scheme 51).⁶⁶

Furthermore, treatment of mixtures of higher potassium silanides with phenyl chlorosilane (PhH_2SiCl) afforded the corresponding phenylsilanes in approximately 20% overall yield, notably no specific yield was given for the individual products (see Scheme 52).⁴⁵

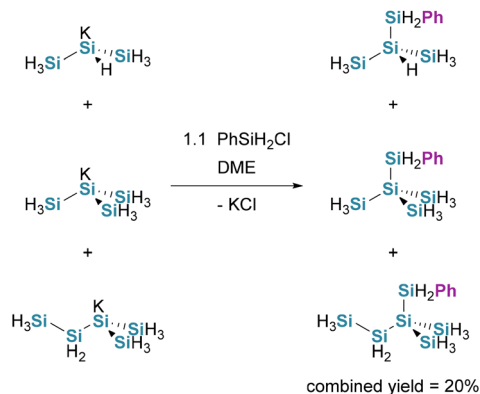
Sundermeyer and co-workers accessed the methyl-substituted silanes MeSiH_3 , methyl-disilane ($\text{MeSiH}_2\text{SiH}_3$), 2-methyltrisilane ($\text{SiH}_3\text{SiHMeSiH}_3$) and $\text{MeSi}(\text{SiH}_3)_3$ *via* the buildup reaction between SiH_4 and K in diglyme, and subsequent alkylation with methyl *p*-toluenesulfonate (*p*-TosMe) (see Scheme 53).^{47,115}

Stueger and co-workers employed lithium and potassium isotetrasilanes to access methylisotetrasilane ($\text{MeSi}(\text{SiH}_3)_3$) and a range of alkyl- and phenyl-substituted neopentasilanes. Treatment of solutions of lithium isotetrasilane ($\text{LiSi}(\text{SiH}_3)_3$)

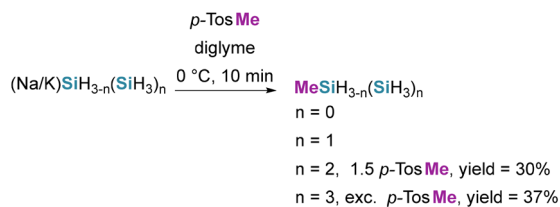


Scheme 51 Synthesis of ethyl substituted silanes from potassium silanides with ethylchloride. No specific yield for the individual compounds was given.



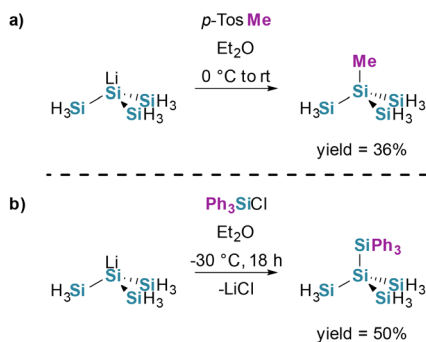


Scheme 52 Synthesis of phenylisotetra-, phenylneopenta-, and phenylneohexasilane from the respective potassium silanide and phenylchlorosilane. No specific yield for the individual compounds was assigned.

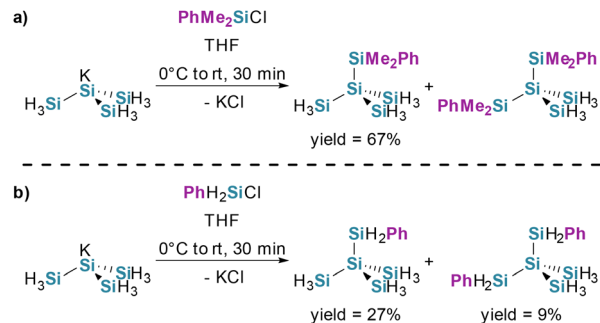


Scheme 53 Synthesis of methylsilanes from silanide mixtures. While products are formed with $n = 0-3$, the isolated yield was only given for $n = 2$ and $n = 3$.

with methyl *p*-toluenesulfonate afforded methylisotetrasilane in 36% yield, while using triphenylchlorosilane (ClSiPh_3) as the electrophile furnished triphenylsilylneopentasilane ($\text{SiPh}_3\text{Si}(\text{SiH}_3)_3$) in 50% yield (see Scheme 54, path a and b). When dimethylphenylchlorosilane (ClSiMe_2Ph) or phenylchlorosilane (ClSiH_2Ph) were employed, both the corresponding monosubstituted neopentasilanes and the disubstituted derivatives were obtained (see Scheme 55, path a and b). To suppress disubstitution, the authors avoided an



Scheme 54 Synthesis of methylisotetrasilane (path a) and triphenylsilylneopentasilane (path b) from lithiumisotetrasilanide.



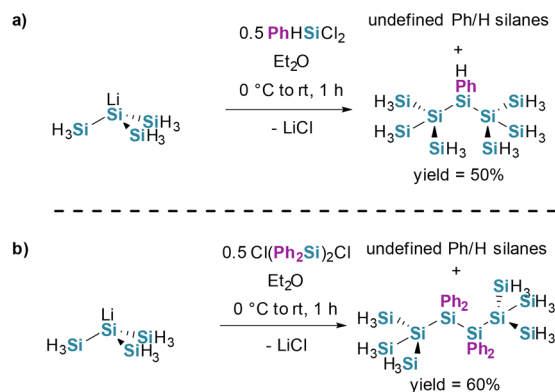
Scheme 55 Synthesis of dimethylphenyl- and phenylneopentasilane from potassiumisotetrasilanide, with concomitant formation of the respective disubstituted product (path a and b). The yield for disubstituted bisdimethylphenylneopentasilane was not reported.

excess of potassium silanide by adding the silanide slowly to the electrophile.⁴⁸

Stueger, Haas and co-workers obtained several phenyl-substituted organosilanes in good yields by treating lithium isote-tetrasilanide with phenylchlorosilanes as electrophiles. When dichlorophenylsilane (Cl_2HSiPh) and 1,2-dichloro-1,2-tetrakisphenyl-disilane were employed as electrophiles, the corresponding branched nonasilane and branched decasilane were isolated as pure compounds, however, the silane byproducts were not identified (see Scheme 56, path a and b). A crystal X-ray structure was determined for $(\text{SiH}_3)_3\text{Si}(\text{SiPh}_2)_2\text{Si}(\text{SiH}_3)_3$ (see Fig. 8).⁴⁹

In contrast, when dichlorodiphenylsilane (Cl_2SiPh_2) was used as electrophile the corresponding diphenylneopentasilane, and two cyclic phenylsilane byproducts were obtained in low yields (see Scheme 57). A crystal structure from $(\text{SiH}_3)_3\text{SiPh}_2(\text{SiH}_3)_3$ was obtained (see Fig. 9).⁴⁹

Moreover, treatment of $(\text{H}_3\text{Si})_3\text{Si}(\text{SiPh}_2)_2\text{Si}(\text{SiH}_3)_3$ with triflic acid gave the partially hydrogenated derivative $(\text{H}_3\text{Si})_3\text{Si}(\text{SiPhH})_2\text{Si}(\text{SiH}_3)_3$, this compound was not isolated but was



Scheme 56 Synthesis of phenylsubstituted nona- and decasilanes from lithium isotetrasilanide (path a and b). Both compounds were isolated as pure compounds, but during the reaction undefined silanes emerged as byproducts.



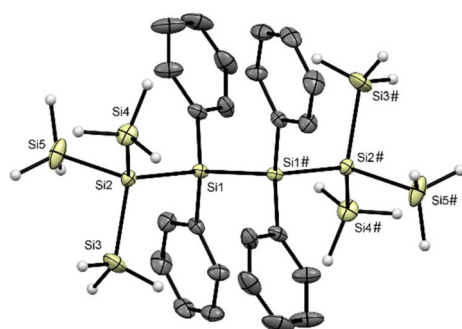
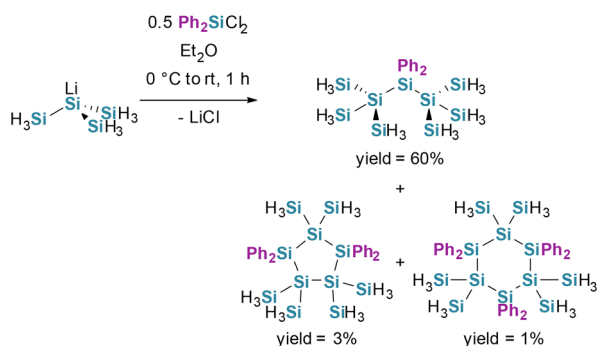


Fig. 8 Crystal structure of $(\text{SiH}_3)_3\text{Si}(\text{SiPh}_2)_2\text{Si}(\text{SiH}_3)_3$, adapted from Stueger and Haas *et al.*⁴⁹ with permission from American Chemical Society © 2019.



Scheme 57 Synthesis of phenylsubstituted organosilanes with dichlorodiphenylsilane.

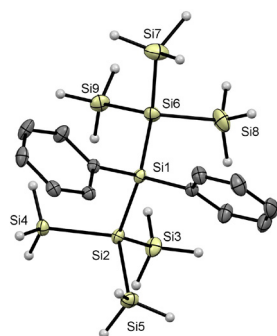
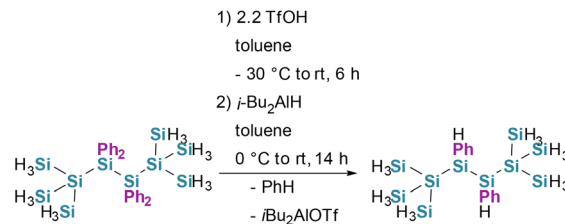


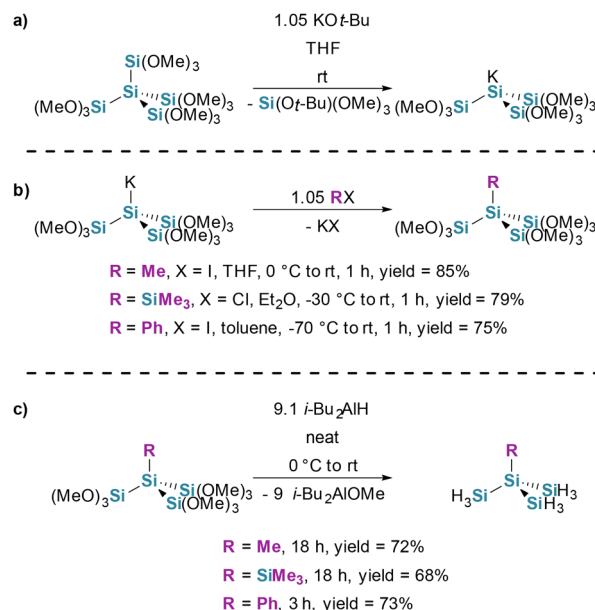
Fig. 9 Crystal structure of $(\text{SiH}_3)_3\text{SiPh}_2(\text{SiH}_3)_3$, adapted from Stueger and Haas *et al.*⁴⁹ with permission from American Chemical Society © 2019.

used *in situ* to prepare the fully hydrogenated product $(\text{H}_3\text{Si})_3\text{Si}(\text{SiH}_2)_2\text{Si}(\text{SiH}_3)_3$ (see Scheme 58).⁴⁹

Haas and co-workers converted dodecamethoxyneopentasilane to the corresponding potassium silanide using potassium *t*-butoxide ($\text{KO}t\text{-Bu}$) (see Scheme 59, path a). The subsequent treatment of the silanide with electrophiles, such as MeI resulted in the formation of the corresponding nonamethoxyisotetrasilanes (see Scheme 59, path b). Reduction of these derivatives with a slight excess of $i\text{-Bu}_2\text{AlH}$ afforded the corres-



Scheme 58 Synthesis of $(\text{H}_3\text{Si})_3\text{Si}(\text{SiPhH})_2\text{Si}(\text{SiH}_3)_3$. The compound was not isolated and reacted further to $(\text{H}_3\text{Si})_3\text{Si}(\text{SiH}_2)_2\text{Si}(\text{SiH}_3)_3$.



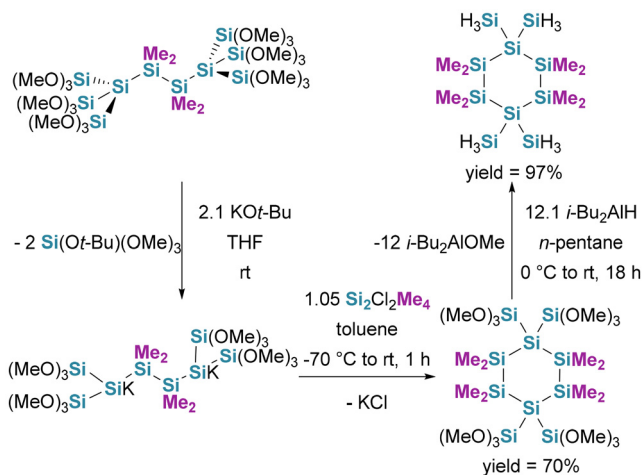
Scheme 59 Synthesis of organosilanes from potassium silanides via reaction with electrophiles and subsequent reduction with $i\text{-Bu}_2\text{AlH}$ (path a–c).

ponding organosilanes in good yields (see Scheme 59, path c).^{22,116} Applying the same strategy to a potassium disilanide delivered the cyclic 1,1,4,4-tetrakis(silyl)octamethyl-cyclohexasilane (see Scheme 60). A crystal structure of this compound was also obtained (see Fig. 10).²²

Silyl halides are viable substrates for Grignard based synthesis of alkylsilanes, though only in moderate yields. As an example, H_3SiBr reacts with various Grignard reagents to afford the respective alkylsilane (see Scheme 61).¹¹⁷

Moreover, halomethylsilanes, such as bromo- and chlorosilylmethane are suitable precursors to silylmethyl Grignard reagents ($\text{XMgCH}_2\text{SiH}_3$), which subsequently react with halosilanes to furnish silyl-substituted methanes, exemplified by $\text{CH}_2(\text{SiH}_3)_2$ (see Scheme 62). However, neither bromo- nor chloromethylsilane reacts with magnesium under standard conditions, the corresponding Grignard reagent is obtained only when activated magnesium is generated by reducing magnesium chloride (MgCl_2) with K in THF under reflux. They stated that they obtained 1,2-disilylthane ($\text{H}_3\text{SiEtSiH}_3$) in 26% yield from the preparation of $\text{H}_3\text{SiCH}_2\text{MgBr}$ due to Wurtz-





Scheme 60 Synthesis of organohexasilane compounds from a potassiumdisilanide.

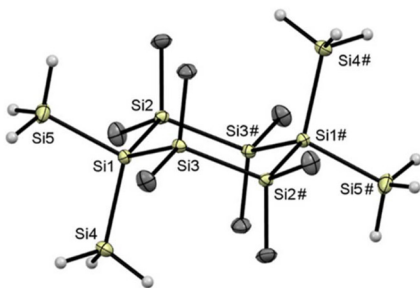
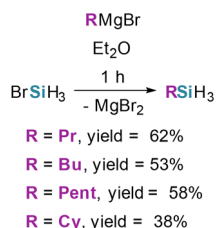


Fig. 10 Crystal structure of 1,1,4,4-tetrakis(silyl)octamethylcyclohexasilane. Adapted from Haas *et al.*²² published by American Chemical Society under CC-BY 4.0.

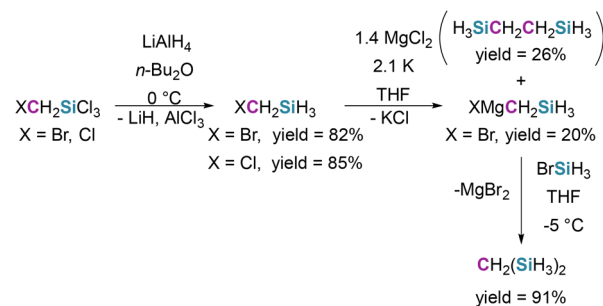


Scheme 61 Synthesis of alkylsilanes from silyl halides and Grignard reagents. No specific molar ratios or temperatures were given for the synthesis.

coupling. Further examples of this synthesis approach are given in Table 5.¹¹⁸

Dimethyltitanocene (Me_2TiCp_2) is able to catalyze redistribution reactions of diethoxymethylsilane ($(\text{EtO})_2\text{MeSiH}$) affording triethoxymethylsilane ($(\text{EtO})_3\text{MeSi}$) and methylsilane in excellent yields.¹¹⁹ Other catalysts like sodium ethoxide are used for the redistribution as well (see Scheme 63).¹²⁰

Ozonizer-type silent electrical discharge tubes were also employed in the synthesis of methylsilane from a mixture of

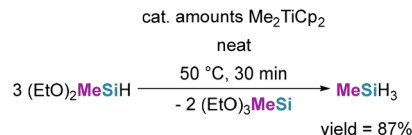


Scheme 62 Example synthesis of alkylsilanes from silylmethylgrignard compounds.

Table 5 Synthesis of silyl substituted methanes from halosilanes and grignard reagents

Grignard reagent	Halosilane	Product	Yield [%]
$\text{Me}_3\text{SiCH}_2\text{MgCl}$	H_3SiBr	$\text{Me}_3\text{SiCH}_2\text{SiH}_3$	86
$\text{Me}_2\text{SiHCH}_2\text{MgCl}$	H_3SiBr	$\text{Me}_2\text{SiHCH}_2\text{SiH}_3$	20–30*
$\text{MeSiH}_2\text{CH}_2\text{MgCl}$	H_3SiBr	$\text{MeSiH}_2\text{CH}_2\text{SiH}_3$	92
$\text{H}_3\text{SiCH}_2\text{MgBr}$	H_3SiBr	$\text{CH}_2(\text{SiH}_3)_2$	91
$\text{H}_3\text{SiCH}_2\text{MgBr}$	Me_2SiHCl	$\text{H}_3\text{SiCH}_2\text{SiHMe}_2$	30*
$\text{H}_3\text{SiCH}_2\text{MgBr}$	Me_3SiCl	$\text{H}_3\text{SiCH}_2\text{SiMe}_3$	85

Yields marked with asterisk are crude yields.

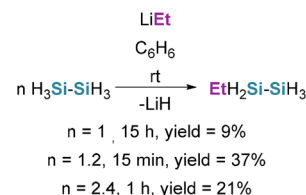


Scheme 63 Catalytic redistribution of $(\text{EtO})_2\text{MeSiH}$.

Me_2O and SiH_4 , though this approach is not synthetically useful due to the low yield of 4% and the poor selectivity.¹²¹

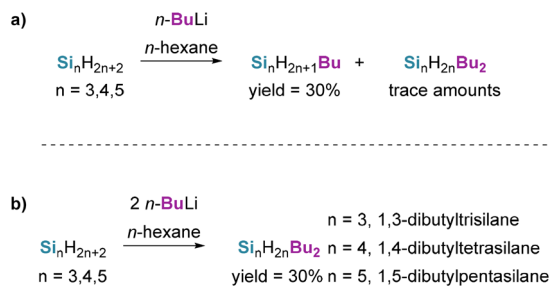
Treatment of silanes with organolithium reagents provides an alternative route to organosilanes. Bolduc and Ring reported that condensing disilane into a solution of ethyllithium (LiEt) in benzene (C_6H_6), furnishes ethyldisilane ($\text{EtH}_2\text{Si-SiH}_3$) in 37% yield by the following reaction at room temperature (see Scheme 64).¹²²

This approach can be expanded to larger silanes such as tri-, *n*-tetra- and *n*-pentasilane as well. When solutions of the respective silanes in *n*-hexane are treated with *n*-butyllithium (*n*-BuLi) solutions, the respective *n*-butylsilane is afforded (see



Scheme 64 Synthesis of ethyldisilane from disilane and ethyllithium.



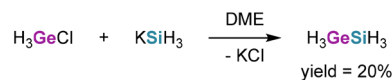


Scheme 65 Synthesis of butylsilanes from tri-, tetra- and pentasilane (path a and b). No specific yields for the disubstituted *n*-butylsilanes with 1 equivalent *n*-BuLi and no individual yields for the monosubstituted yields were given.

Scheme 65, path a and b). Disubstituted dibutylsilanes are observed as well and are the main product of the reaction when 2 equivalents of *n*-BuLi are used. Additionally, a solid polysilane is formed as well. While it was mentioned that SiH₄ and disilane are formed in the reaction with trisilane as well, it was not indicated if these silanes are observed with tetra- and pentasilane as well.¹²³

Silylgermanes. Hydrosilanes with a direct silicon–germanium bond, commonly referred to as silylgermanes, have recently attracted increasing attention as single source precursors for the deposition of mixed Si–Ge materials. In conventional processes, SiGe thin films are typically obtained from mixtures of monogermane (GeH₄) and monosilane. However, the significantly different activation energies and surface reaction kinetics of these two hydrides often lead to non-uniform incorporation during growth. As a result, classical co-flow deposition can suffer from compositional inhomogeneities, gas-phase depletion effects, and segregation phenomena such as the formation of germanium-rich cluster or islands. Silylgermanes offer a promising strategy to circumvent these intrinsic limitations. The presence of a covalent Si–Ge bond within a single molecular precursor ensures that silicon and germanium are delivered to the substrate in a fixed stoichiometric relationship, potentially enabling more uniform incorporation at the surface. Moreover, many silylgermanes decompose readily under mild conditions, allowing high deposition rates even at comparatively low substrate temperatures. This combination of single-source stoichiometric control and enhanced low-temperature reactivity makes silylgermanes an appealing class of feedstocks for chemical vapor deposition, liquid phase deposition, and related techniques aimed at producing SiGe:H amorphous alloys, mixed semiconductors, and advanced thin-film architectures. Their potential enables both: fundamental material research and technologically relevant applications.^{46,124}

The most basic member of the Si–Ge hydride family is monosilylgermane (H₃SiGeH₃). Its first targeted preparation was reported by Cox and Varma in 1964, who achieved the formation of H₃SiGeH₃ in approximately 20% yield *via* the nucleophilic substitution of chlorogermane with potassium silanide (see Scheme 66). This study represents the earliest



Scheme 66 Synthesis of silylgermane (H₃GeSiH₃).

attempt to generate a Si–Ge single-bonded hydride under controlled conditions.¹²⁵

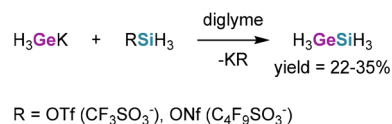
In the same year, Phillips and co-workers identified H₃SiGeH₃ as a minor product during silent electrical discharge experiments, although the hydride was obtained only in trace amounts (~2%).¹²⁶

An alternative approach to the silylation of germyl anions employs silyltriflate (H₃Si-OTf) or silylnonaflate (H₃Si-ONf) as highly electrophilic silylating agents (see Scheme 67). This approach was demonstrated by Sundermeyer and co-workers (1994) and later expanded by Kouvetakis and co-workers (2005). Using these reagents, H₃SiGeH₃ can be obtained in moderate yields ranging from 22–35%, representing a significant improvement over earlier methods based on halide replacement.^{46,127}

Sundermeyer and co-workers also demonstrated the synthesis of branched silylgermane with the general formula (SiH₃)_nGeH_{4-n} (*n* = 2–4). In their studies, a mixture of branched silylsilanides (SiH₃)_{3-n}SiNa (*n* = 0–2) was first generated by reacting sodium with monosilane in diglyme. Subsequent treatment of this anion mixture with monogermane induced a rearrangement in which the germanium atom migrated into the central position of the silyl framework, forming branched silylgermanides. Finally, silylation with H₃SiONf afforded the corresponding silylgermanes (see Scheme 68). However, the individual products could not be separated, and yields were therefore only estimated by gas chromatography, limiting the characterization of the mixture.¹⁸

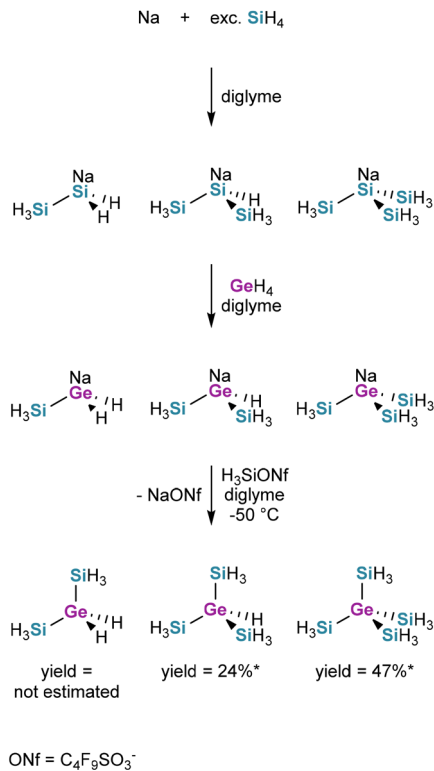
With a similar procedure, Ritter *et al.* synthesized the different silylgermanes with the general formula (H₃Ge)_nSiH_{4-n}. They also employed silyltriflates (H_nSi(OTf)_{4-n}) and silylnonaflates (H_nSi(ONf)_{4-n}), enabling the selective synthesis and isolation of the individual products (Scheme 69).¹²⁷

More recently, Stueger *et al.* introduced a complementary and highly selective approach to silylgermanes based on nucleophilic substitution reactions of well-defined silanide reagents.⁷³ Using lithium tris(silyl)silanide, LiSi(SiH₃)₃, the previously unknown germaisotetrasilane Ph₃GeSi(SiH₃)₃ could be synthesized in high yield on a multigram scale by reaction with Ph₃GeCl (see Scheme 70). The resulting Ph₃Ge-substi-

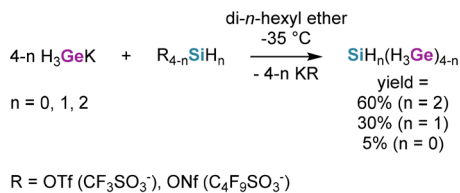


Scheme 67 Synthesis of silylgermane (H₃GeSiH₃) after treatment of KGeH₃ with SiH₃-OTf and SiH₃-ONf.

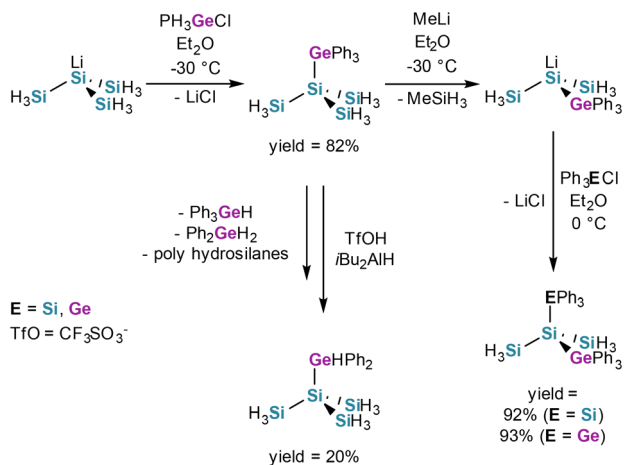




Scheme 68 3-Step-synthesis of silylgermanes. *No isolated yields; only determined via gaschromatography.



Scheme 69 Synthesis of germysilanes.



Scheme 70 Synthesis of different branched germasilicon hydrides.

tuted silyl-germanes serve as versatile intermediates for further derivatization. Selective treatment with methyllithium induces cleavage of a single Si-Si bond while preserving the Si-Ge linkage, generating lithium silanide species that can be reacted with other chlorosilanes or chlorogermanes. This strategy enables the efficient synthesis of higher substituted silylgermanes containing one or two Ph₃Ge groups in excellent yields. In contrast, attempts to access hydrogen rich silylgermanes *via* stepwise dephenylation at the germanium center using triflic acid followed by hydride reduction were significantly less selective.

It was also possible to obtain single crystals suitable for X-ray diffraction analysis (Fig. 11 and 12).

Mixed silylgermanes with preformed Si-Ge bonds were reported by Wagner and co-workers as part of a two-step synthesis strategy toward single-source precursors for Si-Ge materials.¹²⁸ In a first step, dichlorogermanes (R₂GeCl₂, R = Ph, *n*-Bu) were reacted with hexachlorosilane in the presence of catalytic [*n*-Bu₄N]Cl, generating bis(trichlorosilyl)-germanes Cl₃Si-GeR₂-SiCl₃ in high yields. The reaction proceeds *in situ* formation of the nucleophilic [SiCl₃]⁻ species, enabling efficient Si-Ge bond formation under mild conditions. Subsequent hydride reduction of the SiCl₃ groups with LiAlH₄ afforded the corresponding hydrosilanes H₃Si-GeR₂-SiH₃ in good to excellent yields (see Scheme 71).

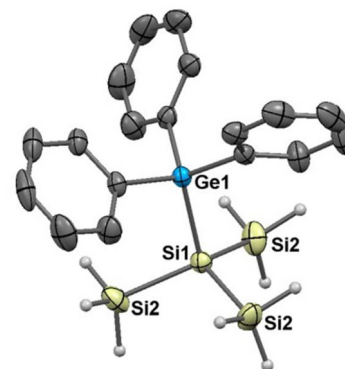


Fig. 11 Crystal structure of Si(GePh₃)(SiH₃)₃. Reproduced from ref. 73 with permission from American Chemical Society, © 2016.

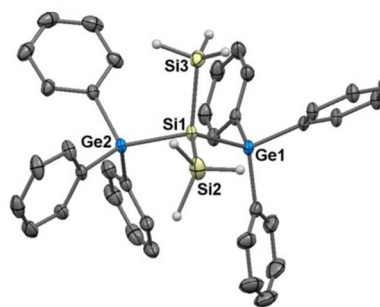
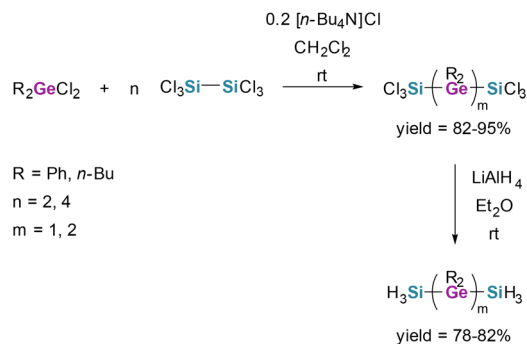


Fig. 12 Crystal structure of Si(GePh₃)₂(SiH₃)₂. Reproduced from Stueger *et al.*⁷³ with permission from American Chemical Society, ©2016.





Scheme 71 Formation of germysilanes with the general formula H₃Si-(GR)_m-SiH₃.

Moreover, Wagner and co-workers were successful in gaining crystals for X-ray diffractometry of intermediates and products (see Fig. 13). This modular approach provides convenient access to well-defined silylgermanes while avoiding preformed Si-Cl bonds and suppressing scrambling reactions typically encountered for fully hydride-substituted Si-Ge compounds.

Silylstannanes. Hydridic silylstannanes, defined by a direct Si-Sn bond, represent the heaviest mixed group-14 hydrides accessible to experimental investigation. In contrast to silylgermanes, whose synthesis, stability and application as single-source precursors have been explored in considerable detail, purely hydridic Si-Sn compounds remain rarely studied. The difference is mainly due to the high instability of Sn-H and Si-Sn bonds, which strongly limits the stability, isolation and handling of silylstannanes.

The simplest hydridic silylstannane, H₃Si-SnH₃, has been experimentally synthesized only under highly controlled conditions. The first targeted synthesis was reported by Wiberg and co-workers, who obtained the compound *via* low-temperature hydride reduction of prefunctionalized Si-Sn acetates or chlorides using LiAlH₄, generating ethereal solutions of the mixed hydride (see Scheme 72).¹²⁹

However, even under these conditions, H₃Si-SnH₃ was found to be stable only in highly diluted solutions below -80 °C, while enrichment or warming led to rapid decompo-

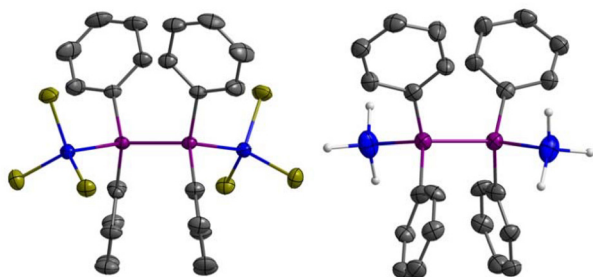
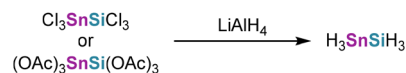


Fig. 13 Crystal structures of Cl₃Si-(GePh₂)₂-SiCl₃ and H₃Si-(GePh₂)₂-SiH₃. Reproduced from Wagner and co-workers¹²⁸ with permission from American Chemical Society, ©2022.

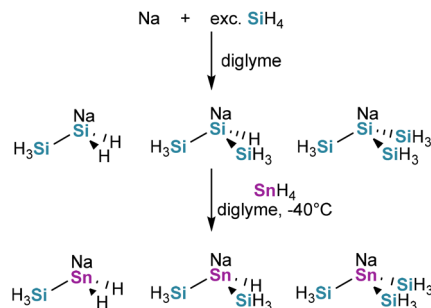


Scheme 72 Formation of silylstannane (H₃SnSiH₃) *via* the treatment of chloro-, or acetatesilylstannane with LiAlH₄. No yields reported.

sition into silane, metallic tin and hydrogen. Complementary matrix-isolation IR studies later provided spectroscopic evidence for hydridic Si-Sn species formed by insertion of atomic tin into silane, yielding HSnSiH₃ complexes stabilized in inert argon matrices at cryogenic temperatures.¹³⁰ Together, these studies demonstrate while hydridic silylstannanes can be generated and spectroscopically characterized, their extreme thermal lability fundamentally limits their isolation and practical application. Sundermeyer and co-workers were successful in generating silyl stannides with the general formula NaSn(SiH₃)_nH_{3-n} *via* the reaction of NaSi(SiH₃)_nH_{3-n} and SnH₄ at -40 °C (see Scheme 73).⁴⁷ In contrast to the corresponding silylgermanides systems (see Scheme 68), no further follow-up chemistry or reactivity studies were reported.

Functionalization with group 5 (synthesis of silylpnictogens)

Silylamines. Silicon nitride SiN_x is a workhorse in metal-oxide-semiconductors and memory as spacers, liners, hard masks, barriers, and passivation layers, but continued scaling demands conformal, low-temperature films with minimal C/O impurities that can degrade fixed charge, trap density, and leakage.⁷⁷ This has sharpened interest in aminosilanes composed exclusively of H, Si, and N, most notably silylamine (H₃SiNH₂), disilylamine (HN(SiH₃)₂), trisilylamine (N(SiH₃)₃), and the preceramic polymer perhydropolysilazane (PHPS); [SiH₂NH]_n. These molecules deliver direct Si-N bonds and high hydrogen content, enabling clean decomposition to volatile byproducts for example H₂ and SiH₄ and facilitating low-impurity SiN_x *via* CVD and plasma-enhanced atomic layer deposition ALD at lower temperatures.¹³¹⁻¹³⁴ In particular, N(SiH₃)₃ and related small H-Si-N aminosilanes can function as single-source Si-N precursors or as nitrogen-rich co-reactants with silane, improving nucleation and conformality in high-aspect-ratio features while avoiding carbon bearing ligands.¹³¹⁻¹³³ At the polymeric scale, PHPS offers a purely H-Si-N spin-on route that converts at comparatively low tempera-



Scheme 73 Generation of silylstannides.

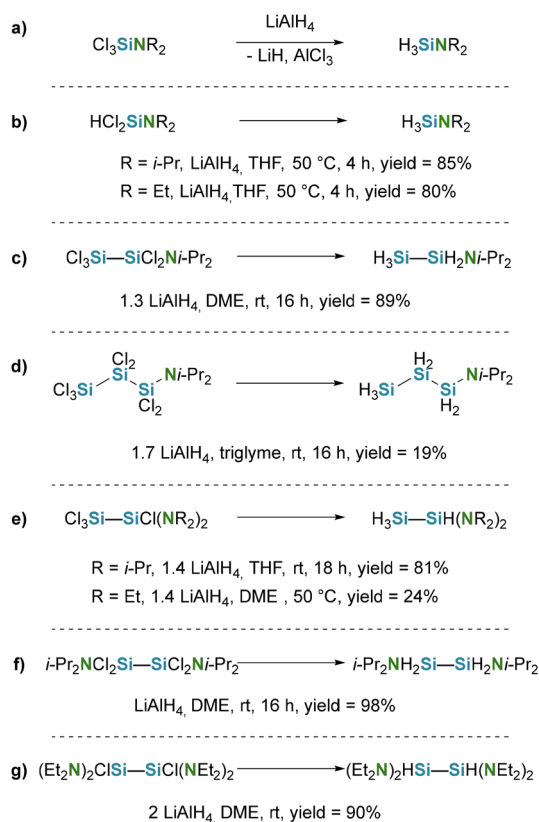


tures to dense SiN_x, supporting gap-fill, barriers, and passivation without introducing heteroatom contaminants.¹³⁴ Collectively, these H-Si-N-only chemistries target key integration needs at ≤400 °C, with ongoing work focused on tuning precursor volatility and reactivity, controlling incorporated hydrogen, and optimizing plasma densification for device reliability.^{131–133}

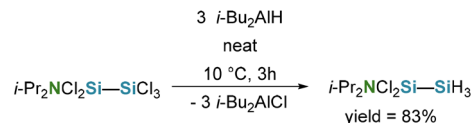
A widely used route to silylamines involves the reduction of silylamino halides. Although several hydride reagents are effective, LiAlH₄ is most commonly employed and usually Cl is the halide of choice. The employed silylamino halides are typically prepared by reacting silyl halides with the corresponding lithium amides,^{135,136} or *via* reaction of the respective amine with the silylhalide,¹³⁷ followed by hydride reduction to afford the target silylamines. A general reaction is given in Scheme 74, path a, several examples can be found in Scheme 74, path b to g.^{135–139}

Another widely used reductant for aminohalosilanes is diisobutylaluminium hydride. For example, reduction of diisopropylaminopentachlorodisilane with *i*-Bu₂AlH affords the partially halogenated diisopropylaminodichlorodisilane in 83% yield (see Scheme 75).¹⁴⁰

An alternative, synthetically straightforward route exploits nucleophilic substitution at halogenated silanes by the corresponding amines, typically generating the ammonium halide of



Scheme 74 General synthesis of silylamines from chlorosilanes and example synthesis (path a–g).

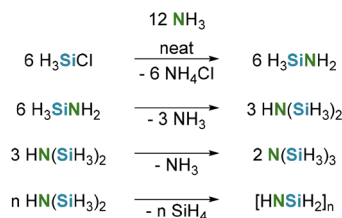


Scheme 75 Example synthesis of partially halogenated aminochlorosilanes using *i*-Bu₂AlH.

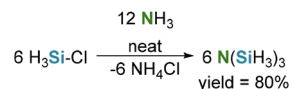
the amine as a byproduct.^{141–143} Stock and Somieski were able to obtain trisilylamine from the reaction between ammonia (NH₃) and H₃SiCl, notably if an excess of NH₃ was used the reaction was unselective, while excess H₃SiCl leads to the selective formation of trisilylamine.^{11,144,145} They reasoned that the reaction proceeds stepwise with silylamine and disilylamine (HN(SiH₃)₂) as intermediates, but could not isolate them and they observed the formation of a polymeric solid and SiH₄ (see Scheme 76).¹⁴⁴ Later Aylett and Hakim showed that disilylamine decomposes to trisilylamine and NH₃ and in the presence of NH₃ disilylamine decomposes to SiH₄ and a solid polymer.¹⁴⁶

Burg and Kuljian adapted Stocks and Somieskis synthesis by slowly mixing gaseous ammonia, from below, into H₃SiCl, resulting in the formation of trisilylamine in 80% yield (see Scheme 77). Notably they mentioned that slow addition of ammonia is necessary to obtain high yields and good selectivity.¹⁴⁷ When ammonia and H₃SiCl were condensed into a flask the reaction afforded trisilylamine in low yields.¹⁴⁸

Emeléus and Miller already employed this method in 1939 for the synthesis of dimethylsilylamine (Me₂NSiH₃), ethyldisilylamine (EtN(SiH₃)₂) and methylsilylamine (MeNSiH₃) (see Scheme 78, path a and b), though they only identified them and gave no yields.¹⁴¹ For instance, monochlorodisilane (H₃SiSiH₂Cl) undergoes substitution with diisopropylamine (*i*-Pr₂NH) to furnish diisopropylaminodisilane (H₃Si-SiH₂Ni-Pr₂), concomitant with formation of diisopropylammonium chloride (*i*-Pr₂NH₂Cl) (see Scheme 78, path c).¹⁴³ Both iso-

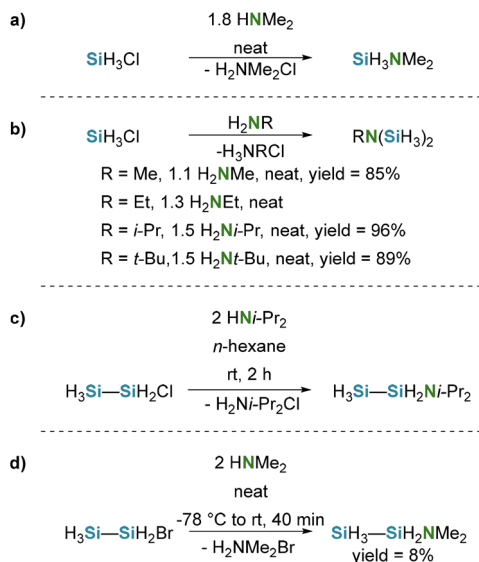


Scheme 76 Synthesis of trisilylamine from H₃SiCl and NH₃, according to Stock. No yield was reported.



Scheme 77 Synthesis of trisilylamine with gaseous ammonia and H₃SiCl, according to Burg.





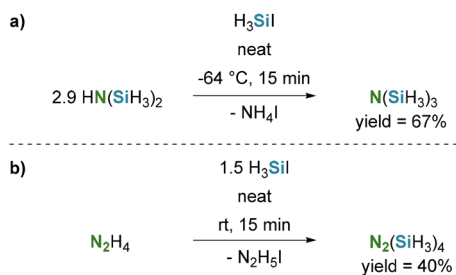
Scheme 78 Example synthesis of silylamines from halosilanes and amines (path a–d). When no yields are given for the product, no yield was reported.

propylamine (*i*-PrNH₂) and *t*-butylamine (*t*-BuNH₂) react with H₃SiCl to afford the corresponding disilylamines in good yields (see Scheme 78, path b),¹⁴² while monochlorodisilane reacts with diisopropylamine to give diisopropylaminodisilane.¹⁴⁹ Burg and Kuljian prepared methyl-disilylamine (MeN(SiH₃)₂) from methylamine (MeNH₂) and ammonia in 85% yield (see Scheme 78, path b).¹⁴⁷ Bromodisilane (H₃Si-SiH₂Br) reacts with dimethylamine (Me₂NH) to afford dimethylaminodisilane (H₃Si-SiH₂NMe₂) in 8% yield (see Scheme 78, path d).¹⁵⁰

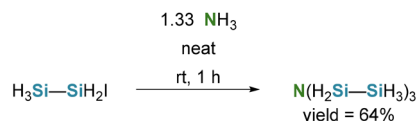
Furthermore, disilylamine reacts with H₃SiI to afford trisilylamine in 67% yield, when a slight excess of H₃SiI is used to afford trisilylamine the yield increases to 87%, though no experimental details were given (see Scheme 79, path a).^{146,151} Similarly, anhydrous hydrazine reacts with H₃SiI to give tetrasilylhydrazine in 40% yield, which is a strong reducing agent, but explodes in contact with air (see Scheme 79, path b).¹⁵²

Ward and MacDiarmid treated iododisilane with NH₃ to afford trisdisilylamine in 64% yield (see Scheme 80).¹⁵³

Diaminosilylamines, such as *t*-BuN(SiH₂NMe₂)₂, can be obtained from dichlorosilane (H₂SiCl₂) in a two-step synthesis



Scheme 79 Synthesis of trisilylamine (path a) and tetrasilylhydrazine (path b) using H₃SiI.



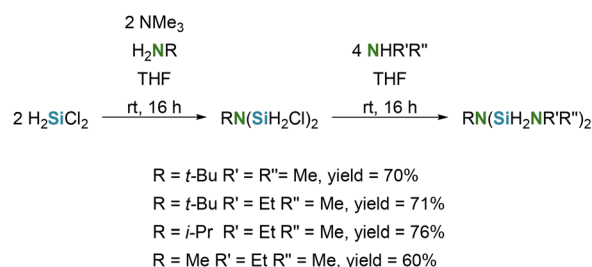
Scheme 80 Synthesis of trisdisilylamine from monoiododisilane and NH₃.

in good yields. H₂SiCl₂ reacts with the respective primary amine, either in excess¹⁵⁴ or under use of a aiding base like trimethylamine (NMe₃),¹⁵⁵ for example *t*-BuNH₂ to obtain a dichlorosilylamine, which subsequently reacts with an amine to afford the respective diaminosilylamine (see Scheme 81).^{154,155}

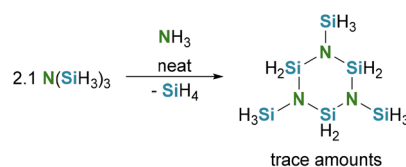
Wells and Schaeffer investigated the reaction of trisilylamine with ammonia by condensing both reagents into a flask and allowing them to react in the liquid phase. The reaction afforded *N,N',N''*-trisilylcyclotrisilazane only in trace amounts, however, multiple runs provided sufficient material for characterization. They reasoned that ammonia catalyses the elimination of SiH₄ from trisilylamine (see Scheme 82).¹⁴⁸

Various azapolysilanes can be prepared by reacting diisopropylaminodisilane with primary amines, such as *t*-BuNH₂. Alternatively by the reaction of chlorodisilane with primary amines in the presence of triethylamine as a base, or by the treatment of 1,2-dichlorodisilane (ClH₂Si-SiH₂Cl) with primary amines and triethylamine (NEt₃) (see Scheme 83).¹⁵⁶

Furthermore, alkalimetal amides, such as sodium amide, are suitable reagents to form silylamines *via* reaction with silylhalides. After formation of the respective sodium amide a silylhalide is added affording the formation of silylamines, this approach allows for the synthesis of diisopropylaminosilane (*i*-Pr₂NSiH₃) (see Scheme 84).¹⁵⁷

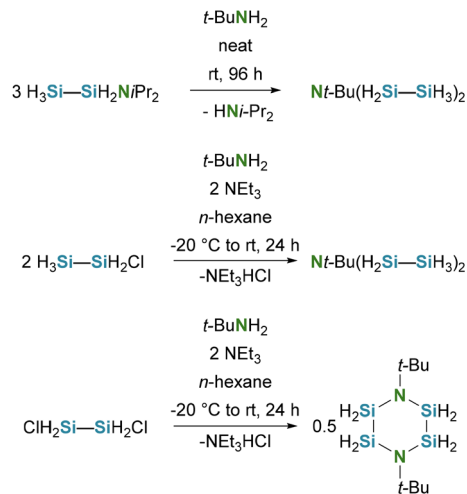


Scheme 81 Synthesis of diaminosilylamines from H₂SiCl₂ and the respective amines.

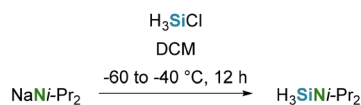


Scheme 82 Reaction between trisilylamine and ammonia.





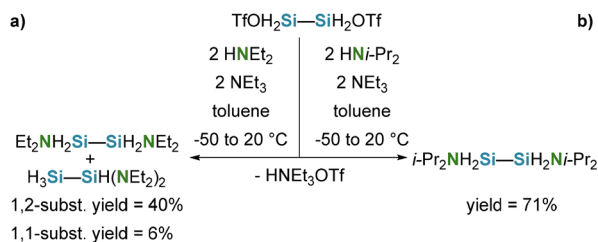
Scheme 83 Example synthesis of silylamines from diisopropylaminodisilane, monochlorodisilane and 1,2-chlorodisilane. No isolated yields were given.



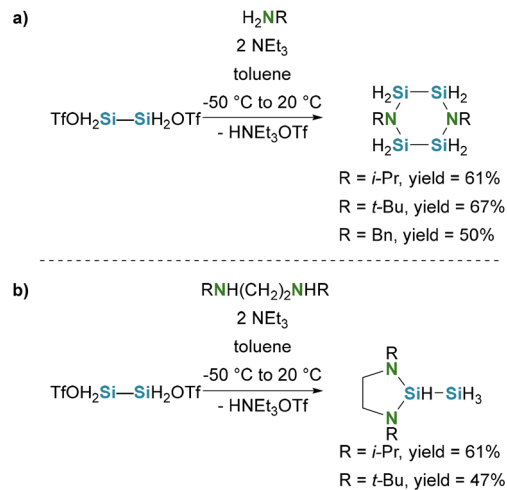
Scheme 84 Synthesis of silylamines from alkali metal amides and silyl halides. No isolated yields were given.

Schmidbauer and co-workers accessed 1,1- and 1,2-diaminodisilanes from solutions of 1,2-disilanediylditriflate. The solution of 1,2-disilanediylditriflate is afforded from di-*p*-tolylidisilane and triflic acid and reacts with solutions of the respective amine and triethylamine to afford the 1,2-diaminodisilanes (see Scheme 85, path a and b). Notably, in the case of diethylamine (HNEt_2) the 1,1-substituted diethylaminodisilane is also formed (see Scheme 85, path a), whereas the 1,1-diisopropylaminodisilane is not observed (see Scheme 85, path b).¹⁵⁸

When primary amines are employed, the reaction furnishes six-membered cyclic aminosilanes containing two disilyl units, rather than the 1,1- and 1,2-substituted linear diaminodisilanes obtained with secondary amines (see Scheme 86, path a). When 1,4-difunctional diamines are used instead, the reaction yields five-membered cyclic compounds bearing an exocyclic silyl substituent (see Scheme 86, path b).¹⁵⁸



Scheme 85 Synthesis of diaminodisilanes from disilanediylditriflate using secondary amines (path a and b).

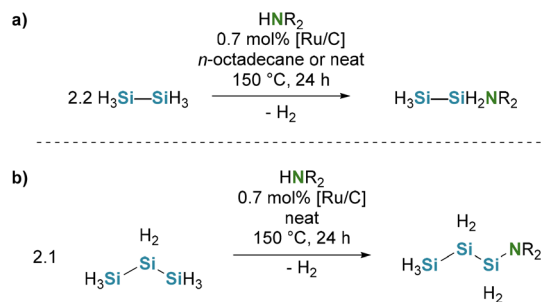


Scheme 86 Synthesis of cyclic silylamines from disilanediylditriflate. (path a and b)

Dehydrogenative coupling offers an attractive, atom-economical route to silylamines. A variety of catalysts promote the coupling of amines with hydrosilanes, including the Lewis acid trispentafluorophenylborane ($\text{B}(\text{C}_6\text{F}_5)_3$),¹⁵⁹ transition metal systems such as triruthenium dodecacarbonyl ($\text{Ru}_3(\text{CO})_{12}$),¹⁶⁰ main-group reagents such as di-*n*-butylmagnesium ($n\text{-Bu}_2\text{Mg}$),¹⁶¹ Mn based catalysts¹⁶² and Zn based catalysts.¹⁶³ Sanchez *et al.* reported the dehydrogenative coupling of amino- and diaminosilanes derived from disilane and trisilane using ruthenium on carbon (Ru/C) as the catalyst, although only non-isolated yields were provided (see Scheme 87, path a and b).¹⁶⁴

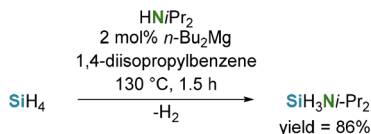
SiH_4 can be dehydrogenatively coupled with diisopropylamine using di-*n*-butylmagnesium $n\text{-Bu}_2\text{Mg}$ as catalyst, as shown by Maddock *et al.* (see Scheme 88).^{159,161}

Moreover, Rekken employed Zn-based catalysis to achieve dehydrogenative coupling, affording diisopropylaminodisilane and bisdiisopropylaminodisilane. They further demonstrated that Zn-based catalysis is applicable to SiH_4 , albeit with low conversions. No isolated yields were reported, the product compositions were determined by GC-FID, and diisopropylamine was used in large excess (see Scheme 89).¹⁶³

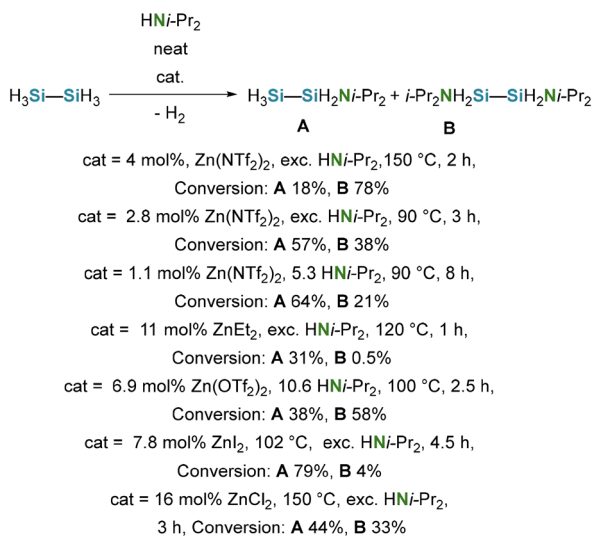


Scheme 87 Synthesis of aminodisilane (path a) and aminotrisilane (path b) using Ru/C as catalyst. Only non-isolated yields were reported. Several R groups can be employed.





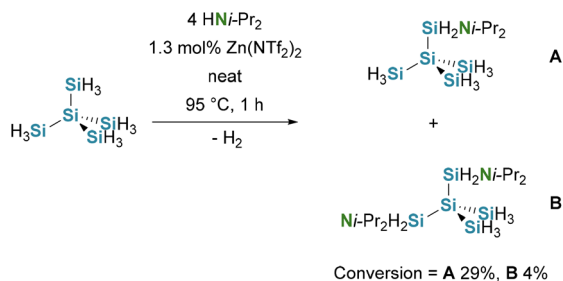
Scheme 88 Dehydrogenative coupling of SiH₄ and diisopropylamine, using *n*-Bu₂Mg.



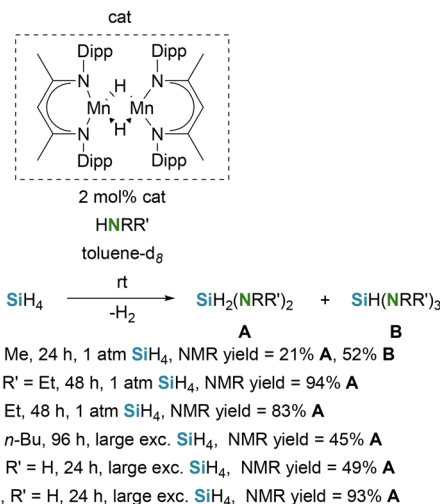
Scheme 89 Dehydrogenative coupling of disilane with diisopropylamine, using Zn based catalysts. Only conversions were reported.

Using Zn(NTf₂)₂ as a catalyst enabled the dehydrogenative coupling to afford diisopropylaminoneopentasilane, however, only crude product conversions determined by GC-FID were reported (see Scheme 90).¹⁶³

In 2022, Trovitch and co-workers demonstrated that the dehydrogenative coupling of SiH₄ with primary and secondary amines proceeds using the manganese-based catalyst [(^{2,6}-iPr₂PhBDI)Mn(μ-H)]₂.¹⁶² With primary or secondary amines, di- and trisubstituted aminosilanes are obtained, and the steric demand of the amine strongly influences the reaction time. Diamines and triamines furnish polycarbosilazanes, whereas ammonia affords perhydropolysilazane (see Scheme 91).¹⁶²



Scheme 90 Dehydrogenative coupling of neopentasilane with Zn(NTf₂)₂ and diisopropylamine. Only conversions were reported.

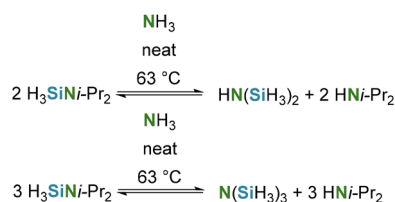


Scheme 91 Synthesis of aminosilanes from SiH₄ via Mn based catalysis.

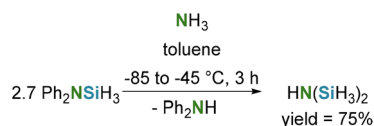
A different approach to obtain aminosilanes is the amine exchange pathway. Various aminosilanes are accessible *via* transamination with amines at room temperature or elevated temperature. The educts of choice for transaminations in the literature are diisopropylaminosilanes. For example, diisopropylaminosilane forms disilylamine with NH₃ and subsequently forms trisilylamine (see Scheme 92).¹⁵⁹

Aylett and Hakim reported the synthesis of disilylamine in 75% yield by treating diphenylaminosilane (Ph₂NSiH₃) in toluene at low temperature with ammonia (see Scheme 93).¹⁵¹

Transamination of diisopropylaminosilane proceeds with a broad range of secondary amines; with primary amines, the corresponding disilylamines are obtained, while polyfunctional amines undergo silylation at multiple amino groups (see Scheme 94, path a to c).¹⁴³

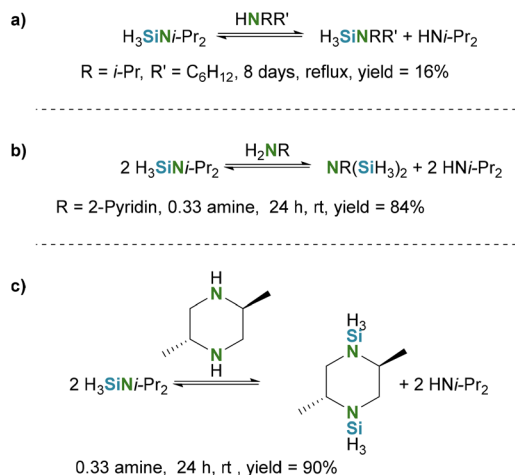


Scheme 92 Synthesis of di- and trisilylamine, *via* transamination of diisopropylamine. No detailed ratios of the reagents were given; therefore, the overall equation is given.



Scheme 93 Synthesis of disilylamine *via* transamination of Ph₂NSiH₃ with NH₃.

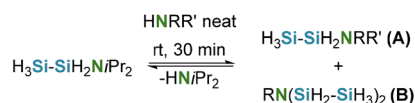




Scheme 94 Example transaminations of diisopropylaminosilane (path a–c).

This methodology extends to larger aminosilane frameworks, for example, Zhou *et al.* employed diisopropylaminodisilane in transamination reactions to access a range of monosubstituted as well as bisubstituted (disilanyl)amines, although only GC-MS conversions were reported and no isolated yields (see Scheme 95 and Table 6).¹⁶⁵

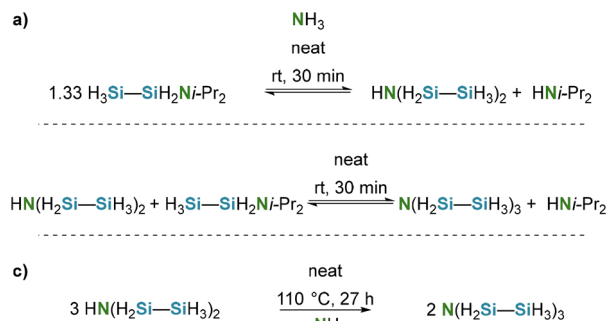
Using an NH₃ : diisopropylaminodisilane ratio of 1 : 3 gives 99% conversion to bisdisilanylamine; with an additional equivalent of diisopropylaminodisilane, trisdisilanylamine is obtained.¹⁶⁵ Furthermore, Rekken *et al.* obtained trisdisilanylamine by thermal degradation of bisdisilanylamine at 110 °C (see Scheme 96, path a to c).¹⁶⁶



Scheme 95 Transamination of diisopropylaminosilane. For conversions see Table 6. R = organic rest, R' = H or organic rest, see Table 6.

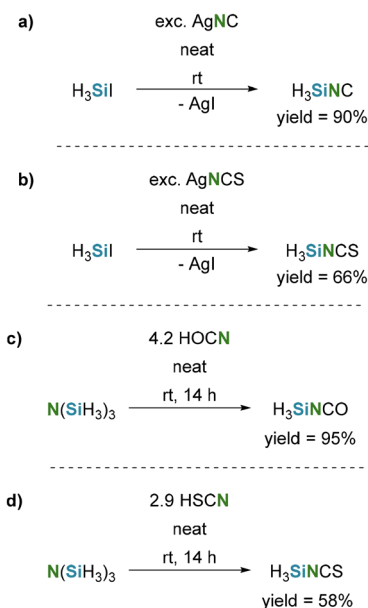
Table 6 Conversions of transamination reactions

Amine (2 eq.)	GC conversion [%]	
	A	B
Diethyl	38	—
Methyl	69	22
Ethyl	73	23
Propyl	62	21
Butyl	71	25
2-Aminobutane	96	1
Pentylamine	51	13
2-Aminopentane	95	1
1,2-Dimethylpropyl	98	—
<i>t</i> -Pentyl	83	—
Cyclopentyl	84	12
Cyclohexyl	92	5
Aniline	74	—
<i>o</i> -Toluidine	38	—



Scheme 96 Transamination of diisopropylaminosilane affording bis- and trisdisilanylamine and thermal degradation of bisdisilanylamine (path a–c). No isolated yields were reported. For the thermal redistribution of bisdisilanylamine only the general equation is given.

Silyl iso-cyanide (H₃SiNC) was previously prepared but wrongfully assigned as silyl cyanide (H₃SiCN) and no detailed analysis of its properties was carried out.¹⁶⁷ MacDiarmid was able to obtain and analyze both silyl iso-cyanide and silyl isothiocyanate (H₃SiNCS). The treatment of silver cyanide (AgNC) with H₃SiI at room temperature afforded silyl iso-cyanide in 90% yield and by reaction with mercuric cyanide at elevated temperatures, though no yield was reported (see Scheme 97, path a). Silyl isothiocyanate was afforded *via* the reaction between H₃SiI and silver thiocyanate (AgNCS) in 66% yield (see Scheme 97, path b).¹⁶⁸ Furthermore, the reaction between trisilylamine and cyanic acid (HOCN) affords silyl iso-cyanate (H₃SiNCO) in 95% yield, and with thiocyanic acid (HSCN), it leads to the formation of silyl isothiocyanate in 58% yield (see Scheme 97, path c and d).¹⁶⁹



Scheme 97 Synthesis of silyl iso-cyanide, silyl iso-cyanate and silyl isothiocyanate from H₃SiI (path a and b) and trisilylamine (path c and d).



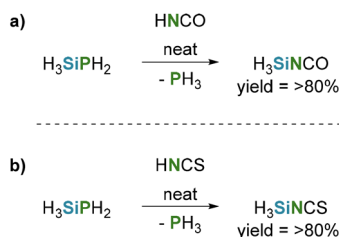
Gaseous silylphosphane (H_3SiPH_2) reacts readily with cyanic acid as well as thiocyanic acid affording silyl iso-cyanate or silyl iso-thiocyanate in yields greater than 80% (see Scheme 98, path a and b).¹⁷⁰

Disilylsulfide ($\text{S}(\text{SiH}_3)_2$) is a viable feedstock for the synthesis of silyl i-thiocyanate. In combination with silver thiocyanate (AgNCS), it afforded H_3SiNCS in 86% yield (see Scheme 99). When instead cyanogen chloride was employed, the reaction led to a mixture of disilylsulfide, silyl cyanide, sulfur, and silyl i-thiocyanate, but the mixture proved to be inseparable.¹⁷¹

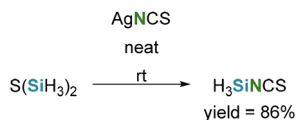
Ebsworth and Mays reported the synthesis of silyl i-cyanate *via* treatment of silvercyanate (AgOCN) and powdered glass with iodasilane vapor with an overall yield of 20% (see Scheme 100).¹⁷²

Silylamines such as $\text{N}(\text{SiH}_3)_3$ and $\text{N}(\text{H}_2\text{Si}-\text{SiH}_3)_3$ serve as precursors to silylaminoboranes. Trisilylamine reacts quantitatively at low temperature with boron trihalides BX_3 ($\text{X} = \text{Cl}, \text{F}$) to afford the corresponding disilylaminohaloboranes.^{147,173} Witz and Sujishi showed that boron trifluoride (BF_3) forms adducts with trisilylamine, methyltrisilylamine, and dimethylsilylamine, these adducts decompose at room temperature to give silyl fluoride and the corresponding silylaminoborane (see Scheme 101, path a and b).¹⁷³

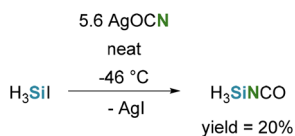
Furthermore, trisilylamine reacts readily with bromodiborane ($\text{B}_2\text{H}_5\text{Br}$) at low temperature to afford disilylaminoborane



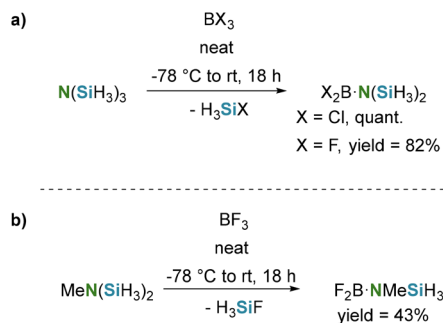
Scheme 98 Synthesis of silyl iso-cyanate (path a) and silyl iso-thiocyanate (path b). No amounts of the used reagents were given.



Scheme 99 Synthesis of silyl i-thiocyanate from disilylsulfide. The amount of AgNCS used was not reported.



Scheme 100 Synthesis of silyl i-cyanate from iodasilane and silvercyanate.

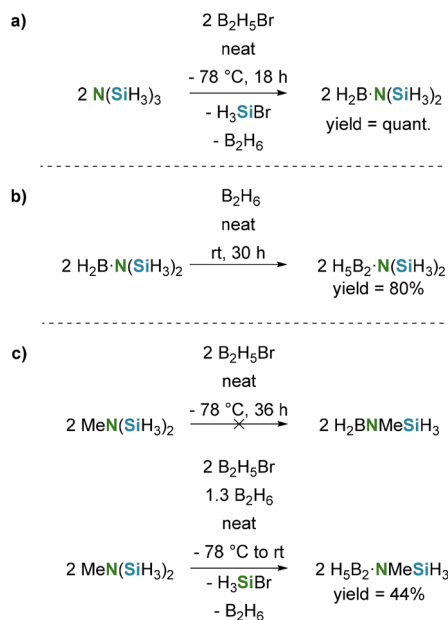


Scheme 101 Synthesis of bisilylaminodichloro- and bisilylaminodifluoroborane (path a and b).

in quantitative yield; subsequent treatment with diborane furnishes bisilylaminodiborane in 80% yield (see Scheme 102, path a and b).¹⁴⁷ The same methodology extends to methyltrisilylamine, but instead of the desired methylsilylaminoborane it yields methylsilylaminodiborane in 20% yield, accompanied by formation of H_3SiBr , SiH_4 and B_2H_6 (see Scheme 102, path c). The yield was improved to 44% by adding 1.3 equivalents of diborane, an effect attributed to reduced disproportionation of the intermediate methylsilylaminoborane (see Scheme 102, path d).¹⁴⁷

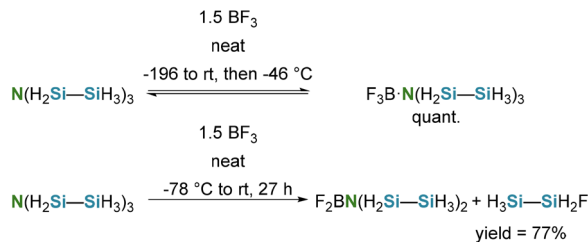
MacDiarmid and Abedini formed the corresponding adduct of trisdisilanylamine with BF_3 at low temperature; upon heating, the adduct decomposed to afford bisdisilanylaminofluoroborane and fluorodisilane, although only the isolated yield of the fluorodisilane was reported (see Scheme 103).¹⁵⁰

Norman and Scantlin reported that boranes catalyze the condensation of trisilylamine and methyltrisilylamine to give

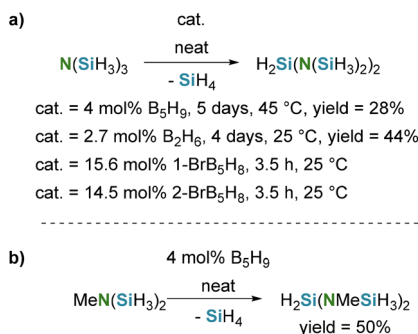


Scheme 102 Reactions between trisilylamine (path a and b) and methyltrisilylamine (path c and d) with bromodiborane and subsequent reaction of the formed silylaminoboranes with diborane.





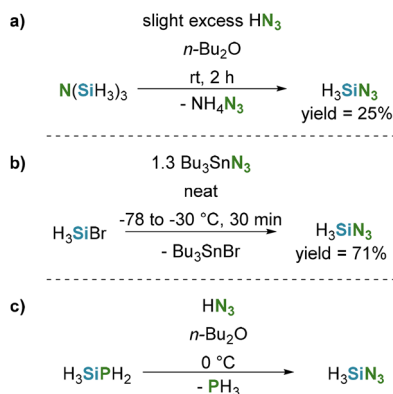
Scheme 103 Synthesis of $\text{F}_2\text{BN}(\text{SiH}_2\text{SiH}_3)_2$. In the second reaction only the yield for fluorodisilane was reported.



Scheme 104 Borane catalyzed condensation of trisilylamine (path a) and methylidisilylamine (path b). Path (a) no isolation was performed under catalysis by 1- and 2- BrB_5H_8 .

the corresponding silazanes with simultaneous liberation of SiH_4 , in good yields (see Scheme 104, path a and b). When B_2H_6 or B_5H_9 is used, the reaction affords $\text{H}_2\text{Si}(\text{N}(\text{SiH}_3)_2)_2$ with only minor formation of higher condensation products $\text{Si}_7\text{N}_3\text{H}_{16}$. In contrast 1- and 2- BrB_5H_8 catalyze much faster reactions that are more difficult to control, leading to increased formation of $\text{Si}_7\text{N}_3\text{H}_{16}$.¹⁷⁴

Silyl azide (H_3SiN_3) can be prepared by reacting trisilylamine with hydrazoic acid (HN_3) in $n\text{-Bu}_2\text{O}$, however, it is unstable at room temperature and slowly decomposes with evolution of SiH_4 (see Scheme 105, path a).¹⁷⁵ Alternatively,



Scheme 105 Synthesis of silyl azide (path a–c). No yield or experimental details were reported for the reaction of H_3SiPH_2 with hydrazoic acid.

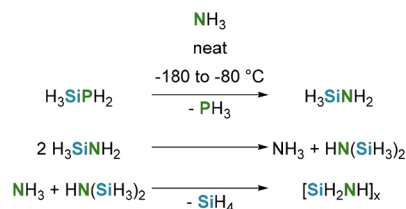
treatment of H_3SiBr with tributyltinazide (Bu_3SnN_3) affords silyl azide in 71% yield (see Scheme 105, path b).¹⁷⁶ A further route involves treating H_3SiPH_2 with a dilute solution of hydrazoic acid, though no yield was reported (see Scheme 105, path c).¹⁷⁰

Fritz and Berkenhoff investigated the reaction between silylphosphane and NH_3 and concluded that at $-80 \text{ }^\circ\text{C}$ silylamine forms and subsequently converts to polymeric solids of the type $[\text{SiH}_2\text{NH}]_x$. To support this interpretation, they also examined the reaction of H_3SiCl and NH_3 , which led to the same solids, although the proposed intermediates could not be directly observed (see Scheme 106).¹⁷⁷

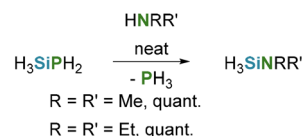
Norman and Jolly further investigated the H_3SiPH_2 and NH_3 system. They found that depending on reaction time, temperature, and ratio of H_3SiPH_2 to NH_3 , a complex product mixture is formed. At $-78 \text{ }^\circ\text{C}$ to $-63 \text{ }^\circ\text{C}$ and a ratio above 6 : 1 $\text{H}_3\text{SiPH}_2 : \text{NH}_3$ mainly PH_3 and $\text{HN}(\text{SiH}_3)_2$ are formed in a 2 : 1 ratio, with small amounts of $\text{N}(\text{SiH}_3)_3$ and SiH_4 from subsequent reactions.¹⁷⁸ When the reaction was carried out with a ratio of $\text{H}_3\text{SiPH}_2 : \text{NH}_3$ below 6 : 1 or at higher temperatures, only a complex product mixture was observed, notably small amounts of the silazanes $\text{SiH}_2(\text{NHSiH}_3)_2$ and $(\text{SiH}_3)_2\text{NSiH}_2\text{NHSiH}_3$ were formed. They also could not find direct evidence for the formation of H_3SiNH_2 .¹⁷⁸

Glidewell further examined the reactions between H_3SiPH_2 and amines and imines. In the gas phase, methylamine and diethylamine react with PH_3 to give the corresponding silylamines in quantitative yield. In contrast, methylamine does not react with gaseous H_3SiPH_2 and with condensed H_3SiPH_2 only a white polymeric solid is obtained (see Scheme 107).¹⁷⁰

Treatment of cyanamide (CH_2N_2) with H_3SiPH_2 or with disilylsulfide affords disilylcarbodiimide ($\text{C}(\text{NSiH}_3)_2$) in excellent yields (see Scheme 108, path a and b). However, the yield of the $\text{S}(\text{SiH}_3)_2$ reaction was not explicitly reported. In contrast,

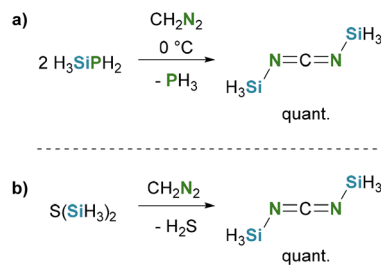


Scheme 106 Ammonolysis of H_3SiPH_2 according to Fritz. No details about the amounts of H_3SiPH_2 and NH_3 as well as reaction time were given. For the following reaction of the formed H_3SiNH_2 only the general formula is given.



Scheme 107 Synthesis of silylamines from H_3SiPH_2 with amines. The amounts of reagents used were not given.





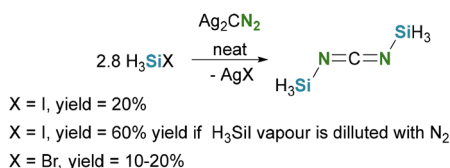
Scheme 108 Synthesis of disilylcarbodiimide (path a and b). No experimental details were given, therefore only the general formula is given.

trisilylphosphane ($\text{P}(\text{SiH}_3)_3$) gives the carbodiimide only in poor yield with concomitant decomposition of $\text{P}(\text{SiH}_3)_3$, and SiH_3PMe_2 undergoes complete decomposition under the reaction conditions.¹⁷⁰

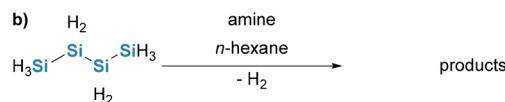
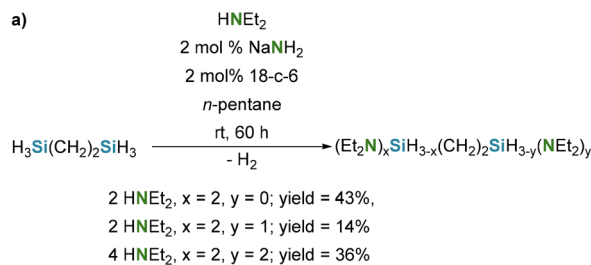
Passing H_3SiI vapor over powdered glass wool and silver cyanamide (Ag_2CN_2) led to the formation of disilylcarbodiimide in 20% yield, with SiH_4 , and HCN as side products. Neither using PbCN_2 , or H_3SiBr with Ag_2CN_2 improves the yields and results in 10–20% yield of disilylcarbodiimide. Notably, H_3SiI and undiluted Ag_2CN_2 led to an explosion.¹⁷⁹ When H_3SiI vapor is diluted with N_2 , the yield of the reaction is increased to up to 60%.¹⁸⁰ While it was first unclear if disilylcyanamide $\text{NCN}(\text{SiH}_3)_2$ or disilylcarbodiimide was formed during the reaction, later IR spectra studies¹⁸⁰ and gas phase electron diffraction¹⁸¹ showed that disilylcarbodiimide is formed (see Scheme 109).

Schmidbaur and Schuh employed NaH and NaNH_2 in the presence of 18-c-6 as a phase-transfer catalyst to convert 1,4-disilabutane and *n*-tetrasilane into their corresponding aminosilanes (see Scheme 110, path a and b). While 1,4-disilabutane reacts with diethylamine using the NaNH_2 /18-c-6 system in pentane to afford the aminosilanes with evolution of H_2 , *n*-tetrasilane undergoes cleavage, giving mixtures of smaller aminosilanes and higher silanes. They found that NaH alone does not catalyze these reactions. When pyrrole was used with *n*-tetrasilane instead of diethylamine, the main product was $\text{Si}(\text{NC}_4\text{H}_4)_4$, accompanied by formation of trisilane.¹⁸²

Perhydropolysilazanes such as bisdisilylamino silane are obtainable from trisilylamine with a suitable catalyst, such as $\text{B}(\text{C}_6\text{F}_5)_3$ or PdCl_2 (for more examples see Scheme 111 and Table 7). Though it is not stated if the product obtained is pure and no number average molecular weight M_n for the products was given. When the reaction is carried out with

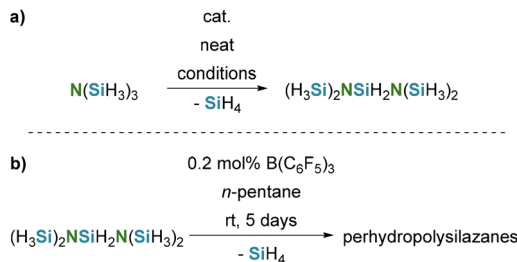


Scheme 109 Synthesis of disilylcarbodiimide from halosilanes and Ag_2CN_2 .



Entry A) 22 HNEt₂, 2 mol% NaH rt,
 products of A: yield = 2% $\text{H}_2\text{Si}(\text{NEt}_2)_2$, 30% mixture $\text{Si}_n\text{H}_{2n+2}$ n = 5,6,7
 Entry B) 0.96 HNEt₂, 3 mol% NaNH₂, 3 mol% 18-crown-6, reflux,
 products of B: yield = 5% $\text{H}_2\text{Si}(\text{NEt}_2)_2$, 8% Si_5H_{12}
 Entry C) HNEt₂, 5 mol% NaH, then 5 mol% NaNH₂, -196 °C to rt, neat, 17 h,
 products of C: yield = 61% $\text{H}_2\text{Si}(\text{NEt}_2)_2$, 5% mixture $\text{Si}_n\text{H}_{2n+1}\text{NEt}_2$ n = 2,3,4
 Entry D) Pyrrole, 3 mol% NaNH₂, 3 mol% 18-crown-6, rt,
 products of D: yield = 60% $\text{Si}(\text{NC}_4\text{H}_4)_4$

Scheme 110 Reactions of 1,4-disilabutane (path a) and *n*-tetrasilane (path b) with amines under NaNH_2 catalysis.



Scheme 111 Synthesis of bis(disilylamino)silane and perhydropolysilazanes. Yields for path a are given in Table 7. No yields or molecular weight distributions were given for path b.

Table 7 Synthesis of bis(disilylamino)silane

Catalyst	Catalyst loading [mol%]	Cocatalyst [mol%]	T [°C]	t [h]	Yield [%]
Pt/C	5	NEt ₃ 31%	100	18	48
Pt/C	5	NMe ₂ Et 25%	100	4	36
Pt/C	5	NMe ₂ Et 25%	100	22	46
Pt/C	0.4	NMe ₂ Et 25%	100	4	31
Pt/C	0.4	NMe ₂ Et 25%	105	25	39
[RuCl ₂ ((AMPY) (DPPB))]	0.4	—	100	18	10
[RuCl ₂ ((AMPY) (DPPB))]	0.4	NEt ₃ 30%	100	18	83
[RhCl(PPh ₃) ₃]	0.4	NMe ₂ Et 25%	100	1	86
[(R,R)-teth-TsDpenRuCl]	0.6	NMe ₂ Et 25%	100	1.5	83
Ru ₃ (CO) ₁₂	1.1	NMe ₂ Et 25%	80	1	80

increased catalyst loading, M_n increases and the ratio of SiH_2 : SiH_3 of the products increases as well.¹⁸³

Silylphosphanes. For further information about silylphosphanes containing partially hydrated and fully non hydrated



silyl groups Fritz and Scheer wrote an excellent review, which is beyond the scope of fully hydrated silylphosphanes of this review.¹⁸⁴

The composition of silylphosphane precursors is especially relevant for semiconductor applications. Silylphosphanes consisting only of P, Si, and H are attractive for semiconductor processing because they are carbon- and halogen-free and decompose to benign H₂, reducing impurity incorporation that degrades carrier lifetimes and interface quality.^{185,186} Their preformed Si–P bonds make them single-source reagents that deliver Si and P together, enabling *in situ* n-type doping of Si/Ge and the growth of Si–P materials with improved dopant incorporation efficiency and spatial uniformity compared with separate feeds.^{186,187}

The first reported silylphosphane H₃SiPH₂ was prepared by Fritz, in 1952, *via* thermal decomposition of equimolar amounts of SiH₄ and PH₃, proceeding through a radical mechanism.^{12,53,188} Furthermore, under the reaction conditions, less volatile species such as H₂Si(PH₂)₂ and SiP₂ are generated.^{189,190} This pathway enabled the first investigations into the properties of silylphosphanes but was problematic for the synthesis of H₃SiPH₂ in a preparative scale, due to the further decomposition of H₃SiPH₂ towards SiP₂ during the reaction (see Scheme 112).¹⁹⁰

Sabherwal and Burg adapted the thermal decomposition conditions to a decreased temperature of 300 °C in the presence of trace amounts of I₂, leading to a significantly increased yield of 61% for H₃SiPH₂.¹⁹¹ The enhanced yield was attributed to a lower degree of product degradation, due to the lower temperature and to the formation of H₃SiI, which reacts with PH₃ to give H₃SiPH₂ and HI. The formed HI then reacts with SiH₄ to regenerate H₃SiI.¹⁹¹ Another early report of silylphosphanes was made by Aylett *et al.* in 1955, who demonstrated that H₃SiI reacts with white phosphorous to afford P₂SiH₃ with various side products, most notably P(SiH₃)₃, which they could not characterize fully. They further showed that H₃SiPH₂ can be formed *via* reaction of NMe₃SiH₃I with PH₃.¹³

In addition to the thermal route photochemistry was also investigated to yield silylphosphanes. Blazejowski obtained small quantities of H₃SiPH₂ by IR irradiation of a PH₃/SiH₄ mixture, photosensitized by SiF₄,¹⁹² later by irradiation of a PH₃/SiH₄ mixture,¹⁹³ and by photolysis of PH₃/SiH₄ mixtures at 147 nm.¹⁹⁴ The formation of H₃SiPH₂ and hydrosilanes such as disilane and trisilane is rationalized by the generation of silylene groups that insert into Si–H and P–H bonds.^{192,193}

Another alternative approach towards silylphosphanes such as H₃SiPH₂ employed electrical discharge methods. Mixtures of SiH₄ and PH₃ form silylphosphanes in an ozonizer-type silent

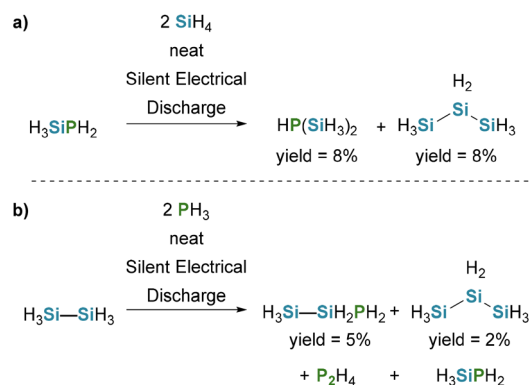
electrical discharge tube.^{195,196} Using this setup Jolly and Gokhale obtained HP(SiH₃)₂ from a mixture of H₃SiPH₂ and SiH₄.^{196,197} Furthermore ozonizer-type silent electrical discharge tubes have also facilitated the preparation of H₃SiSiH₂PH₂ from disilane and PH₃. However the silent electrical discharge approach has proven to be unsuitable for larger scales, due to the low yields and poor selectivity (see Scheme 113, path a and b).^{196,197}

Halide mediated exchange reactions between silylphosphane and halosilanes were also investigated in order to obtain silylphosphanes. Drake *et al.* obtained disilanylphosphane (H₃SiSiH₂PH₂) *via* exchange reaction between H₃SiPH₂ and disilylhalides (see Scheme 114).^{198,199}

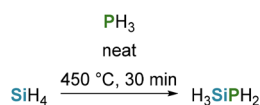
They further employed SiH₂Cl₂ and SiHCl₂SiH₂Cl with H₃SiPH₂ to synthesize the chlorinated silylphosphanes SiH₂ClPH₂ and SiHCl₂SiH₂PH₂ (see Scheme 115, path a and b). Whereas 1,1-dichlorodisilane does not react with H₃SiPH₂, 1,2-dichlorodisilane undergoes facile conversion to 1,2-diphosphinodisilane *via* the intermediate SiH₂ClSiH₂PH₂ (see Scheme 115, path c). Furthermore 1,1,2-trichlorodisilane affords 1,1-dichloro-2-phosphinodisilane.¹⁹⁹

Silylphosphane synthesis can also be achieved through nucleophilic substitution of silyl halides by alkali metal phosphides. Amberger and Boeters demonstrated that the direct reaction of bromosilane with potassium dihydrophosphide (KPH₂) does not afford H₂PSiH₃, but instead leads to the synthesis of P(SiH₃)₃ (see Scheme 116).²⁰⁰

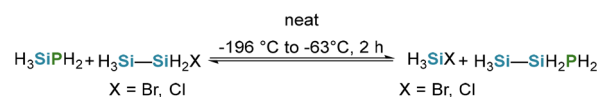
A sequence of transmetalation steps results in the formation of P(SiH₃)₃ steps involving mono- and disilylated intermediates (see Scheme 117).^{16,200–202}



Scheme 113 Synthesis of HP(SiH₃)₂ (path a) and Si₂H₅PH₂ (path b) *via* silent electrical discharge. No yields for P₂H₄ and H₃SiPH₂ were given in the reaction of disilane.

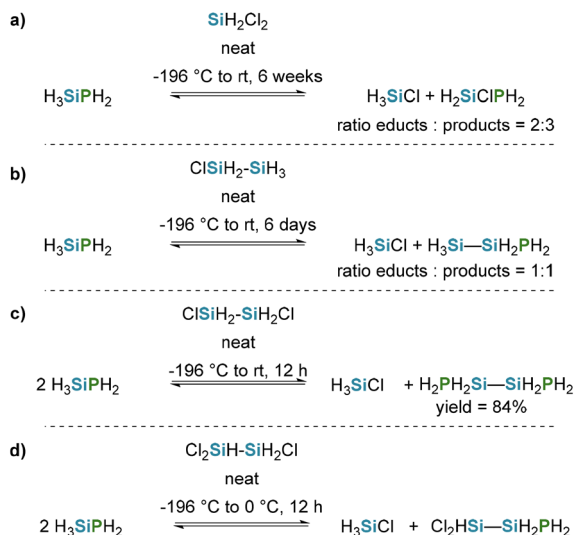


Scheme 112 Synthesis of H₃SiPH₂ *via* pyrolysis of SiH₄/PH₃ mixtures. No yields were reported.

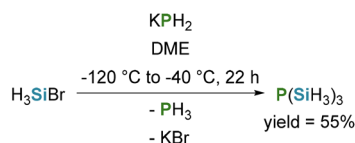


Scheme 114 Synthesis of H₃SiSiH₂PH₂ from H₃SiPH₂ and H₃SiSiH₂X. They noted that all compounds are present in equimolar amounts at the equilibrium.

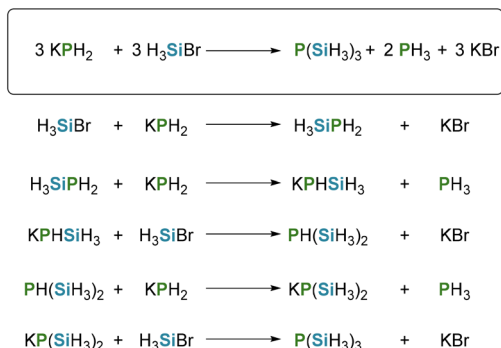




Scheme 115 Synthesis of silylphosphanes and chlorosilylphosphanes from H_3SiPH_2 with chlorosilanes (path a–d). No yields were given for the reaction of H_3SiPH_2 with 1,1,2-trichlorodisilane.



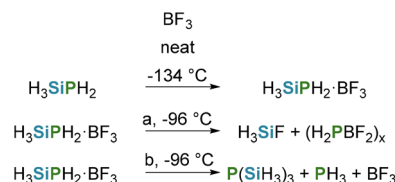
Scheme 116 Synthesis of $\text{P}(\text{SiH}_3)_3$ from KPH_2 and H_3SiBr .



Scheme 117 Formation of $\text{P}(\text{SiH}_3)_3$ from H_3SiBr through the intermediates H_2PSiH_3 and $\text{HP}(\text{SiH}_3)_2$.

Glidewell and Sheldrick demonstrated that the intermediate mono- and disilylsubstituted silylphosphanes can be obtained as well, when using an excess of potassium dihydrophosphide with H_3SiBr , followed by acidification of the non-volatile products with hydrogen sulfide.²⁰²

Lewis acid driven redistribution reactions also lead to the formation silylphosphanes. MacDiarmid and Russ demonstrated that H_3SiPH_2 forms a Lewis adduct with BF_3 , which subsequently decomposes at low temperatures to a mixture of



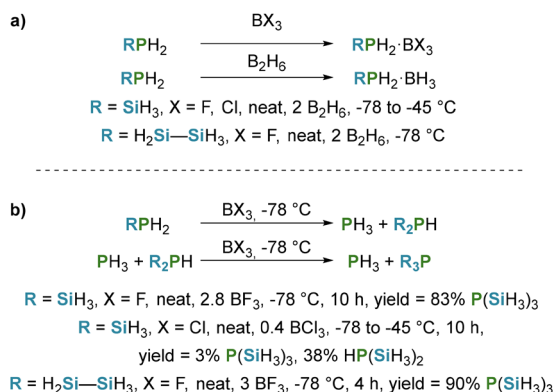
Scheme 118 Decomposition pathways of $\text{H}_3\text{SiPH}_2\cdot\text{BF}_3$. Both reactions a and b occur equally.

compounds containing $\text{P}(\text{SiH}_3)_3$. Both pathways (a and b) proceed to comparable extents (see Scheme 118).²⁰³

Further investigations showed that boranes promote the redistribution of silylphosphanes and their mixtures into trisilylphosphanes.^{203–206} In the first step of these redistribution reactions the silylphosphanes form Lewis acid–base complexes (see Scheme 119, path a) and, depending on the used borane, then undergo redistribution into trisilylphosphanes (see Scheme 119, path b).²⁰⁴ The best yields are obtained when using an excess of BF_3 with 83% formation of $\text{P}(\text{SiH}_3)_3$ and small amounts of $\text{HP}(\text{SiH}_3)_2$ and 90% for $\text{P}(\text{SiH}_2\text{SiH}_3)_3$ with small amounts of $\text{HP}(\text{SiH}_3)_2$ as side product.^{204,206} BCl_3 induces only limited redistribution, while BBR_3 predominantly led to the formation of H_3SiBr and BH_3 complexes only redistributed in trace amounts.²⁰⁴ Mixed trisilylphosphanes are obtained when mixtures of H_3SiPH_2 and $\text{H}_3\text{SiH}_2\text{SiPH}_2$ are subjected to these conditions.²⁰⁴

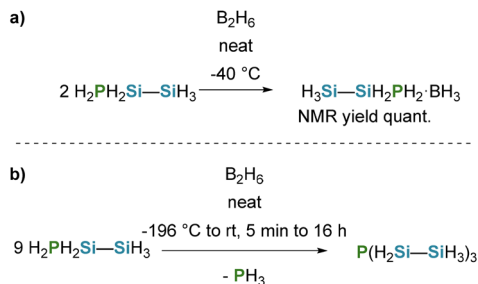
When disilanylphosphane is converted to borane adducts and subsequently heated, redistribution to trisilylphosphanes is not observed, instead SiH_4 and a polymeric substance is formed (see Scheme 120, path a). Only when 9 equivalents of disilanylphosphane were employed could trisdisilanylphosphane be detected, though no yields were given (see Scheme 120, path b).²⁰⁵

In 2010 Tice *et al.* reported a solvent free approach in which $\text{P}(\text{SnMe}_3)_3$ reacts with H_3SiBr to afford $\text{P}(\text{SiH}_3)_3$ in 98% yield (see Scheme 121).²⁰⁷

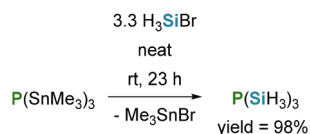


Scheme 119 Formation of Lewis acid–base complexes of boranes and silylphosphanes and subsequent BF_3 promoted redistribution reaction, forming trisilylphosphanes (path a and b). No yields were given for the BX_3 and diborane adducts.





Scheme 120 Formation of the borane adduct of $\text{H}_2\text{PSiH}_2\text{SiH}_3$ (path a) and thermal degradation into trisdilanylphosphane (path b). No isolated yields were given.

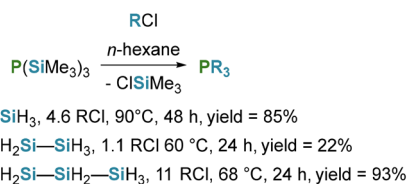


Scheme 121 Synthesis of $\text{P}(\text{SiH}_3)_3$ from $\text{P}(\text{SnMe}_3)_3$.

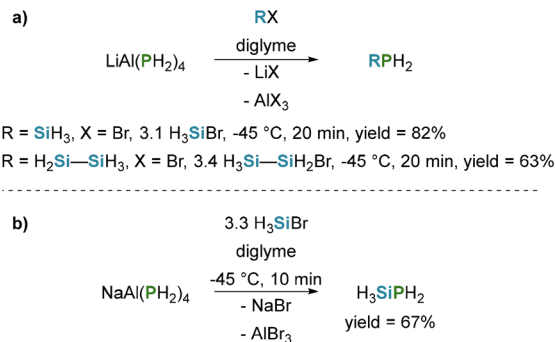
Recently Li *et al.* employed exchange reactions between $\text{P}(\text{SiMe}_3)_3$ and an excess of monochlorosilanes to generate the corresponding trisilylphosphanes (see Scheme 122).²⁰⁸

The direct reaction between metalated phosphanes and silylhalides was also thoroughly investigated. Lithium tetrakis-dihydrogenphosphidoaluminate was prepared by Finholt *et al.* in 1963,²⁰⁹ which proved as a useful reagent for phosphanylation. In contrast to reactions of silylhalides with KPH_2 ,^{16,200–202} the transmetalation sequence leading to the formation of $\text{P}(\text{SiH}_3)_3$ is not observed when metal tetrakis-dihydrogenphosphidoaluminates are employed, giving access to H_3SiPH_2 (see Scheme 123, path a and b).^{210,211}

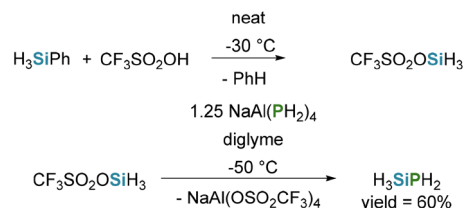
Use of $\text{LiAl}(\text{PH}_2)_4$ as phosphanylation agent enables the synthesis of diverse silylphosphanes from silylhalides, notably they were able to use SiH_2Br_2 to obtain $\text{SiH}_2(\text{PH}_2)_2$ and SiHBr_3 for $\text{SiH}(\text{PH}_2)_3$ respectively.^{210,212,213} Norman and co-workers showed that analogous methodology employing sodium tetrakis-dihydrogenphosphidoaluminate ($\text{NaAl}(\text{PH}_2)_4$) enables access to several silylphosphanes, as well as germylphosphanes.^{210,212} The reaction of $\text{NaAl}(\text{PH}_2)_4$ with H_3SiBr has proven to be a viable synthetic approach for the phosphanylation of silicon halides, allowing the synthesis of silylphosphanes such as H_2PSiH_3 .²¹¹ In 1994 Becker *et al.* successfully employed silyltriflate ($\text{CF}_3\text{SO}_2\text{OSiH}_3$) as silylation



Scheme 122 Synthesis of trisilylphosphanes *via* exchange reaction of $\text{P}(\text{SiMe}_3)_3$ with monochlorosilanes.



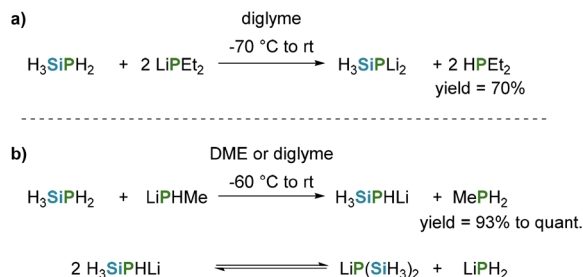
Scheme 123 Synthesis of silylphosphanes from metal tetrakis(dihydrogenphosphido)aluminates (path a and b).



Scheme 124 Synthesis of H_3SiPH_2 from $\text{CF}_3\text{SO}_2\text{OSiH}_3$. No yield for silyltriflate was given, as it is freshly prepared and used immediately without isolation.

agent for $\text{NaAl}(\text{PH}_2)_4$ to obtain H_3SiPH_2 in 60% yield (see Scheme 124).²¹⁴

Lithium dialkylphosphides are useful for preparing metalated silylphosphanes *via* reaction with H_3SiPH_2 (see Scheme 125, path a and b). Solutions of the monometalated silylphosphanes with concentrations above 0.1 mol l⁻¹ undergo disproportionation at room temperature in apolar solvents, establishing an equilibrium between H_3SiPHLi and $\text{LiP}(\text{SiH}_3)_2$ (see Scheme 125, path b).²¹⁵ This behavior prevents the direct synthesis of disilylphosphanes from monometalated H_3SiPHLi by subsequent reaction with silylhalides, as trisilylphosphanes will be formed as well.²¹⁵ Precipitation of LiPH_2 after removing most of the solvent and adding benzene drives



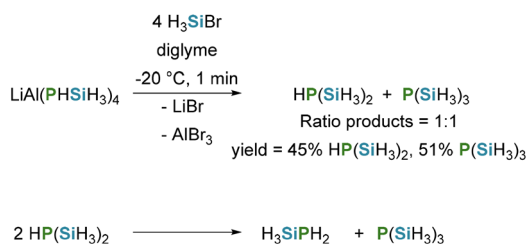
Scheme 125 Synthesis of metalated silylphosphanes from H_3SiPH_2 (path a and b) and disproportionation equilibrium of H_3SiPHLi . No isolated yield was given for the metalated silylphosphanes but for the associated byproducts.



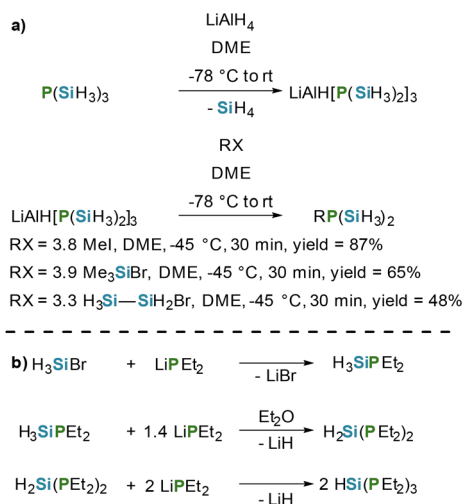
the equilibrium towards $\text{LiP}(\text{SiH}_3)_2$ and allows for recrystallization in Et_2O .²¹⁵

The monometalated H_3SiPHLi can be treated with AlCl_3 in diglyme to form $\text{LiAl}(\text{PHSiH}_3)_4$, which reacts with H_3SiBr to afford $\text{HP}(\text{SiH}_3)_2$. Owing to the disproportionation of H_3SiPHLi into $\text{LiP}(\text{SiH}_3)_2$ and LiPH_2 , the initially formed $\text{LiAl}(\text{PHSiH}_3)_4$ also contains $\text{LiAlP}(\text{SiH}_3)_2$ and LiAlPH_2 , which in turn yield H_3SiPH_2 and $\text{P}(\text{SiH}_3)_3$ upon reaction with H_3SiBr . Additionally, $\text{HP}(\text{SiH}_3)_2$ undergoes dismutation to monosilyl- and trisilylphosphane, leading to the approximately equimolar formation of mono-, di-, and trisilylphosphanes. By quickly separating the disilylphosphanes the dismutation can be circumvented. The dismutation is only observed with PH containing silylphosphides (see Scheme 126).²¹⁵

Drake and Anderson converted $\text{P}(\text{SiH}_3)_3$ with LiAlH_4 to the disilylphosphinoaluminate ion $\text{LiAlH}[\text{P}(\text{SiH}_3)_2]_3$, which further reacts with halides, such as, monobromodisilane $\text{H}_3\text{SiSiH}_2\text{Br}$ to give $\text{P}(\text{SiH}_3)_2\text{SiH}_2\text{SiH}_3$ (see Scheme 127, path a).²¹⁶ H_3SiPEt_2 derived from H_3SiBr undergoes H/Li exchange with LiPEt_2 to form $\text{H}_2\text{Si}(\text{PEt}_2)_2$ and LiH . Subsequent reactions of $\text{H}_2\text{Si}(\text{PEt}_2)_2$ with 2 equivalents of LiPEt_2 provides $\text{HSi}(\text{PEt}_2)_3$ (see Scheme 127, path b).²¹⁷



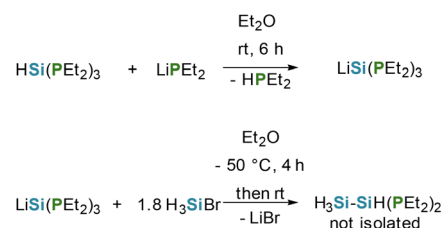
Scheme 126 Synthesis $\text{HP}(\text{SiH}_3)_2$ from $\text{LiAl}(\text{PHSiH}_3)_4$ and subsequent disproportionation into H_3SiPH_2 and $\text{P}(\text{SiH}_3)_3$.



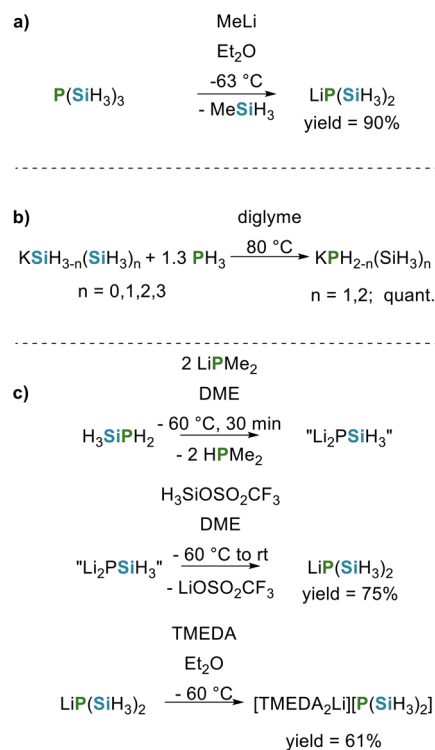
Scheme 127 Path (a) synthesis of disilylphosphinoaluminate and subsequent reactions with halides. Path (b) synthesis of $\text{H}_3\text{SiP}(\text{Et})_2$, $\text{H}_2\text{Si}(\text{P}(\text{Et})_2)_2$ and $\text{HSi}(\text{P}(\text{Et})_2)_3$ from H_3SiBr . No isolated yields were given.

$\text{HSi}(\text{PEt}_2)_3$ is interesting in the context of silylphosphanes, as it reacts with LiPEt_2 to give $\text{LiSi}(\text{PEt}_2)_3$, which reacts with H_3SiBr , resulting in the formation of $\text{H}_3\text{SiSiH}(\text{PEt}_2)_2$, but was only isolated with sideproducts (see Scheme 128).²¹⁷ Metalation of silylphosphanes using *n*-BuLi leads to cleavage of the Si-P bond.^{215,217}

Silylphosphides as interesting reagents for further functionalization were obtained either *via* metalation of silylphosphanes,^{218,219} or by employing build up reactions of silanes.¹¹⁵ In 1973, Cradock *et al.* obtained $\text{LiP}(\text{SiH}_3)_2$ from $\text{P}(\text{SiH}_3)_3$ in 90% yield by metalation with MeLi (see Scheme 129, path a).^{218,219} In 1994 Sundermeyer and co-workers accessed KPHSiH_3 and $\text{KP}(\text{SiH}_3)_2$ *via* the buildup reaction between SiH_4 and K in diglyme and subsequent reaction with PH_3 (see Scheme 129, path b).⁴⁷ $\text{LiP}(\text{SiH}_3)_2$ can be syn-



Scheme 128 Synthesis of $\text{H}_3\text{SiSiH}(\text{PEt}_2)_2$ from $\text{LiSi}(\text{PEt}_2)_3$. The formation of $\text{H}_3\text{SiSiH}(\text{PEt}_2)_3$ was confirmed but isolation as not possible due to degradation during distillation.



Scheme 129 Synthesis of $\text{LiP}(\text{SiH}_3)_2$ (path a), KPHSiH_3 , $\text{KP}(\text{SiH}_3)_2$ (path b) and $[\text{Tmeda}_2\text{Li}][\text{P}(\text{SiH}_3)_2]$ (path c).

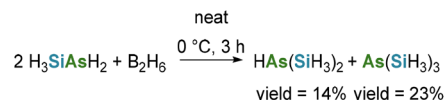


thesized through the dismutation of H_3SiPH_2 and LiPHCH_3 (see Scheme 125, path b), and isolated as $[(\text{TMEDA})_2\text{Li}][\text{P}(\text{SiH}_3)_2]$ (see Scheme 129, path c). A crystal structure is shown in Fig. 14.²¹⁴

Silylarsanes. Silylarsanes containing only As, Si, and H, are promising precursors for semiconductor fabrication because they are carbon- and halogen-free, which helps minimize contamination during CVD/PECVD/ALD and supports cleaner, low-temperature decomposition to volatile byproducts, mainly H_2 .^{186,220} Arsenic is a shallow donor in group-IV semiconductors, so silylarsanes can serve as single-source, *in situ* n-type dopant feeds for Si, Ge, and Si-rich alloys, leveraging the high activation of As and notably low diffusivity in Si to form ultra-shallow, abrupt junctions that are advantageous for modern complementary metal-oxide-semiconductors source/drain engineering.¹⁸⁵

The smallest member of the silylarsane family is silylarsane (H_3SiAsH_2) and was prepared by Jolly and Drake in 1962. Similar to the synthesis of H_3SiPH_2 , using an equimolar mixture of SiH_4 and arsine (AsH_3) in ozonizer-type silent electrical discharge tube yields H_3SiAsH_2 , as well as disilanylarsane ($\text{H}_3\text{SiH}_2\text{SiAsH}_2$) (see Scheme 130).¹⁹⁵ Notably disilane as well as trisilane are formed as sideproducts.²²¹

When H_3SiAsH_2 and B_2H_6 are condensed into a vessel they react upon warming to 0°C by forming a solid as well as disilylarsane ($\text{HAS}(\text{SiH}_3)_2$) and trisilylarsane ($\text{As}(\text{SiH}_3)_3$) (see Scheme 131).²²¹ Reactions between H_3SiAsH_2 and bromodibor-



Scheme 131 Synthesis of $\text{HAS}(\text{SiH}_3)_2$ and $\text{As}(\text{SiH}_3)_3$ from H_3SiAsH_2 and B_2H_6 .

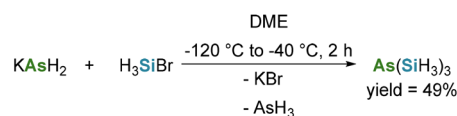
ane ($\text{B}_2\text{H}_5\text{Br}$) only afford the formation of bromosilane and a arsine containing polymer.²²¹ H_3SiAsH_2 forms the 1 : 1 adduct with BX_3 ($\text{X} = \text{Cl}, \text{Br}$), but $\text{H}_3\text{SiAsH}_2\text{BX}_3$ decomposes at low temperatures forming H_3SiX .²²¹

Aylett *et al.* showed in 1955, that monoiodosilane reacts with arsenic to afford diiodosilylarsane (AsI_2SiH_3) with various side products, most notably trisilylarsane, additionally they showed that trimethylarsane (AsMe_3) undergoes reaction with iodosilane, giving access to trisilylarsane.¹³

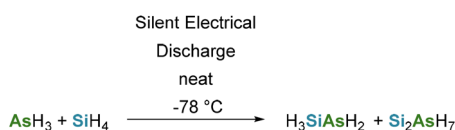
Arsenides show similar reactivity towards silyl halides as phosphides. Trisilylarsane can be accessed through nucleophilic substitution of silyl halides by alkali metal arsenides. Amberger and Boeters used bromosilane with potassium dihydroarsenide (KAsH_2) to afford $\text{As}(\text{SiH}_3)_3$ (see Scheme 132).²⁰⁰ The same reported method of Glidewell and Sheldrick, in which H_3SiPH_2 and $\text{HP}(\text{SiH}_3)_2$ can be obtained from the reaction of KPH_2 with H_3SiBr *via* acidification with H_2S also works for potassium arsenide KAsH_2 , but leads mostly to silylarsine in 54% yield.²⁰² The formation of $\text{As}(\text{SiH}_3)_3$ from KAsH_2 proceeds *via* a series of transmetalation steps, similar to the respective synthesis of trisilylphosphane $\text{P}(\text{SiH}_3)_3$ (see Scheme 117).²⁰²

Metalated silylarsanes can react with silyl halides to form the respective silylarsanes. Lithium tetrakisdiarsidoaluminate ($\text{LiAl}(\text{AsH}_2)_4$) reacts with silylhalides H_3SiX ($\text{X} = \text{Br}, \text{I}$) to afford silylarsane, though monochlorosilane only led to formation of H_3SiAsH_2 in trace amounts (see Scheme 133).^{222,223}

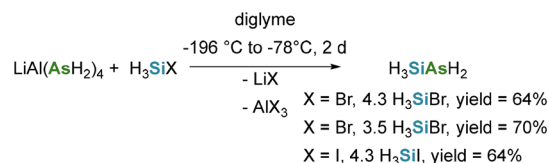
Anderson and Drake were able to obtain disilylarsane $\text{HAS}(\text{SiH}_3)_2$ by treating $\text{LiAl}(\text{AsH}_2)_4$ with bromosilane. After removal of the volatiles the remaining solid was treated with dihydrogen selenide (H_2Se), resulting in the formation of $\text{HAS}(\text{SiH}_3)_2$.



Scheme 132 Synthesis of $\text{As}(\text{SiH}_3)_3$ from KAsH_2 and H_3SiBr .²⁰⁰



Scheme 130 Synthesis of H_3SiAsH_2 and Si_2AsH_7 from a $\text{SiH}_4/\text{AsH}_3$ mixture. No experimental details were given.



Scheme 133 Synthesis of H_3SiAsH_2 from $\text{LiAl}(\text{AsH}_2)_4$ and silylhalides.

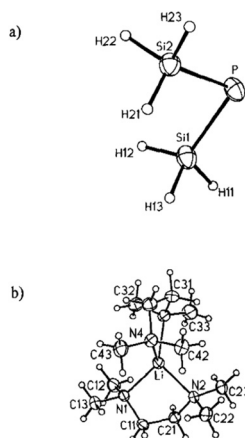


Fig. 14 Crystal structure of the anion (a) and cation (b) of $[(\text{TMEDA})_2\text{Li}][\text{P}(\text{SiH}_3)_2]$. For better visibility the anion and cation are not shown in the same scale. Adapted from G. Becker, B. Eschbach, D. Kāshammer, *et al.*²¹⁴ with permission from John Wiley and Sons © 1994.



(SiH₃)₂.²⁰² Furthermore the treatment of lithium tetrasilylarsenide (LiAs(SiH₃)₄) with bromodisilane led to the formation of disilanylarsane (H₃SiH₂SiAsH₂) in 59% yield (see Scheme 134).²²³

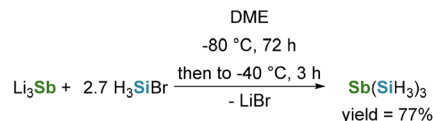
Disilanylarsane can also be obtained from the exchange reaction with monohalodisilanes H₃SiH₂SiX (X = Cl, Br) at low temperatures. The yields for H₃SiH₂SiAsH₂ can be brought to 30%, by stepwise removal of the formed silyl halide H₃SiX (see Scheme 135).¹⁹⁸

Lithium disilylarsenide (LiAs(SiH₃)₂) can be obtained from trisilylarsane in 90% yield by metalation with MeLi, as shown by Cradock *et al.* in 1973.^{218,219}

Similar to trisilylphosphanes, trisilylarsanes are also available through an exchange reaction between tris(trimethylsilyl)arsane (As(SiMe₃)₃) and monohalodisilanes, though only the reaction with chlorotrisilane is reported (see Scheme 136).²⁰⁸

Silylstibanes. Antimony can act similar to other group V elements as n-type dopant.¹⁸⁵ Antimony has a significantly larger atomic size compared to phosphorous and arsenic, leading to slower diffusion and therefore more precise control of dopant profiles, which is especially useful for specialized applications, such as, power electronics and high-temperature devices.²²⁴ Compared to phosphorous and arsenic there are only few investigations into the synthesis of silylstibanes.

The nucleophilic substitution of phosphides and arsenides with silyl halides gave access to their respective trisilyl compound, but similar reactions with antimonides and stibanes did not lead to the desired trisilylstibane (Sb(SiH₃)₃).^{200,225} Amberger and Boeters instead accessed Sb(SiH₃)₃ *via* the salt metathesis reaction of lithium antimonide (Li₃Sb) with H₃SiBr (see Scheme 137).^{200,225}



Scheme 137 Synthesis of Sb(SiH₃)₃ *via* salt metathesis reaction of Li₃Sb and H₃SiBr.

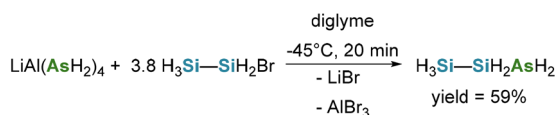
Functionalization with group 6 (synthesis of silylchalcogenes)

Siloxanes. Single-source Si–O feedstocks deliver silicon and oxygen in a fixed stoichiometric ratio, simplifying process control compared with separate silane and oxidant flows, and reducing parasitic gas-phase reactions.²²⁶ When designed to be carbon- and halogen-free, they can evolve only hydrogen or water as byproducts, lowering contamination.²²⁷

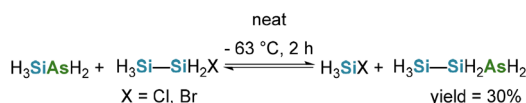
In 1917, Stock, Somieski, and Wintgen reported the first isolation of O(SiH₃)₂. Their method involved shaking H₃SiBr with degassed H₂O, allowing the mixture to stand, and then purifying the product by fractional distillation (see Scheme 138). They proposed that hydrolysis generates H₃SiOH as intermediate, which rapidly self-condenses to give O(SiH₃)₂ with loss of water.²²⁸

In a follow-up study Stock and Somieski isolated O(Si₂H₅)₂ by reacting Si₂H₅Br (which was contaminated with Si₂H_nBr_{6–n}, n = 0–6) with degassed H₂O, and then extracting it with benzene (see Scheme 139). They failed in isolating the pure compound and always had some H₂O next to O(Si₂H₅)₂. The higher silyl bromides present in the educt as contaminations did not interfere with the reaction, since their resulting siloxanes polymerized and then precipitated as a white solid.¹⁴⁵

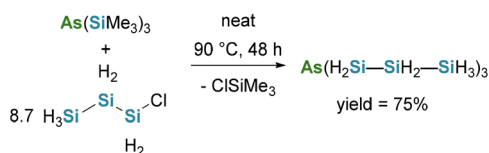
Emel us, MacDiarmid, and Maddock attempted the reduction of O(SiCl₃)₂ with LiAlH₄, but were unable to prepare O(SiH₃)₂ *via* this route. Instead, they obtained O(SiH₃)₂ in 37% yield by passing H₂ through boiling O(SiCl₃)₂, then directing the saturated gas stream over aluminium foil at 500 °C (see Scheme 140, path a). They also generated O(SiH₃)₂ *via* hydrolysis of SiH₃I, S(SiH₃)₂, and Se(SiH₃)₂ (see Scheme 140, path b



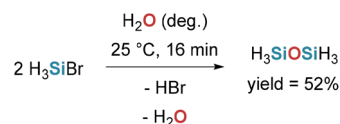
Scheme 134 Synthesis of H₃SiH₂SiAsH₂ from LiAl(AsH₂)₄ and H₃SiSiH₂Br.



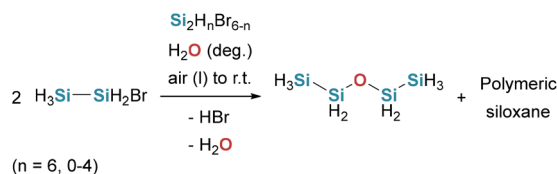
Scheme 135 Synthesis of H₃SiSiH₂AsH₂ *via* exchange reaction from H₃SiSiH₂X (X = Cl, Br) and H₃SiAsH₂.



Scheme 136 Synthesis of As(SiH₂SiH₂SiH₃)₃ *via* exchange reaction from H₃SiH₂SiH₂SiCl and As(SiMe₃)₃.

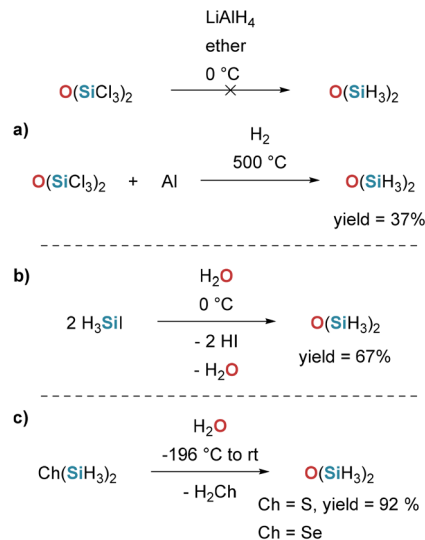


Scheme 138 Synthesis of O(SiH₃)₂ *via* hydrolysis of SiH₃Br.



Scheme 139 Hydrolysis of Si₂H₅Br, contaminated with higher bromosilanes, leading to O(Si₂H₅)₂ and polymeric siloxanes. Yields of the siloxane were not determined.





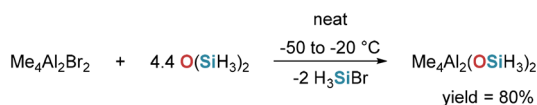
Scheme 140 Synthesis of O(SiH₃)₂ from O(SiCl₃)₂ (path a), SiH₃I (path b), S(SiH₃)₂ and Se(SiH₃)₂ (path c). Yields of Se(SiH₃)₂ hydrolysis reaction not determined.

and c). For the Se(SiH₃)₂ route, the yield could not be determined because H₂Se could not be separated from the silylether.²²⁹

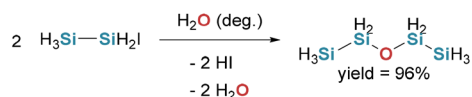
Kriner, MacDiarmid, and Evers investigated reactions of O(SiH₃)₂ with aluminum halides. Treatment with Me₄Al₂Br₂ afforded Me₄Al₂(OSiH₃)₂ (see Scheme 141), which is stable at -78 °C but decomposes at room temperature to give SiH₄ and a non-volatile viscous residue. In contrast, reactions of O(SiH₃)₂ with Al₂X₆ (X = Cl, Br, I) yielded only the corresponding halosilanes; no aluminum-containing products could be isolated.²³⁰

Ward and MacDiarmid isolated pure O(Si₂H₅)₂ by hydrolysis purified Si₂H₅I. Purification of O(Si₂H₅)₂ required an extensive protocol: multiple fractional distillations, drying over P₂O₅ (noting that prolonged contact causes degradation of the silylether and formation of PH₃), followed by repeated distillations. The final product was obtained in 96% yield (see Scheme 142).²³¹

Sternbach and MacDiarmid (1961) investigated routes to H₃SiOCH₃. Reacting SiH₄ with methanol (MeOH) at room temperature gave only unreacted SiH₄, H₂, and a complex



Scheme 141 Synthesis of Me₄Al₂(OSiH₃)₂ from Me₄Al₂Br₂ and O(SiH₃)₂.



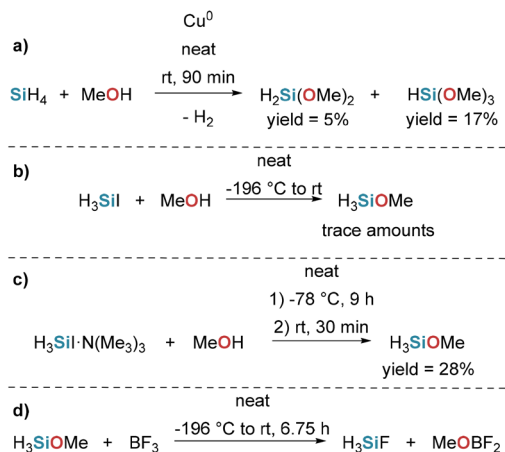
Scheme 142 Hydrolysis of O(Si₂H₅)₂ from Si₂H₅I.

mixture of methoxysilanes. With copper powder as a promoter, low yields of H₂Si(OCH₃)₂ and HSi(OCH₃)₃ were isolated (see Scheme 143, path a). Direct reaction of SiH₃I with methanol was highly vigorous, leading mainly to polymeric material; only traces of H₃SiOCH₃ were detected in the volatile fraction (see Scheme 143, path b). In contrast, treating the amine adduct SiH₃I·N(Me)₃ with methanol furnished MeOSiH₃ in 28% yield (see Scheme 143, path c). They further showed that MeOSiH₃ reacts with BF₃ to give SiH₃F and MeOBF₂ (see Scheme 143, path d).²³²

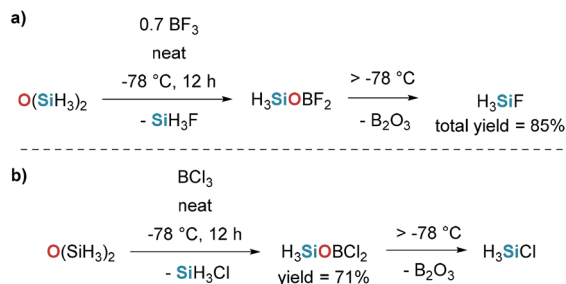
Onyszchuk found that O(SiH₃)₂ reacts with BF₃ and BCl₃ to give H₃SiOBX₂ (X = F, Cl), but both products are highly unstable. The fluorinated derivative decomposed during isolation, even at low temperature, and could not be isolated. The chloro analogue decomposes more slowly and was successfully isolated at -64 °C; several subsequent distillations at -112 °C were used to remove H₃SiCl formed in the process (see Scheme 144).²³³

Van Dyke and MacDiarmid prepared the unsymmetrical silylether H₃SiOSi₂H₅ by two routes: path (a) hydrolysis of a mixture containing SiH₃I and Si₂H₅Br; path (b) equilibration between O(SiH₃)₂ and O(Si₂H₅)₂ (see Scheme 145).²³⁴

Van Dyke examined the reactions of O(SiH₃)₂ with phosphorus halides PX₃ (X = F, Cl, Br). No reaction was observed

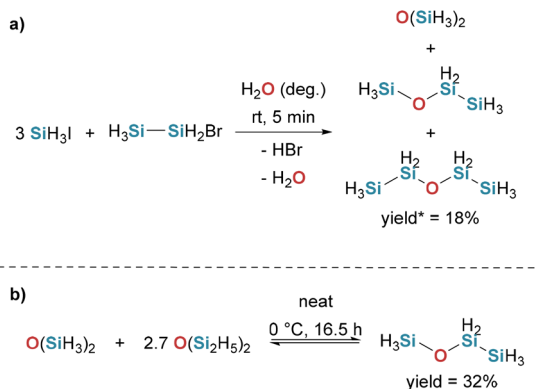


Scheme 143 Synthesis of alkoxy silanes (path a–c) and reaction of H₃SiOMe with BF₃ (path d).



Scheme 144 Reactions of O(SiH₃)₂ with BF₃ (path a) and BCl₃ (path b).



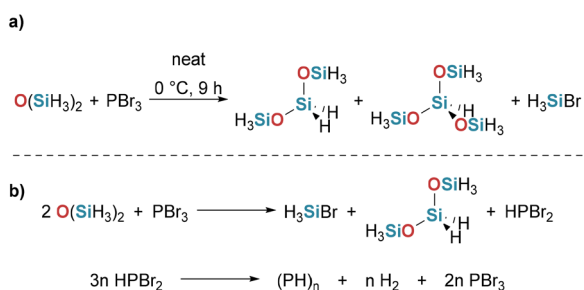


Scheme 145 Synthesis of the unsymmetrical silylether $\text{H}_3\text{SiOSi}_2\text{H}_5$ via hydrolysis (path a) and equilibration reactivity of silylethers (path b). *Yield of product mixture.

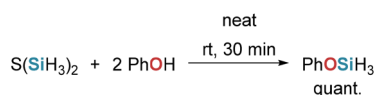
with PF_3 or PCl_3 . In contrast, PBr_3 caused H_2 evolution and formation of a yellow solid; the product mixture contained, in addition to unreacted starting materials, SiH_3Br and $(\text{H}_3\text{SiO})_n\text{SiH}_{4-n}$ ($n = 2, 3$) (see Scheme 146, path a). These products were inseparable, so no yields were reported. The absence of SiH_4 formation and the appearance of a yellow, presumably polymeric phosphorus hydride $(\text{PH})_x$ led Van Dyke to propose the transformation shown in (Scheme 146, path b).²³⁵

Glidewell and Rankin prepared the aryl silylether PhOSiH_3 in nearly quantitative yield by reacting $\text{S}(\text{SiH}_3)_2$ with phenol (PhOH) (see Scheme 147).²³⁶

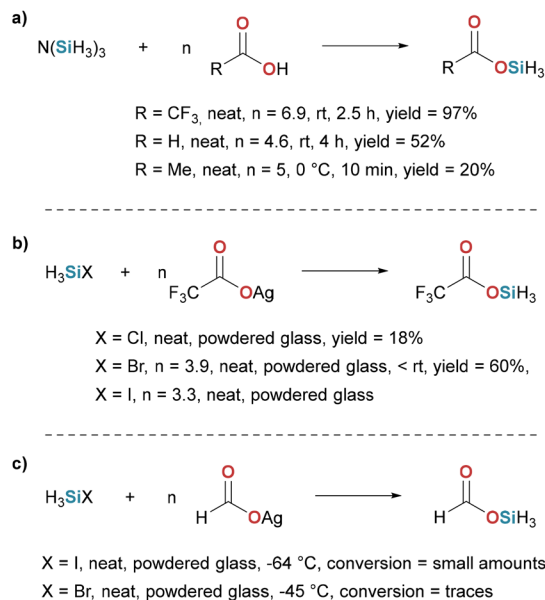
Ebsworth and Thompson prepared silyl esters RCO_2SiH_3 ($\text{R} = \text{CF}_3, \text{H}, \text{Me}$) by protonolysis of trisilylamine $\text{N}(\text{SiH}_3)_3$ with the corresponding carboxylic acids (see Scheme 148, path a). Side products depended on R : with $\text{R} = \text{CF}_3$ they observed traces of monosilane; with $\text{R} = \text{H}$ they detected SiH_4 , $\text{H}_3\text{SiOSiH}_3$, and traces of CO_2 . They next examined the reaction of silver trifluoroacetate ($\text{F}_3\text{CC}(\text{O})\text{OAg}$) with silyl halides H_3SiX



Scheme 146 a) Reaction of $\text{O}(\text{SiH}_3)_2$ with PBr_3 and (b) the proposed reaction mechanism, no yields were reported.



Scheme 147 Synthesis of PhOSiH_3 using $\text{S}(\text{SiH}_3)_2$.



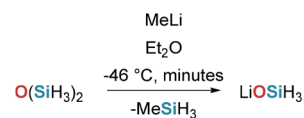
Scheme 148 Synthesis towards silyl esters using $\text{N}(\text{SiH}_3)_3$ (path a) and SiH_3X ($\text{X} = \text{Cl}, \text{Br}, \text{I}$) (path b and c). Yield of reaction between H_3SiI and silver trifluoroacetate not reported.

($\text{X} = \text{Cl}, \text{Br}, \text{I}$) (see Scheme 148, path b). SiH_3Cl gave the trifluoroacetate silyl ester in low yield, SiH_3Br improved the yield to about 60%, and with SiH_3I isolation of the ester failed. Finally, they attempted the analogous synthesis with silver formate ($\text{HC}(\text{O})\text{OAg}$). With SiH_3I , substantial iodine was liberated along with non-condensable gases; the mixture contained disiloxane, formic acid, and SiH_3I bearing only small amounts of silyl formate ($\text{HC}(\text{O})\text{OSiH}_3$). With H_3SiBr only traces of silyl formate were obtained, and warming the reaction tube to 0°C caused it to explode (see Scheme 148, path c).¹⁶⁹

Cradock *et al.* reported that treatment of $\text{O}(\text{SiH}_3)_2$ with MeLi liberates MeSiH_3 in approximately 85% of the theoretical amount, forming $\text{Li}(\text{OSiH}_3)$ (see Scheme 149). They then attempted to react solutions containing $\text{Li}(\text{OSiH}_3)$ with different electrophiles, but never observed the expected product.²¹⁹

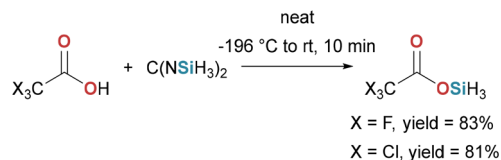
Drake, Henderson, and Hemmings synthesized the silyl esters $\text{H}_3\text{SiOC}(\text{O})\text{CX}_3$ ($\text{X} = \text{F}, \text{Cl}$) by adapting the Ebsworth-Thompson protocol, replacing $\text{N}(\text{SiH}_3)_3$ with a bis(silyl) carbodiimide $[\text{C}(\text{NSiH}_3)_2]$ as the silylating agent (see Scheme 150).^{169,237} This provided a complementary route to the trihaloacetate esters.

Glidewell prepared mixed silyl ethers ROSiH_3 ($\text{R} = \text{Me}, \text{Et}, i\text{-Pr}, t\text{-Bu}$) by reacting the corresponding lithium tetraalumi-



Scheme 149 Synthesis of $\text{Li}(\text{OSiH}_3)$, no reaction details reported and yields were not determined.



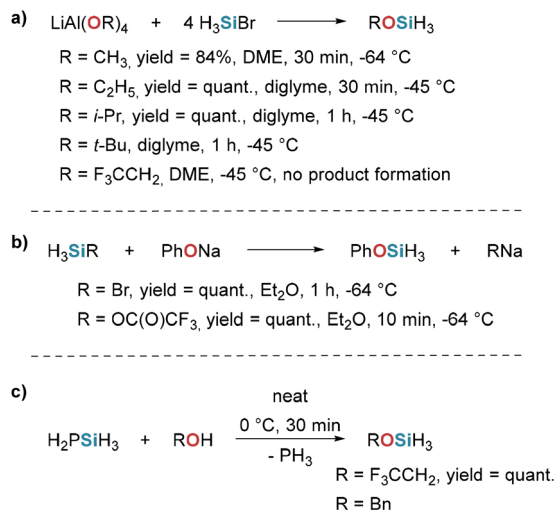


Scheme 150 Synthesis of silyl esters using $\text{C}(\text{NSiH}_3)_2$.

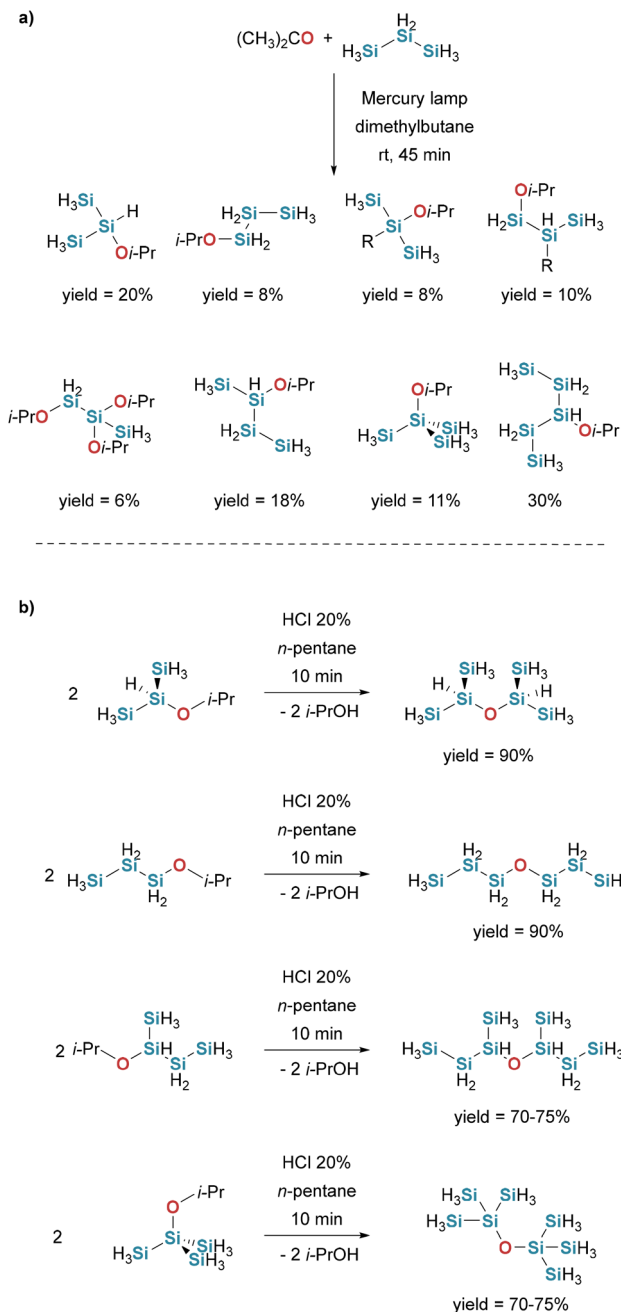
nates with SiH_3Br (see Scheme 151, path a). The phenyl silyl ether PhOSiH_3 was obtained from PhONa using either SiH_3Br or silyl trifluoroacetate (Scheme 151, path b). He further showed that silylphosphine can serve as an SiH_3 -transfer reagent: 2,2,2-trifluoroethanol was smoothly converted to $\text{CF}_3\text{CH}_2\text{OSiH}_3$ (a transformation that failed under the tetraaluminate/ SiH_3Br conditions), and benzyl alcohol gave BnOSiH_3 selectively (Scheme 151, path b and c).²³⁸

Fehér, Fischer, and Skrodzki found that UV irradiation (medium-pressure Hg lamp) of trisilane in the presence of acetone affords a mixture of alkoxy-silanes (silylethers) (see Scheme 152, path a). They note that the substitution pattern can be tuned by conditions: short irradiation times with an excess of silane favour predominantly monosubstituted alkoxy-silanes, whereas excess ketone and prolonged irradiation shift the distribution toward highly alkoxyated silanes. They further showed that the formed isopropoxysilanes undergo acid-promoted hydrolysis with dilute, non-oxidizing acids to give the corresponding bis-silyl ethers (disiloxanes), in high yields (see Scheme 152, path b).²³⁹

Lobreyer, Oeler, and Sundermeyer (1991) reported two routes towards silyl nonaflate. Reaction of silver nonaflate with SiH_3Cl afforded low yields (see Scheme 153, path a), whereas an alternative approach employing phenylsilane with perfluorobu-



Scheme 151 Synthesis towards mixed silyl ethers using SiH_3Br and tetraaluminates, SiH_3R (R = Br, $\text{OC}(\text{O})\text{CF}_3$) and PhONa , and H_2PSiH_3 with ROH (R = F_3CCH_2 , Bn). Treatment of mixed silylethers ROSiH_3 (R = Et, *i*-Pr, *t*-Bu, F_3CCH_2) with HI (path a–c). Yield of the reactions between lithium aluminate and H_3SiBr , and silylphosphine and BnOH were not determined.



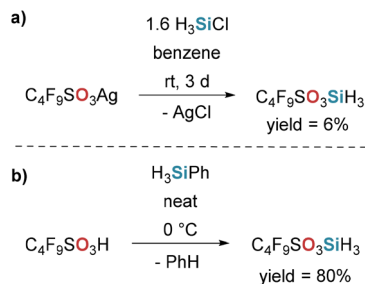
Scheme 152 UV irradiation of trisilane in the presence of acetone leading to different mixed silylethers (path a) and the hydrolysis of formed silylethers with aqueous HCl (path b).

tanessulfonic acid gave significantly improved isolated yields (see Scheme 153, path b). The resulting silyl nonaflate was then used in further functionalization reactions (Scheme 67).⁴⁶

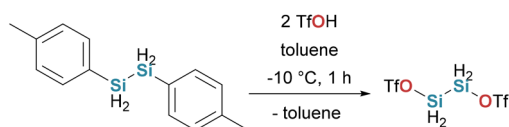
Cradock *et al.* generated $(\text{TfOSiH}_2)_2$ *in situ* by protonolysis of bis(*p*-tolyl)disilane with triflic acid (TfOH) (see Scheme 154). The disilyl di(triflate) was not isolated; instead, it was used directly for subsequent functionalization (Scheme 86).¹⁵⁸

Silylthiones. Single-source Si–S feedstocks deliver silicon and sulfur simultaneously in a fixed stoichiometric ratio, sim-





Scheme 153 Formation of silyl nonaflate using silver nonaflate with SiH_3Cl (path a) and perbutanesulfonic acid with phenylsilane (PhSiH_3) (path b).

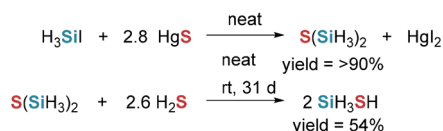


Scheme 154 Synthesis towards disilyl di(triflate) using (*p*-tolyl- SiH_2)₂ and triflic acid. Isolated yields not reported.

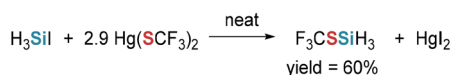
plifying process control. They also suppress gas-phase parasitic reactions and reactor memory effects compared with separate silane/ H_2S or organosulfide co-flows.¹³⁴ Because Si and S are pre-bonded, these precursors can enable lower-temperature deposition; used examples like bis(trimethylsilyl)sulfide demonstrate processability.²⁴⁰ By contrast, a carbon-free analogue such as disilyl sulfide ($\text{S}(\text{SiH}_3)_2$) would, in principle, evolve only hydrogen or hydrogen sulfide as volatiles and minimize residual carbon.

Emel us, MacDiarmid, and Maddock prepared disilyl sulfide $\text{S}(\text{SiH}_3)_2$ by passing SiH_3I vapour three times through a tube packed with HgS . Subsequent reaction of $\text{S}(\text{SiH}_3)_2$ with H_2S at room temperature for 31 days furnished SiH_3SH (see Scheme 155).²²⁹

Downs and Ebsworth prepared F_3CSSiH_3 by passing H_3SiI vapor over $\text{Hg}(\text{SCF}_3)_2$ deposited on glass wool. The initially obtained material partially decomposed to give SiH_3F and CSF_2 ; repeated fractional distillation removed these volatile by products and furnished pure F_3CSSiH_3 (see Scheme 156).²⁴¹



Scheme 155 Synthesis of $\text{S}(\text{SiH}_3)_2$ using SiH_3I and HgS , reaction of $\text{S}(\text{SiH}_3)_2$ with H_2S forming SiH_3SH .

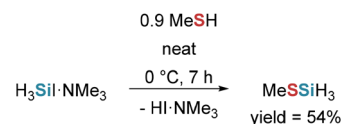


Scheme 156 Reaction between SiH_3I and $\text{Hg}(\text{SCF}_3)_2$ forming F_3CSSiH_3 .

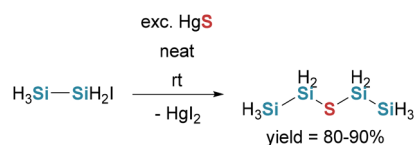
Sternbach and MacDiarmid synthesized MeSSiH_3 by reacting $\text{SiH}_3\text{I}\cdot\text{NMe}_3$ with MeSH at 0 °C (see Scheme 157).²⁴²

Ward and MacDiarmid prepared $\text{S}(\text{Si}_2\text{H}_5)_2$ by passing $\text{Si}_2\text{H}_5\text{I}$ vapor over excess HgS at room temperature (see Scheme 158).¹⁵³

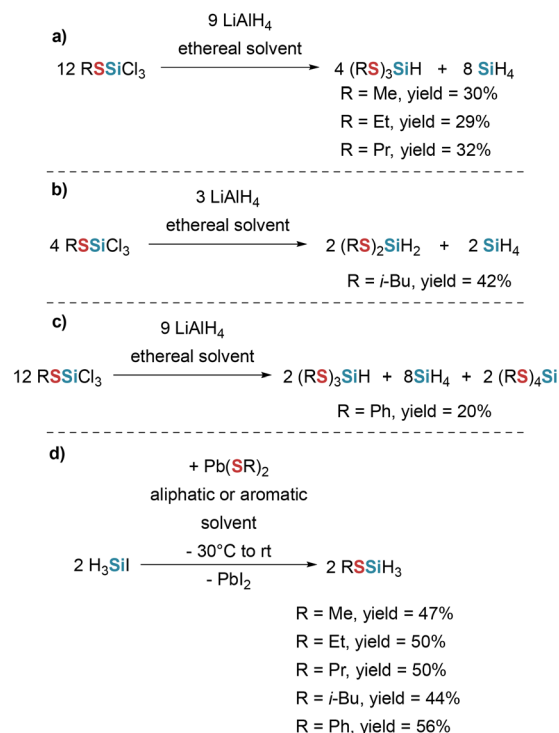
Schmei er and Frouzanfar attempted to prepare monosubstituted thiosilanes $(\text{RS})\text{SiH}_3$ by LiAlH_4 reduction of $\text{RS}\text{-SiCl}_3$, but instead obtained di-, tri-, and tetrasubstituted products. They attributed this outcome to AlCl_3 formed *in situ*, which promotes disproportionation of thiolato groups. The product distribution depends on the substituent R: with *n*-alkyl groups, $(\text{RS})_3\text{SiH}$ formed together with SiH_4 (see Scheme 159, path a);



Scheme 157 Formation of MeSSiH_3 by reacting $\text{SiH}_3\text{I}\cdot\text{NMe}_3$ with MeSH .



Scheme 158 Synthesis of $\text{S}(\text{Si}_2\text{H}_5)_2$ by the reaction of $\text{Si}_2\text{H}_5\text{I}$ with HgS .



Scheme 159 Synthesis of mono-, di-, tri- and tetrasubstituted thiosilanes starting either from trichlorosilanes and LiAlH_4 (path a–c), or from SiH_3I and lead mercaptides (path d).

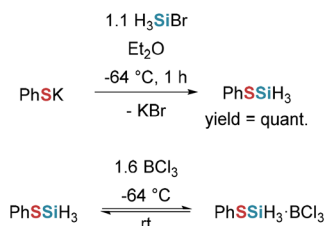


with a branched alkyl group (i-Bu), (RS)₂SiH₂ and SiH₄ were obtained (see Scheme 159, path b); and with phenyl, a mixture of tri- and tetrasubstituted thiosilanes accompanied by SiH₄ (Scheme 159, path c). Monosubstituted thiosilanes were obtained only when employing lead mercaptides in aliphatic or aromatic solvents, which furnished isolable (RS)SiH₃ (Scheme 159, path d).²⁴³

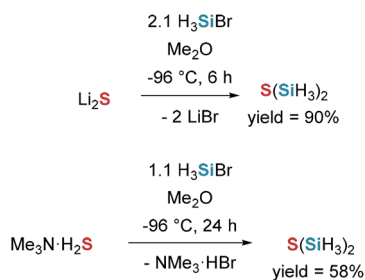
Glidewell and Rankin prepared PhSSiH₃ by salt metathesis of PhSK with SiH₃Br. They also examined the reactivity of PhSK toward boron halides: no reaction was observed with BF₃, whereas BCl₃ afforded a white 1 : 1 adduct at low temperature that dissociated on warming to ambient temperature (see Scheme 160).²³⁶

Glidewell later obtained disilyl sulfide S(SiH₃)₂ in excellent yields by salt metathesis of Li₂S with SiH₃Br (see Scheme 161). Alternatively, treatment of SiH₃Br with Me₃N·H₂S also furnished S(SiH₃)₂.¹⁷¹

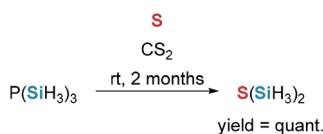
Ebsworth, Glidewell, and Sheldrick monitored the reaction of trisilylphosphine P(SiH₃)₃ with elemental sulfur in CS₂ in an NMR tube over an extended period. After 3 weeks, NMR spectroscopy indicated 16% formation of S(SiH₃)₂; after 2 months, conversion to S(SiH₃)₂ was essentially complete. In contrast, P(SiH₃)₃ showed no detectable reaction with H₂S under analogous conditions (see Scheme 162).²⁴⁴



Scheme 160 Formation of PhSSiH₃ and reaction of PhSSiH₃ with BCl₃.



Scheme 161 Synthesis of disilylsulfide by Glidewell.



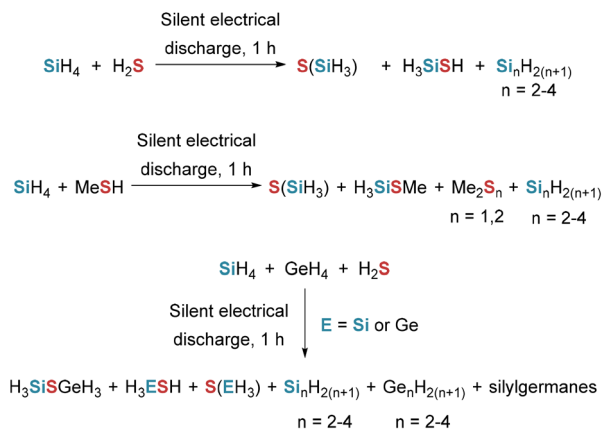
Scheme 162 Synthesis of disilylsulfide by reacting trisilylphosphane with sulfur.

Drake and Riddle subjected gas mixtures to silent electrical discharge and observed broad product formation. For an equimolar SiH₄/H₂S mixture, in addition to higher silanes, S(SiH₃)₂ and H₃SiSH were detected. Using SiH₄/MeSH, the products included S(SiH₃)₂, H₃SiSMe, Me₂S and Me₂S₂, along with higher silanes. Finally, a SiH₄/GeH₄/H₂S mixture afforded H₃SiSGeH₃, H₃SiSH, H₃GeSH, S(SiH₃)₂, S(GeH₃)₂, higher silanes and germanes, as well as mixed silylgermanes (see Scheme 163).²⁴⁵

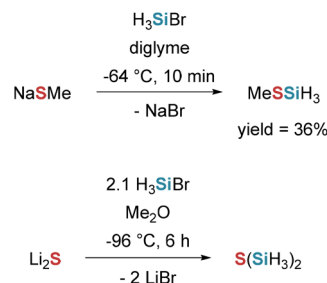
Glidewell obtained MeSSiH₃ by reacting LiAl(SMe)₄ with H₃SiBr (see Scheme 164). Treatment of Li₂S with H₃SiBr furnished the expected S(SiH₃)₂, but it could not be isolated, contrary to his previous work where isolation was successful (Scheme 161).^{171,238}

Anderson and Drake prepared a range of thiosilanes by using the thiolato-aluminate LiAl(SMe)₄ as nucleophilic RS-source. Treatment of LiAl(SMe)₄ with H₃SiBr or H₅Si₂Br furnished the corresponding MeSSiH₃ and MeSSi₂H₅, respectively (see Scheme 165), providing a convenient route to both silyl- and disilyl-substituted thiosilanes.²⁴⁶

Cradock, Ebsworth, and Jessep obtained S(SiH₃)₂ in quantitative yield by treating N(SiH₃)₃ with H₂S, also forming the ammonium salt NH₃·HSSiH₃. The same ammonium salt was also obtained quantitatively by combining HSSiH₃ with NH₃ (see Scheme 166, path a). Using partially substituted amines

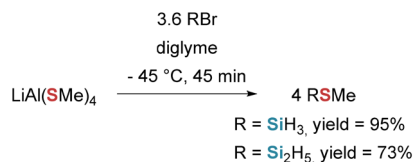


Scheme 163 Silent electrical discharge reactions of different SiH₄ mixtures. Yields of individual products were not reported.

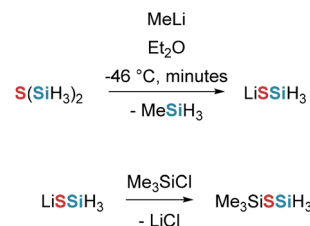


Scheme 164 Synthesis of silylsulfides starting from alkali sulfides. No yields for S(SiH₃)₂ reported.

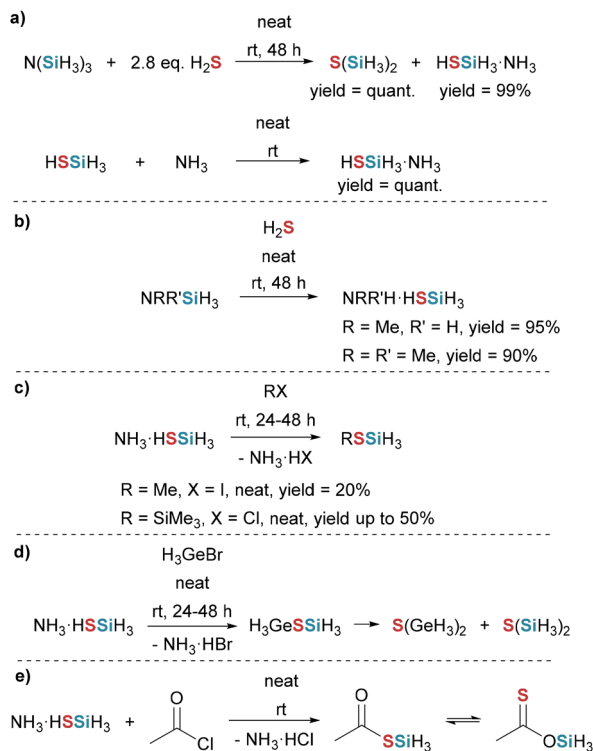




Scheme 165 Synthesis of silylsulfides using the thiolato-aluminate LiAl(SMe)₄.



Scheme 167 Generation of Li(SSiH₃) and its reactivity with Me₃SiCl. No yields were reported.



Scheme 166 Generation of disilylsulfide and the ammonium salt HSSiH₃·NH₃ and reactivity studies of the ammonium salt (path a–e). Yields of the reactions between the ammonium salt and H₃GeBr and acetylchloride not reported.

derived from N(SiH₃)₃, they similarly prepared NMe₂H·HSSiH₃ and NMeH₂·HSSiH₃ (see Scheme 166, path b). They then explored the electrophile scope of NH₃·HSSiH₃. MeI afforded MeSSiH₃, and Me₃SiCl gave Me₃SiSSiH₃, as expected (see Scheme 166, path c). Reaction with H₃GeBr produced H₃GeSSiH₃ together with the follow-up products S(GeH₃)₂ and S(SiH₃)₂ (see Scheme 166, path d). With acetyl chloride, using an excess led predominantly to SiH₃Cl, whereas sub-equimolar MeC(O)Cl furnished MeC(O)SSiH₃, which isomerized in solution to MeC(S)OSiH₃ with an isomer ratio of at least 7:1 in favor of MeC(S)OSiH₃ (see Scheme 166, path e).²⁴⁷

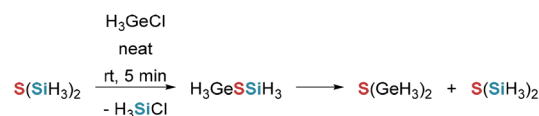
Cradock *et al.* reported that treatment of S(SiH₃)₂ with MeLi liberates MeSiH₃ in approximately 90% of the theoretical amount, forming Li(SSiH₃) (see Scheme 167). A solution of Li(SSiH₃) can then be quenched with Me₃SiCl to give the expected (Me₃Si)S(SiH₃).²⁴⁸

Finch and Van Dyke generated H₃GeSSiH₃ by treating S(SiH₃)₂ with H₃GeCl, but the product disproportionates to S(GeH₃)₂ and S(SiH₃)₂, preventing isolation of pure H₃GeSSiH₃ (see Scheme 168). S(GeH₃)₂ can be removed readily, but H₃GeSSiH₃ and S(SiH₃)₂ have very similar volatilities and could not be separated by distillation.²⁴⁹ This behaviour mirrors the disproportionation reaction observed by Cradock, Ebsworth, and Jessep when NH₃·HSSiH₃ was reacted with GeH₃Br, which likewise furnished H₃GeSSiH₃ together with S(GeH₃)₂ and S(SiH₃)₂ (see Scheme 166, path d).²⁴⁷

Cradock *et al.* published follow-up chemistry on Li(SSiH₃), reacting it with Me₃SiCl yields Me₃SiSSiH₃ (see Scheme 169, path a). Reaction with MeI results in the expected MeSSiH₃ formation; acetylchloride giving the thioester MeC(O)SSiH₃ and with Me₂SiCl₂ the corresponding Me₂Si(SSiH₃)₂ (see Scheme 169, path b and c). They also reported several unsuccessful attempts that did not deliver the targeted S-substituted products (see Scheme 169, path d). Reactions with MeSiCl₃, SiCl₄, PBrF₂, PF₃, HgCl₂, SnCl₂, and BCl₃ mainly produced S(SiH₃)₂, SiH₃F, or SiH₄. Finally, chalcogen exchange experiments showed that reacting Li(SSiH₃) with Se(SiH₃)₂, or alternatively Li(SeSiH₃) with S(SiH₃)₂, converged in both cases to Li(SeSiH₃) and S(SiH₃)₂ (see Scheme 169, path e).²¹⁹

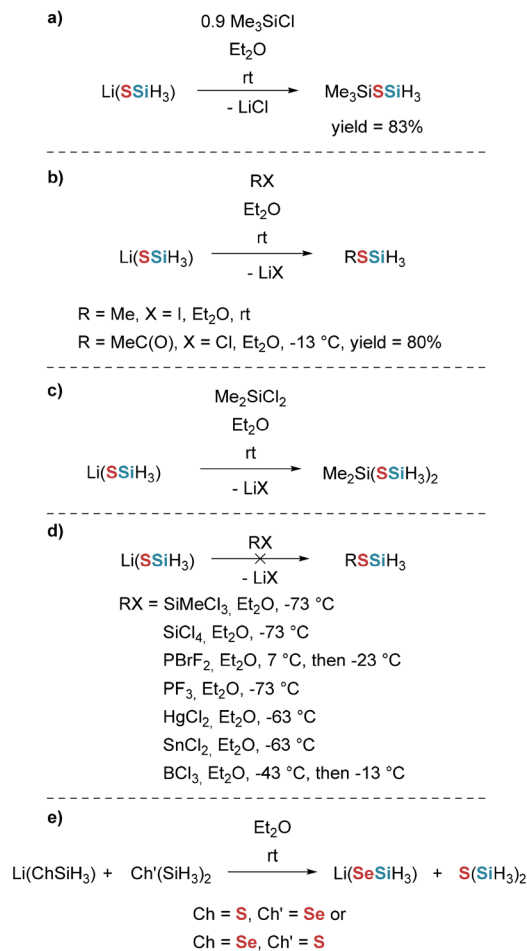
Haas and Vongher isolated the cyclic trimer (SSiH₂)₃ in 1978. Their route began with diiodosilane (SiH₂I₂) and HgS at elevated temperature, followed by filtration and solvent removal to give an oligomeric mixture. After leaving the oligomeric mixture exposed to light for about one week, this mixture converted into a gummy-like, polymeric solid. Vacuum depolymerization at 210 °C for 2 h furnished (SSiH₂)₃ (see Scheme 170), which is stable at –80 °C but slowly polymerizes at 20 °C over several days. Thermolysis in the presence of Al₂S₃ showed no change up to 170 °C; above this temperature the trimer decomposes to give mainly H₃SiSH and S(SiH₃)₂, with traces of H₂S.²⁵⁰

Haas and Hitze reported new routes to cyclotrisilathiane (SSiH₂)₃ in 1984. When Li(SSiH₃) was combined with SiH₂Cl₂,

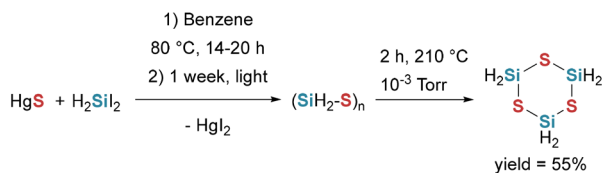


Scheme 168 Synthesis of H₃GeSSiH₃ and its disproportionation towards digermyl- and disilylsulfide, no yields were reported.



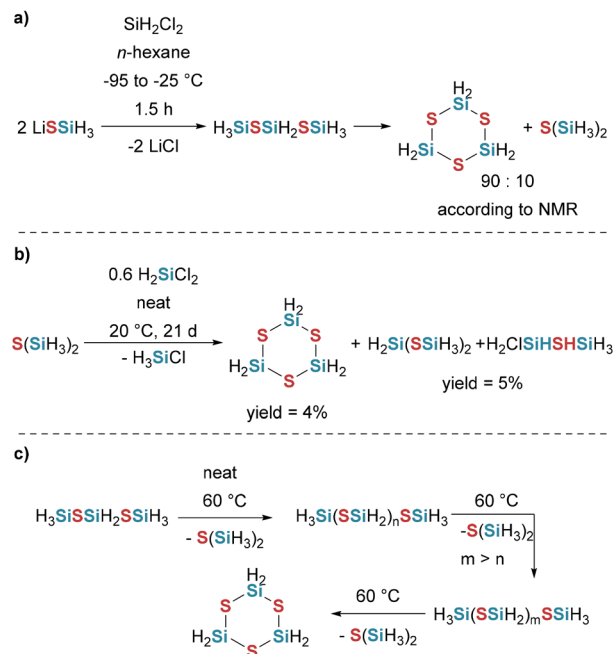


Scheme 169 Reactivity of Li(SSiH₃) with different electrophiles (path a–e). Yields of MeC(O)SSiH₃ and Me₂Si(SSiH₃)₂ were not reported.



Scheme 170 Synthesis of the cyclic (SSiH₂)₃ by reacting HgS with SiH₂I₂.

the expected H₂Si(SSiH₃)₂ was not obtained; instead, its decomposition products S(SiH₃)₂ and (SSiH₂)₃ were formed (see Scheme 171, path a). The analogous reaction with SiH₂I₂ gave similar outcomes. Notably, (SSiH₂)₃ prepared from SiH₂Cl₂ was more stable than material obtained from SiH₂I₂, which the authors attributed to iodide catalyzing polymerization. Alternatively, reacting S(SiH₃)₂ directly with SiH₂Cl₂ furnished cyclotrisilathiane and, in parallel, H₂Si(SSiH₃)₂, which they succeeded in isolating (see Scheme 171, path b). Using the purified H₂Si(SSiH₃)₂, they conducted a thermal stability study and determined its degradation pathway leading to cyclotrisilathiane (see Scheme 171, path c).²⁵¹

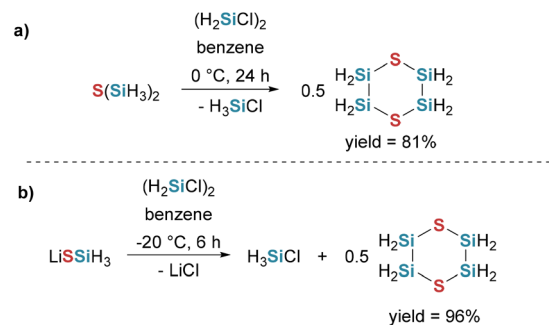


Scheme 171 Synthesis of the cyclotrisilathiane via different routes (path a–c). Yields for H₂ClSiSSiH₃ were not reported.

Haas, Sülentrup, and Krüger generated the new six-membered cyclic disilathiane (SSi₂H₄)₂ by two routes. By combining (H₂SiCl)₂ with S(SiH₃)₂ (see Scheme 172, path a), or by reacting Li(SSiH₃) with one equivalent of (ClSiH₂)₂, wherein two molecules of the intermediate (ClH₂Si)₂S(SiH₃) undergo self-condensation with elimination of SiH₃Cl to close the ring (see Scheme 172, path b).²⁵²

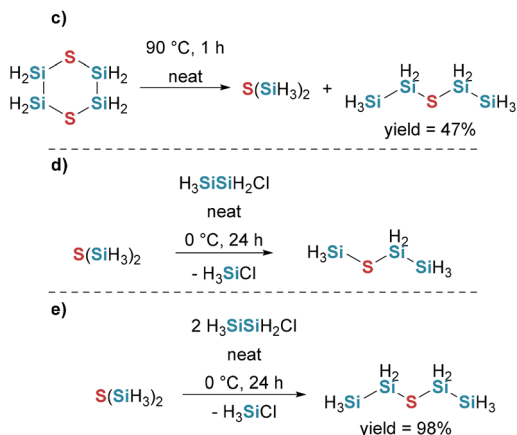
A thermolysis study at 90 °C for 1 h showed that, alongside the recovered ring, S(Si₂H₅)₂ is the principal degradation product (Scheme 173, path a). They also accessed linear disilathianes of the type (H₃Si)_mS(Si₂H₅)_{2-n} (n = 0, 1) by treating S(SiH₃)₂ with two or one equivalent(s) of Si₂H₅Cl, respectively (Scheme 173, path b and c).²⁵²

Silylselenides. Relative to oxygen and sulfur, selenium has a larger covalent radius, higher electronic polarizability, and greater metallic character, yielding softer Si–Se bonds, greater



Scheme 172 Two pathways towards the cyclic disilathiane (SSi₂H₄)₂ by Haas, Sülentrup and Krüger (path a and b).





Scheme 173 Thermolysis of disilathiane (SSi_2H_4)₂ (path a) and generation of the unsymmetrical silylsulfide (path b) and disilylsulfide (path c). No yields reported for $\text{H}_3\text{SiS}(\text{Si}_2\text{H}_5)$.

structural compliance, and stronger dielectric screening in Si-based semiconductors. Consequently, Se enables tunable band gaps and defect energetics, higher carrier mobilities with reduced interface-state densities in passivation layers, and superior electronic conductivity for conductive interlayers. Its higher atomic mass also enhances spin-orbit coupling, providing an additional lever for band-structure engineering.²⁵³

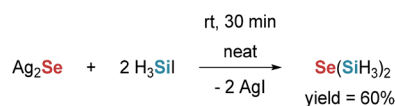
In 1955, Emel us, MacDiarmid, and Maddock attempted to synthesize $\text{Se}(\text{SiH}_3)_2$ by reacting SiH_3I with either Se or HgSe over extended periods, but both approaches failed. By contrast, using Ag_2Se led to rapid formation of $\text{Se}(\text{SiH}_3)_2$ within about 30 minutes (see Scheme 174).²²⁹

Ebsworth, Emel us, and Welcman prepared perfluoroalkyl silyl selenides RSeSiH_3 ($\text{R} = \text{CF}_3, \text{C}_3\text{F}_7$) by reacting H_3SiI with $\text{Hg}(\text{SeR})_2$ (see Scheme 175).²⁵⁴

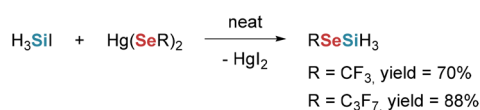
Contrary to the H_2S case, Ebsworth, Glidewell, and Sheldrick reported that $\text{P}(\text{SiH}_3)_3$ reacts with H_2Se to furnish the expected $\text{Se}(\text{SiH}_3)_2$ (see Scheme 176).²⁴⁴

Cradock and Ebsworth obtained $\text{Se}(\text{SiH}_3)_2$ in quantitative yield by reacting Li_2Se with H_3SiBr (see Scheme 177), providing a straightforward halide/selenide metathesis.²⁵⁵

Drake and Riddle applied silent electrical discharge to equimolar $\text{SiH}_4/\text{H}_2\text{Se}$ and observed, in addition to higher silanes,



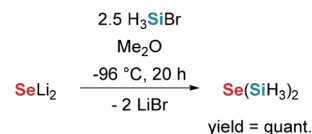
Scheme 174 Synthesis of disilylselenide using Ag_2Se and SiH_3I .



Scheme 175 Synthesis of mixed silylselenides.



Scheme 176 Generation of disilylselenide through the reaction of trisilylphosphide and H_2Se .

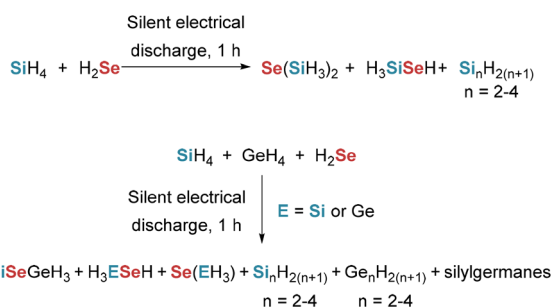


Scheme 177 Synthesis of disilylselenide using lithiumselenide and SiH_3Br .

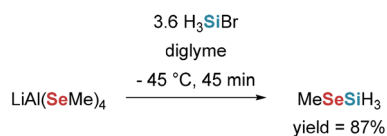
the formation of $\text{Se}(\text{SiH}_3)_2$ and H_3SiSeH (see Scheme 178). With ternary $\text{SiH}_4/\text{GeH}_4/\text{H}_2\text{Se}$ mixtures, the product spectrum expanded to include $\text{H}_3\text{SiSeGeH}_3$, H_3ESeH and $\text{Se}(\text{EH}_3)_2$ ($\text{E} = \text{Si}, \text{Ge}$), along with higher silanes, higher germanes, and silylgermanes.²⁴⁵

Anderson and Drake synthesized MeSeSiH_3 by combining H_3SiBr with $\text{LiAl}(\text{SeMe})_4$ (see Scheme 179), directly analogous to the sulfur congener prepared from $\text{LiAl}(\text{SMe})_4$ (Scheme 165).²⁴⁶

Cradock, Ebsworth, and Jessep showed that $\text{N}(\text{SiH}_3)_3$ reacts with H_2Se to give $\text{Se}(\text{SiH}_3)_2$ together with the ammonium selenosilane $\text{NH}_3 \cdot \text{HSeSiH}_3$ (see Scheme 180, path a). Replacing NH_3 with partially substituted amines such as HNMeSiH_3 or Me_2NSiH_3 resulted in the formation of the corresponding salts $\text{HNRR}' \cdot \text{HSeSiH}_3$ ($\text{R}, \text{R}' = \text{H}, \text{Me}$) (see Scheme 180, path b). The $\text{NH}_3 \cdot \text{HSeSiH}_3$ adduct was examined in detail: methylation with MeI delivered MeSeSiH_3 ; treatment with Me_3SiCl afforded

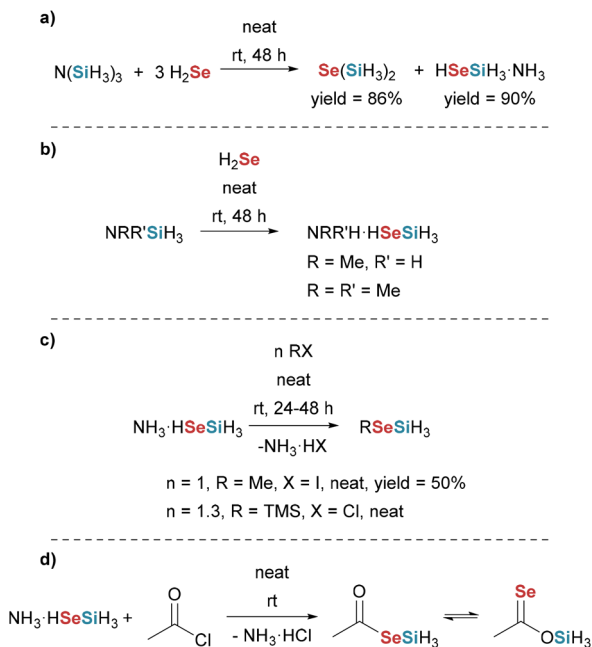


Scheme 178 Silent electrical of $\text{SiH}_4/\text{H}_2\text{Se}$ and $\text{SiH}_4/\text{GeH}_4/\text{H}_2\text{Se}$ mixtures. Yields of individual products were not reported.

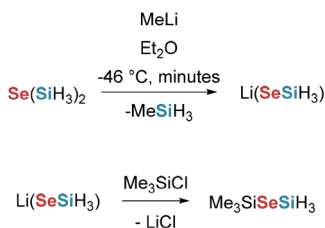


Scheme 179 Synthesis of the mixed MeSeSiH_3 selenide using $\text{LiAl}(\text{SeMe})_4$ and SiH_3Br .





Scheme 180 Generation of disilylselenide and the ammonium salt HSeSiH₃·NH₃ and reactivity studies of the ammonium salt (path a–d). Yields of the reaction between the ammonium salt and Me₃SiCl and acetylchloride not reported.

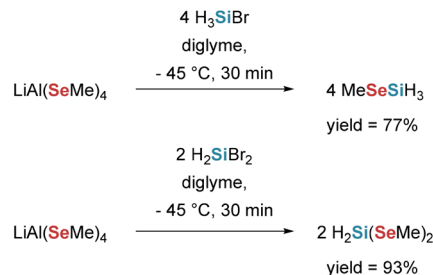


Scheme 181 Generation of Li(SeSiH₃) by the reaction of disilylselenide and MeLi and its reaction with Me₃SiCl. Yields of products were not determined.

Me₃SiSeSiH₃, which slowly disproportionated at room temperature to (Me₃Si)₂Se and Se(SiH₃)₂ (see Scheme 180, path c); and exposure to PF₂Br produced a complex mixture containing PF₃, SiH₃F, unreacted PF₂Br, H₂Se, Se(SiH₃)₂, and SiH₃·NH·PF₂. Finally, reaction with acetyl chloride yielded a mixture of Se(SiH₃)₂, diacetyl selenide [Se[(O)CMe]₂], and the desired silylselenoacetate MeC(O)SeSiH₃, which could not be isolated; nonetheless, the isomer ratio at room temperature was determined to be approximately 2.5:1, with MeC(O)SeSiH₃ as the major isomer (see Scheme 180, path d).²⁴⁷

Cradock *et al.* reported that treating Se(SiH₃)₂ with MeLi evolves methylsilane (MeSiH₃) in approximately 90% of the theoretical amount and forms Li(SeSiH₃). The resulting solution of Li(SeSiH₃) can then be quenched with Me₃SiCl to afford the expected Me₃SiSeSiH₃ (see Scheme 181).²⁴⁸

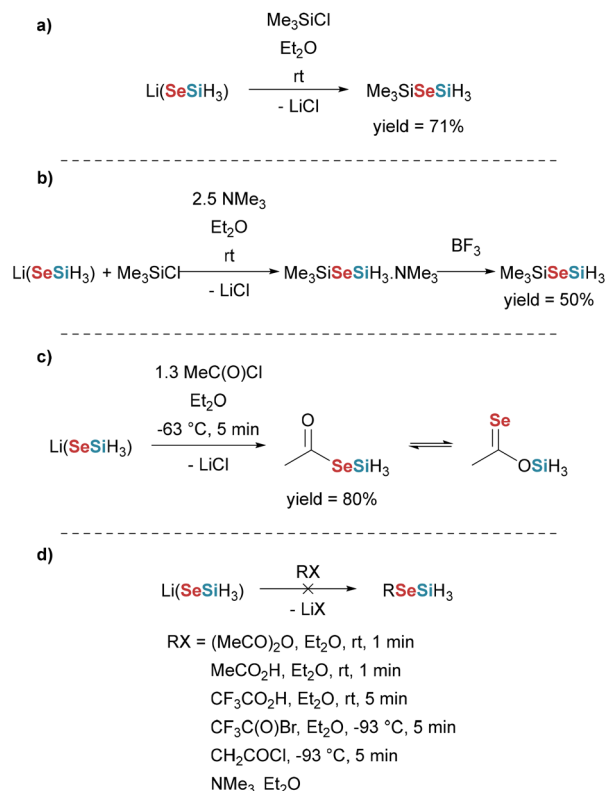
Barker, Drake, and Hemmings showed that LiAl(SeMe)₄ reacts with H₃SiBr to give H₃SiSeMe and with H₂SiBr₂ to give



Scheme 182 Generation of mixed silylselenides using LiAl(SeMe)₄.

H₂Si(SeMe)₂; both products were successfully isolated, and in each case only traces of SiH₄ were detected as a byproduct (see Scheme 182).²⁵⁶

Cradock *et al.* showed that Li(SeSiH₃) reacts cleanly with Me₃SiCl to furnish Me₃SiSeSiH₃ (see Scheme 183, path a). If NMe₃ is present prior to quenching, the Lewis adduct Me₃SiSeSiH₃·NMe₃ is formed, subsequent treatment with BF₃ releases the free selenide (with formation of NMe₃·BF₃) (see Scheme 183, path b). Acylation with acetyl chloride affords MeC(O)SeSiH₃, which isomerizes in solution and exists in equilibrium with MeC(Se)OSiH₃ (see Scheme 183, path c). Extending this electrophile scope gave divergent outcomes. With MeC(O)₂O or MeCO₂H, the main product is again the acetyl silyl selenide MeC(O)SeSiH₃. In contrast, CF₃CO₂H reacts mainly to the silyl trifluoroacetate CF₃C(O)OSiH₃, while



Scheme 183 Reactivity scope of Li(SeSiH₃) (path a–d).



the acyl halides $\text{CF}_3\text{C}(\text{O})\text{Br}$ and $\text{CClH}_2\text{C}(\text{O})\text{Cl}$ lead predominantly to $\text{Se}(\text{SiH}_3)_2$. No reaction is observed with NMe_3 alone under the same conditions (see Scheme 183, path d).²¹⁹

Drake and Hemmings synthesized phenylselenosilanes by two complementary routes: reaction of $\text{Li}(\text{SePh})$ with H_3SiBr to give PhSeSiH_3 , and reaction of the selenoaluminate $\text{LiAl}(\text{SePh})_4$ with H_2SiBr_2 to furnish $\text{H}_2\text{Si}(\text{SePh})_2$ (see Scheme 184).²⁵⁷

Drake, Glavinčevski, and Hemmings prepared $\text{Se}(\text{SiH}_3)_2$ by reacting H_3SiI with the selenoaluminate $\text{LiAl}(\text{SeH})_4$, which serves as an efficient selenide-transfer reagent (see Scheme 185).²⁵⁸

Haas and Hitze were the first to obtain the cyclic selenosilane $(\text{SeSiH}_2)_3$ by heating HgSe with H_2SiI_2 to 120 °C. The initial reaction produced oligomeric mixtures, which upon depolymerization under vacuum at 140 °C, followed by recrystallization in benzene furnished crystalline $(\text{SeSiH}_2)_3$ (see Scheme 186, path a). The crystals are unstable at 20 °C and revert to an oligomeric mixture within 1–2 hours. Attempts to reach the same product *via* Na_2Se and H_2SiI_2 in benzene at 20 °C led to decomposition into iodine and selenium; per-

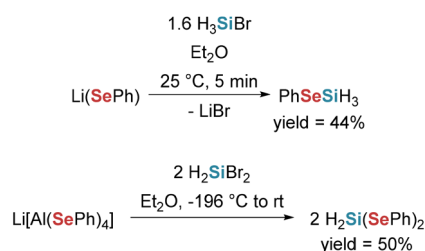
forming the reaction in ether gave the same outcome, with decomposition occurring above –40 °C. Reactions between SiH_2I_2 and $\text{K}_6[\text{HgSe}_4]$ behaved similarly (see Scheme 186, path b). When Ag_2Se was combined with H_2SiI_2 , no reaction was observed at 20 °C, and upon refluxing the mixture, SiH_3I and $\text{Se}(\text{SiH}_3)_2$ were obtained instead of $(\text{SeSiH}_2)_3$ (see Scheme 186, path c).²⁵⁹

Haas, Sülentrup, and Krüger generated the new cyclic compound $(\text{SeSi}_2\text{H}_4)_2$ by reacting $(\text{SiH}_2\text{Cl})_2$ with $\text{Se}(\text{SiH}_3)_2$, with elimination of H_3SiCl (see Scheme 187, path a). Thermolysis of this ring at 90 °C for 1 h gave $\text{Se}(\text{Si}_2\text{H}_5)_2$ as the principal degradation product together with Si_2H_6 (see Scheme 187, path b). They also obtained the new linear disilaseselenides $(\text{H}_3\text{Si})_m\text{Se}(\text{Si}_2\text{H}_5)_{2-n}$ ($n = 0, 1$) by reacting $\text{Se}(\text{SiH}_3)_2$ with one or two equivalents of $\text{Si}_2\text{H}_5\text{Cl}$ (see Scheme 187, path c and d).²⁵²

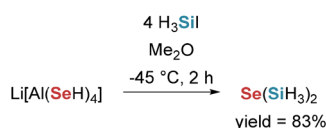
Silyltelluride. Relative to O, S, and Se, tellurium has the largest covalent radius, highest electronic polarizability, and greatest metallic character in group 16, yielding the softest Si–Te bonds and enhanced lattice compliance in Si-based semiconductors. These attributes enable deeper band-structure modulation, tuning band gaps or sub-bandgap states into the near-IR, and can produce higher electronic conductivity in Te-rich chalcogenide passivation or interlayer stacks.²⁶⁰

Bürger and Goetze were the first in 1967 to synthesize $\text{Te}(\text{SiH}_3)_2$ by reacting Li_2Te with SiH_3I in tetralin and heating the mixture at 70 °C for 3 days (see Scheme 188).²⁶¹

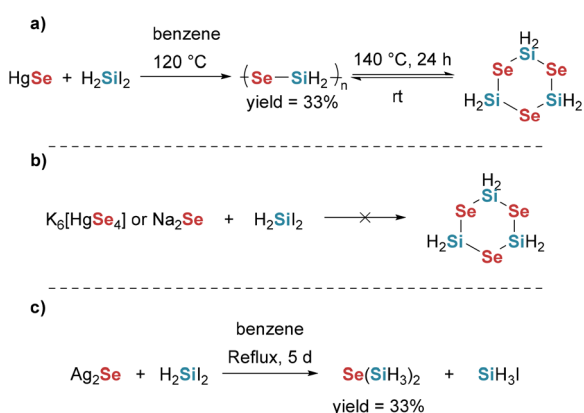
Two years later, Cradock, Ebsworth, and Rankin obtained $\text{Te}(\text{SiH}_3)_2$ by reacting SiH_3Br with Li_2Te in Me_2O at low temperature (see Scheme 189).²⁵⁵



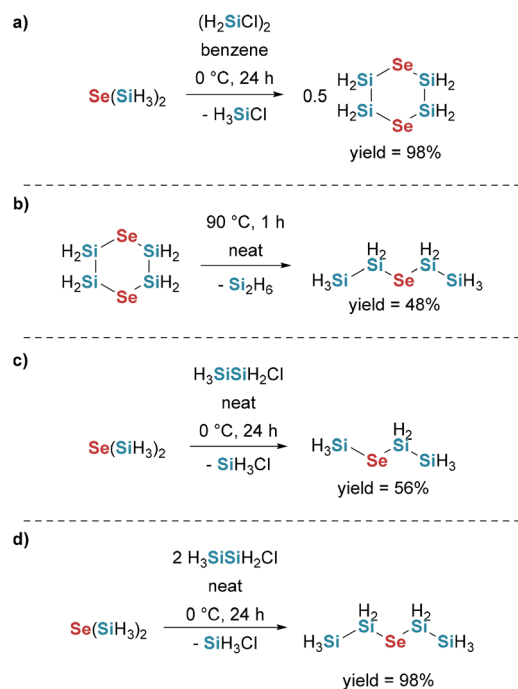
Scheme 184 Generation of phenylselenosilanes.



Scheme 185 Synthesis of disilylselenide using selenoaluminate and SiH_3I .

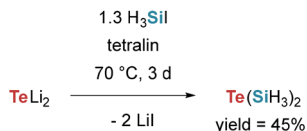
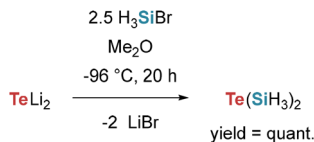


Scheme 186 Attempted reactions towards the cyclic selenosilane $(\text{SeSiH}_2)_3$ and its successful generation using HgSe and SiH_2I_2 (path a–c).



Scheme 187 Synthesis of the cyclic disilylselenide $(\text{SeSi}_2\text{H}_4)_2$ *via* different pathways (path a) and generation of mixed and symmetrical disilylselenides (path b–d).

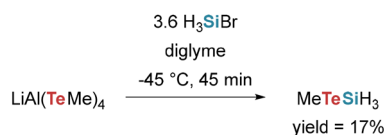
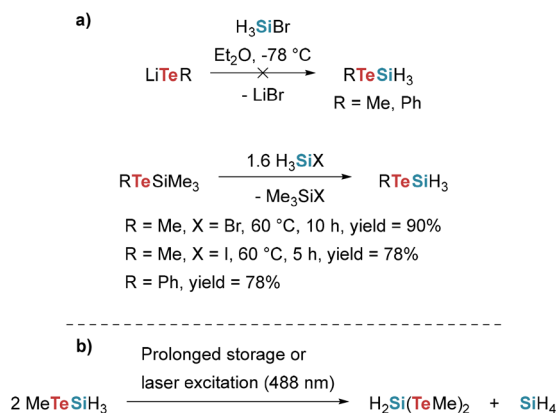
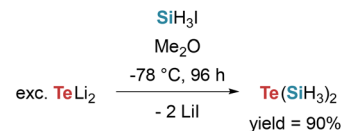


Scheme 188 Synthesis of Te(SiH₃)₂ using TeLi₂ and SiH₃I in tetralin.Scheme 189 Synthesis of Te(SiH₃)₂ using TeLi₂ and SiH₃Br.

Anderson and Drake prepared MeTeSiH₃ by reacting the telluroaluminate LiAl(TeMe)₄ with SiH₃Br, but the product was obtained only in low yield (see Scheme 190).²⁴⁶

Drake and Hemmings attempted to prepare RTeSiH₃ (R = Me, Ph) by reacting LiTeR with SiH₃Br, but they were unable to isolate the desired products; instead, they observed Te(SiH₃)₂ and traces of silane among the volatile species alongside intractable polymeric material. In contrast, an exchange route employing RTeMe₃Si (R = Me, Ph) with SiH₃Br or SiH₃I, eliminating Me₃SiBr or Me₃SiI, results in a successful RTeSiH₃ formation (see Scheme 191, path a). They also found that MeTeSiH₃ decomposes after prolonged storage or upon laser excitation to give H₂Si(TeMe)₂ and SiH₄ (see Scheme 191, path b).²⁶²

Drake, Glavinčevski, and Hemmings later synthesized Te(SiH₃)₂ by reacting SiH₃I with an excess of Li₂Te at low temperatures in Me₂O (see Scheme 192).²⁵⁸

Scheme 190 Synthesis of the mixed MeTeSiH₃ using LiAl(TeMe)₄ and SiH₃Br.Scheme 191 Attempted and successful reaction towards RTeSiH₃ (path a) and decomposition products of MeTeSiH₃ (path b).Scheme 192 Generation of disilyltelluride using SiH₃I and TeLi₂ in ether.

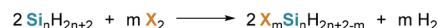
Functionalization with group 7 (synthesis of silylhalogenes)

Halohydrosilanes represent a central class of silicon compounds in which Si–X bonds (X = F, Cl, Br, I) replace one or more Si–H or Si–Si functionalities. The strong polarity and thermodynamic stability of Si–halogen bonds significantly influence their chemical behaviour: halohydrosilanes are highly sensitive to hydrolysis, readily undergo redistribution reactions, and frequently serve as activated intermediates in silicon bond construction. From a synthetic perspective, they occupy a strategic position between elemental silicon and hydrosilanes, acting both as precursors to reduce silicon species and electrophilic building blocks for tailored silicon frameworks.

Industrial and technological interest in halohydrosilanes is driven largely by thin-film deposition processes. In chemical vapor deposition and liquid phase deposition or solution-based routes, halohydrosilanes provide a controlled silicon delivery, variable reactivity, and favourable volatility. Chlorinated and fluorinated silanes, in particular, are widely exploited for semiconductor fabrication, surface passivation, and the formation of silicon-containing coatings. Their decomposition pathways allow precise regulation of film growth kinetics, impurity profiles, and microstructure – critical parameters for semiconductor devices, photovoltaics, and protective layers. Furthermore, halohydrosilanes serve as key intermediates in the preparation of higher hydrosilanes and functional silicon oligomers, linking fundamental synthesis with applied materials chemistry.²⁶³

Synthetic access to halohydrosilanes generally follows several recurring strategies (see Scheme 193).

i) Direct halogenation of hydrosilanes



ii) Electrophilic dearylation of arylsilanes



iii) Halogen exchange reaction



iv) Reactive Silylene

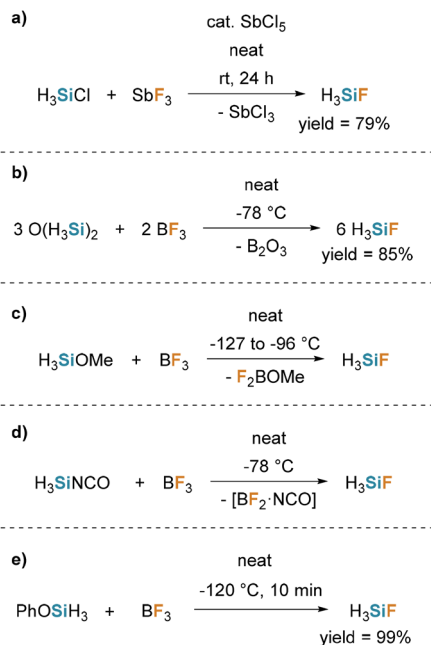


v) Partial hydrogenation of siliconhalides



Scheme 193 Method (i)–(v) for the formation of different halohydrosilanes.





Scheme 194 Methods for the synthesis of monofluorosilane (path a–e). For the reactions of $\text{H}_3\text{SiOMe} + \text{BF}_3$ (path c) and $\text{SiH}_3\text{NCO} + \text{BF}_3$ (path d) no yields reported.

Structurally, halohydrosilanes can be divided into acyclic perhalogenated, cyclic compounds and mixed derivatives. The following sections summarize the principal compound classes and their synthetic approaches, organized according to the halogen substituent – beginning with fluorohydrosilanes and proceeding through chlorosilanes and bromohydrosilanes to iodohydrosilanes – reflecting their sequence in the periodic table.

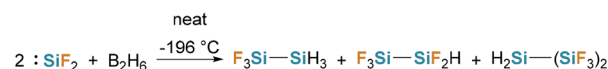
Fluorohydrosilanes. Intensive investigations towards the synthesis, properties and reactivity of fluorohydrosilanes began in the early 1970s. Particular attention has been devoted to disilane derivatives because of their relevance to semiconductor processing, whereas comparatively fewer studies have addressed the preparation of higher fluorinated silanes.²⁶⁴

Monofluorosilane (H_3SiF) has been prepared primarily through electrophilic fluorination or Lewis-acid-induced Si–X bond cleavage reactions. Early work by Emeléus and Maddock demonstrated that H_3SiF can be obtained in approximately 79% yield by fluorination of chlorosilane with antimony trifluoride at room temperature (see Scheme 194, path a), although competing oxidative fluorination and disproportionation limited product stability and purity.²⁶⁵ A significant cleaner and higher-yielding approach was later introduced by Onyszczuk, who showed that boron trifluoride induces efficient Si–O bond cleavage in disiloxane, affording H_3SiF in up to 85% isolated yield under solvent-free conditions (see Scheme 194, path b).²³³ Related studies by Sternbach and MacDiarmid further established that boron trifluoride readily converts alkoxy silanes into H_3SiF , confirming the general applicability of BF_3 -mediated fluorination pathways, although this route was not optimized for preparative yields (see

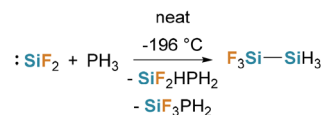
Scheme 194, path c).²³² In addition, Ebsworth and Mays reported the formation of H_3SiF from the reaction of silyl isocyanate with boron trifluoride at -78°C , an observation made in the course of probing the reactivity of silylisocyanate rather than as dedicated synthetic approach to H_3SiF (see Scheme 194, path d).¹⁷² Treatment of PhOSiH_3 with HF affords H_3SiF in excellent yields (see Scheme 194, path e).²³⁶ The most common method for the synthesis of fluorohydrooligosilanes is the co-condensation of SiF_2 with B_2H_6 at a cool copper surface (method iv). The reactive SiF_2 intermediate is generated *in situ* by passing SiF_4 over elemental silicon at high temperatures. Under these conditions, a mixture of $\text{F}_3\text{Si-SiH}_3$, $\text{F}_3\text{Si-SiF}_2\text{H}$ and $\text{H}_2\text{Si-(SiF}_3)_2$ is formed (see Scheme 195). Although isolated yields were not determined, spectroscopic analyses indicated that $\text{H}_2\text{Si-(SiF}_3)_2$ is formed in relatively higher amounts, while $\text{F}_3\text{Si-SiH}_3$ and $\text{F}_3\text{Si-SiF}_2\text{H}$ are produced in comparable portions. This species were separated by high vacuum, low temperature fractional condensation.²⁶⁶

$\text{F}_3\text{Si-SiH}_3$ is also formed as a byproduct during the synthesis of SiF_2HPH_2 and SiF_3PH_2 via the condensation of SiF_2 with PH_3 (method iv) (see Scheme 196).²⁶⁷

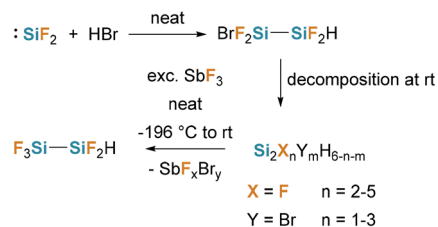
Reactions of SiF_2 with protic reagents (such as HBr) typically generate initially formed fluorinated bromodisilanes that are thermally unstable and undergo rapid secondary transformation. Scheme 197 shows that the reaction with HBr first produces 1-bromo-1,1,2,2-tetrafluorodisilane, which decomposes quickly to a mixture of different mixed halohydrosilanes. Subsequent treatment of the resulting mixture with excess SbF_3 converts it efficiently into $\text{F}_3\text{Si-SiF}_2\text{H}$.²⁶⁸



Scheme 195 Formation of different fluorohydrosilanes from Si_2F with B_2H_6 ; no yields reported.



Scheme 196 Formation of $\text{F}_3\text{Si-SiH}_3$ as a byproduct during the condensation of SiF_2 and PH_3 ; no yields reported.



Scheme 197 Treatment of SiF_2 with HBr yielding in the unstable $\text{BrF}_2\text{Si-SiF}_2\text{H}$. Subsequent treatment of decomposition products with SbF_3 affording $\text{F}_3\text{Si-SiF}_2\text{H}$. No yields reported.

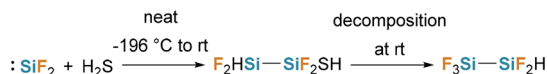


A similar pattern is observed with H₂S: the initially formed silanethiol F₂HSi-SiF₂SH decomposes within minutes, again yielding F₃Si-SiF₂H (see Scheme 198).²⁶⁹

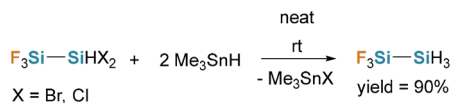
Direct fluorination routes of hydrosilanes (method i) have not been reported, but indirect access is possible through selective hydrogenation of mixed halodisilanes (method v). In compounds containing both, fluorine and chlorine or bromine substituents, the heavier halides can be selectively reduced with Me₃SnH without cleaving Si-F bonds. Using this strategy, F₃Si-SiH₃ can be obtained in high yields from the corresponding mixed halo precursors (see Scheme 199).²⁷⁰

In contrast, partially fluorinated bromodisilanes do not undergo clean hydrogenation. Instead, F/Br redistribution occurs prior to reduction, producing mixtures of fluorinated disilanes. Stronger hydride reagent led to even less selective outcomes, promoting Si-Si bond cleavage and partial reduction of Si-F bonds. Together, these observations highlight the delicate balance between halogen redistribution, bond stability and reductive pathways in fluorinated disilane chemistry.²⁷⁰

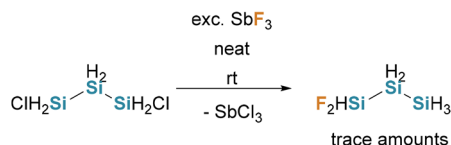
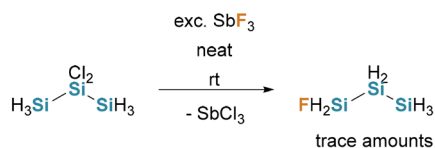
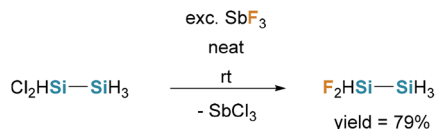
FH₂Si-SiH₃ was obtained by fluorination of dichlorodisilanes or dichlorotrisilane with SbF₃ (method iii) (see Scheme 200).^{271,272}



Scheme 198 Reaction of SiF₂ with H₂S. Decomposition at room temperature affords F₃Si-SiF₂H. No yields reported.



Scheme 199 Hydrogenation of mixed halodisilane yielding in F₃Si-SiH₃.



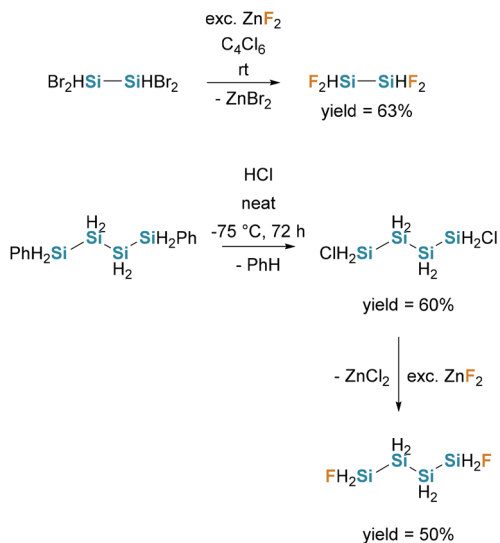
Scheme 200 Fluorination of oligohydrosilanes with SbF₃.

ZnF₂ is another well-established fluorinating agent and has been used to prepare F₂HSi-SiHF₂ and FH₂Si-(SiH₂)₂-SiH₂F from their corresponding chlorinated or brominated precursors (method iii) (see Scheme 201).^{273,274}

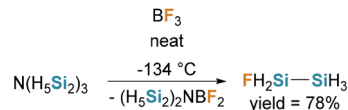
In addition, cleavage of Si-N bonds in N(Si₂H₅)₃ by BF₃ provides another pathway to FH₂Si-SiH₃ (see Scheme 202).¹⁵⁰

Moreover, it is possible to fluorinate different methoxyoligo-silanes to the corresponding branched fluorohydrosilanes with BF₃ (see Scheme 203).²⁷⁵

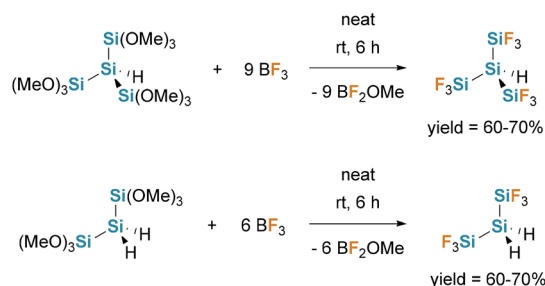
Finally, fluorohydrosilanes can be accessed *via* an electrical discharge approach. In this method, various monofluorosilanes were converted into F₂HSi-SiH₃, FH₂Si-SiH₂F, F₂HSi-SiHF₂, F₃Si-SiF₂H, F₂HSi-Si₂H₅ and F₃Si-Si₂H₅. However, the



Scheme 201 Fluorination of chloro-, and bromooligohydrosilanes with ZnF₂.



Scheme 202 Formation of FH₂Si-SiH₃ *via* the reaction of N(H₅Si₂)₃ and BF₃.



Scheme 203 Fluorination of branched methoxysilanes with BF₃.



resulting product mixtures proved difficult to impossible to separate.^{271,276}

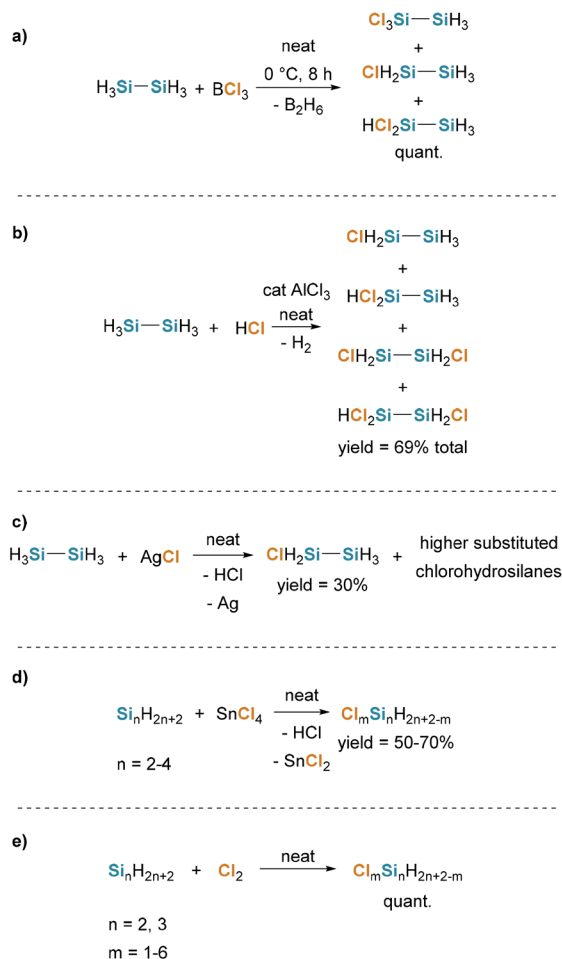
Chlorohydrosilanes. Chlorosilanes, particularly chlorohydrosilanes, serve as key precursors in the production of high-purity polycrystalline silicon. Driven by the rapid expansion of photovoltaic technologies, global polysilicon production capacity reached approximately 1.6 million metric tons in 2023.²⁷⁷ The overwhelming majority of this material is manufactured *via* chemical vapour deposition (CVD) using trichlorosilane as primary feedstock.²⁷⁸

Already in 1919 Stock and Somieski reported the synthesis of monochlorosilane (H_3SiCl).¹⁰ They treated monosilane with hydrogen chloride and catalytic amounts of AlCl_3 (method i) (see Scheme 204). Heating this mixture to 100 °C for 30 hours afforded ClSiH_3 in 50–55% yield, with dichlorosilane as byproduct (ratio $\text{ClSiH}_3:\text{Cl}_2\text{SiH}_2 = 4:1$). More recent studies showed, that the yields of ClSiH_3 can be increased to 76% when a zeolite catalysator (Na-ZSM-5) is used.²⁷⁹

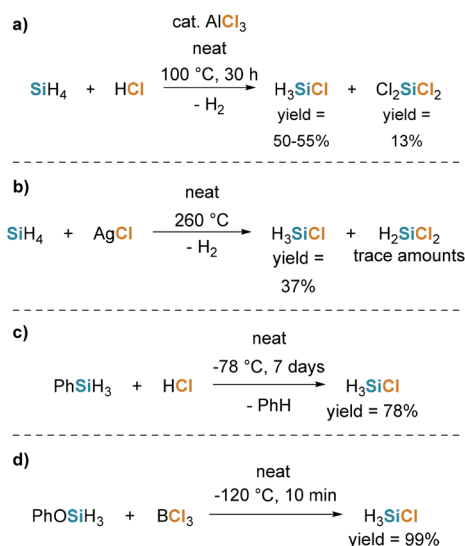
Hollandsworth *et al.* showed, that monosilane can also be chlorinated with silver chloride to afford monochlorosilane (see Scheme 204).²⁸⁰ When phenylsilane (PhSiH_3) is used as starting material, H_3SiCl could be obtained in yields of 78% (method ii) (see Scheme 204, path c).²⁸¹ In addition, Glidewell and Rankin showed, that treatment of PhOSiH_3 with HCl affords H_3SiCl (see Scheme 204, path d).²³⁶

Starting in the 1960s, synthetic efforts towards chlorooligohydrosilanes increasingly focused on the chlorination (method i) of smaller hydrosilanes such as disilane, trisilane and tetrasilane.

Early studies by Drake *et al.* and van Dyke *et al.* established boron trichloride as an efficient chlorination reagent for these substrates (see Scheme 205, path a).^{271,276,282,283} In analogy to observations made of monosilane, hydrogen chloride²⁸⁴ and silverchloride^{285,286} were subsequently shown to be suitable chlorination agents for disilane as well (see Scheme 205, path



Scheme 205 Chlorination of oligohydrosilanes using different chlorination agents (path a–e).



Scheme 204 Methods for the synthesis of monochlorosilane (path a–d).

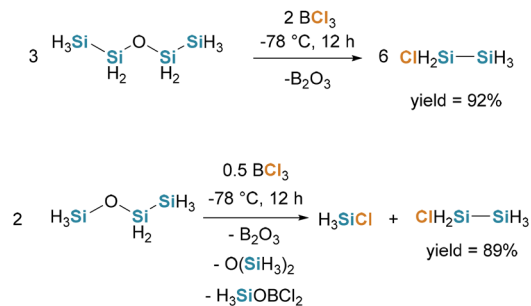
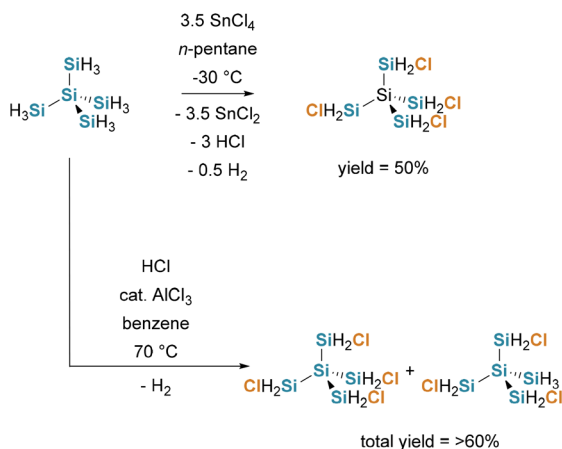
b and c). Beyond these systems, tetrachlorostannane was demonstrated to chlorinate di-, tri-, and tetrasilane efficiently, thereby broadening the scope of applicable chlorination reagents (see Scheme 205, path d).²⁸⁷ Finally, direct halogenation using molecular chlorine was reported by Fehér and co-workers, providing a more straightforward, albeit harsher, approach to the chlorination of disilane (see Scheme 205, path e).²⁸⁸

However, all of the mentioned methods for direct halogenation of oligohydrosilanes yield complex product mixtures that often require time consuming separation or further derivatization before reliable analysis is possible.^{271,276,284,286–289} Another challenge is the tendency of higher silanes to undergo isomerization.²⁸³

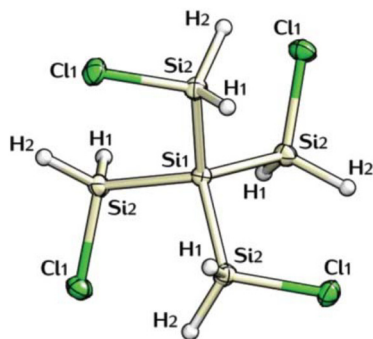
Van Dyke, and MacDiarmid prepared the silylethers $\text{H}_3\text{SiOSi}_2\text{H}_5$ and $\text{H}_3\text{SiOSi}_2\text{H}_5$ (see Scheme 145). In subsequent reactions, both $\text{O}(\text{Si}_2\text{H}_5)_2$ and $\text{H}_3\text{SiOSi}_2\text{H}_5$ reacted with BCl_3 to give $\text{Si}_2\text{H}_5\text{Cl}$ as the main product (see Scheme 206).²³⁴

In 2012 Stueger *et al.* demonstrated the selective chlorination of neopentasilane with 3.5 equivalents SnCl_4 to afford tetra(chlorosilyl)silane (see Scheme 207 and Fig. 15).²⁹⁰



Scheme 206 Reaction of silyl ethers with BCl_3 .

Scheme 207 Synthesis of branched chlorooligohydrosilanes.

Fig. 15 Crystal structure of $\text{Si}(\text{SiH}_2\text{Cl})_4$ reproduced from Stueger *et al.*⁴⁸ with permission from American Chemical Society, © 2012.

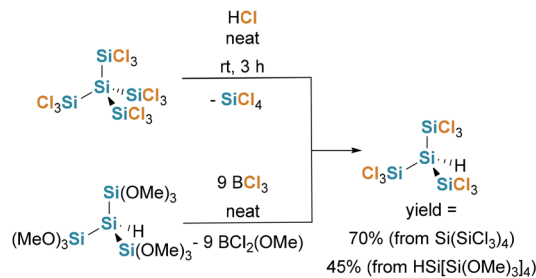
However, a significant drawback of employing SnCl_4 as halogenating reagent is the formation of large quantities of SnCl_2 , which are difficult to remove completely, particularly on a preparative scale. To address limitation, the authors also examined an alternative protocol based on gaseous HCl in presence of catalytic AlCl_3 and obtained the selective formation of tetra(chlorosilyl)silane (85%), accompanied only by minor amounts of 1,2,3-trichloroneopentasilane as byproduct (15%) in a total yield of more than 60%.²⁹¹

An additional example for the synthesis of branched chlorohydrosilanes, is the preparation of $\text{HSi}(\text{SiCl}_3)_3$. Höfler *et al.* reported two efficient synthetic approaches to this compound. The first involves the reaction of dodecachloroneopentasilane ($\text{Si}(\text{SiCl}_3)_4$) with HCl , eliminating SiCl_4 , affording the target product in 70% yield (see Scheme 208). The second approach is based on the chlorination of $\text{HSi}[\text{Si}(\text{OMe})_3]_3$ with nine equivalents of BCl_3 , providing $\text{HSi}(\text{SiCl}_3)_3$.²⁹²

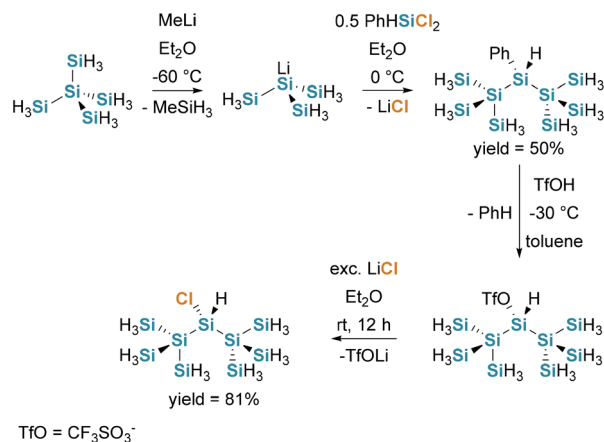
The synthesis of an even higher branched chlorooligohydrosilane was demonstrated by Christopoulos *et al.* First, they generated phenylnonasilane *via* the reaction of the trissilyllithium anion and 0.5 equivalents dichlorophenylsilane. Subsequent treatment with triflic acid affords the triflate substituted nonasilane, which can be chlorinated with an excess of lithiumchloride and the chlorononasilane can be obtained in yields of 81% (see Scheme 209).⁴⁹

An alternative method for the synthesis of chlorohydrosilanes is the partial hydration of perchlorooligosilanes using hydrating reagents, such as LiAlH_4 or Bu_3SnH (method v). But also these approach were found to yield in unselective product mixtures.^{107,109}

A more attractive strategy involves the controlled partial hydrogenation (method v) with substoichiometric amounts of $i\text{-Bu}_2\text{AlH}$ (see Scheme 210). This methodology enables access

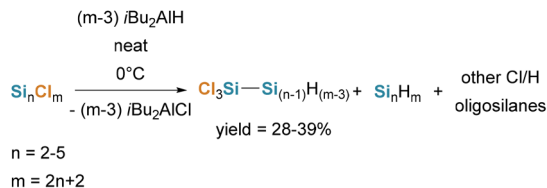


Scheme 208 Two methods for the synthesis of hexachlorotrisilane.



Scheme 209 Synthesis of chlorononasilane starting from neopentasilane.





Scheme 210 Synthesis of chlorooligosilanes via partial hydrogenation.

to broader range of chlorohydrooligosilanes under comparatively mild conditions. *i*-Bu₂AlH promotes selective Si–Cl hydrogenation in both linear and branched chlorooligosilanes without inducing Si–Si bond cleavage.²⁹¹

An additional method to prevent the complete hydrogenation of oligochlorosilanes with LiAlH₄ is the implementation of N(SiMe₃)₂ or N(SiMe₂Ph)₂ substituents as protecting groups into the molecule (see Scheme 211). After the hydrogenation, these groups can easily be cleaved off with HCl.¹³⁹

In contrast to hydrosilanes, aryl-substituted silanes (Ar_mSi_nH_{2n+2-m}) are excellent starting materials for the selective synthesis of chlorohydrosilanes (Cl_mSi_nH_{2n+2-m}, *n* = 2–7, *m* = 1–9) (Scheme 212). The aryl substituents can be cleanly replaced by chlorine upon treatment with liquefied hydrogen chloride or with HCl solutions in benzene, enabling controlled halogen incorporation with good selectivity (method ii).^{252,273,274,293,294}

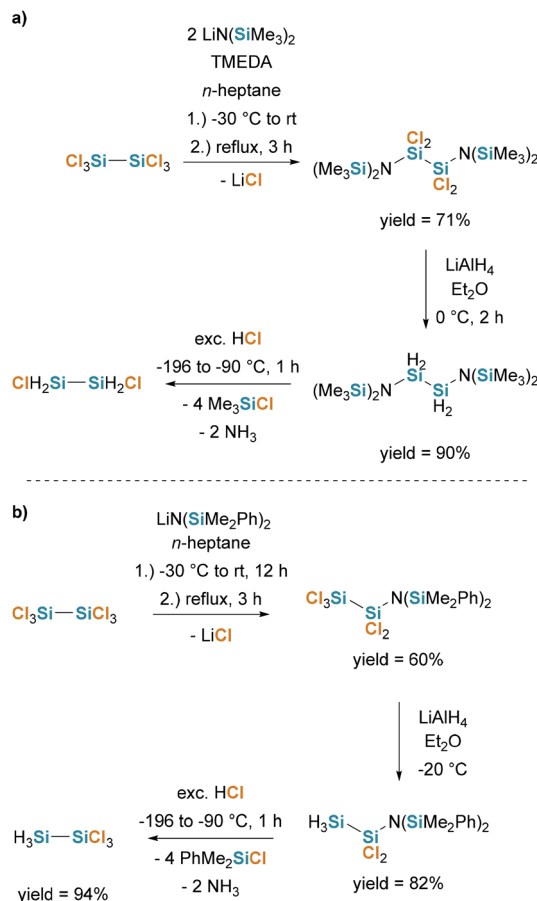
To suppress equilibrium of the chlorinated products,²⁹⁵ Uhlig *et al.* proposed a stepwise dephenylation strategy in which triflic acid is first used to remove the organic substituents, followed by either hydride reduction with LiAlH₄ or chlorination with Et₃NHCl (see Scheme 213). Using Ph₃Si–SiH₃ as precursor, this route enables the selective formation of HCl₂Si–SiH₃ and Cl₃Si–SiH₃, respectively.²⁹⁶

An analogous electrical discharge strategy for the formation of fluorohydrosilanes, has also been applied for chlorohydrosilanes. Under comparable conditions, monochlorosilane undergoes coupling reactions to give mixtures of chloro-substituted di- and oligosilanes. Similar to the fluorinated systems, these discharge processes produce complex product distributions, and separation of the individual components is challenging.²⁷⁶

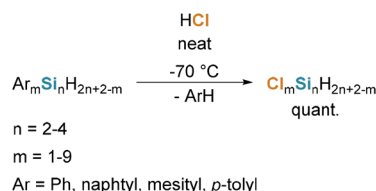
Bromohydrosilanes. Also bromohydrosilanes have attracted high interest as alternative silicon precursors for vapor-phase deposition processes, particularly in efforts to move beyond the well-established chlorosilane chemistry used in large-scale silicon production.²⁹⁷

Monobromosilane can be synthesized by reacting monosilane with various bromination agents, including HBr¹¹⁷ (see Scheme 214, path a), SnBr₄²⁹⁸ (see Scheme 214, path b), and AgBr²⁸⁰ (see Scheme 214, path c) (method i). A more efficient approach involves the conversion of phenylsilane with hydrogen bromide and catalytic amounts of AlBr₃ (see Scheme 214, path d) (method ii).^{281,299}

As already shown in the section Siloxanes, H₃SiBr is also formed at the reaction of O(SiH₃)₂ with PBr₃ (see Scheme 146, path a).



Scheme 211 Synthesis of chlorodisilanes using N(SiMe₃)₂ (path a) and N(SiMe₂Ph)₂ (path b) as protecting groups. No reported yields of ClH₂Si–SiH₂Cl.

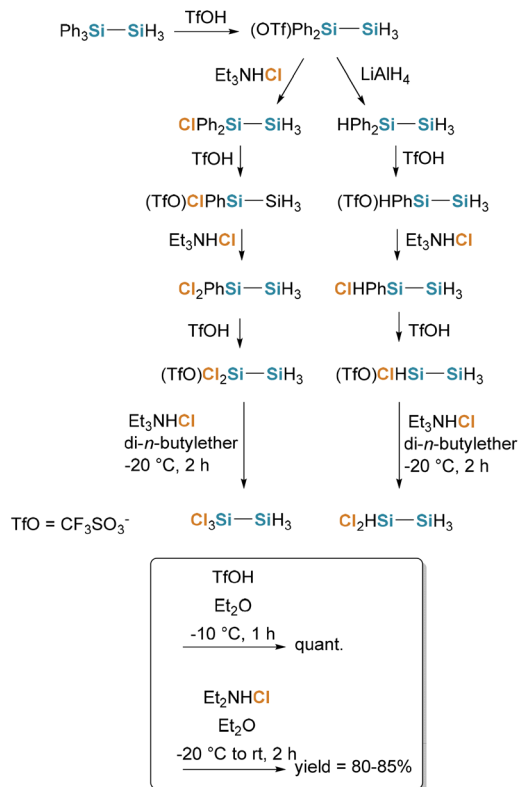


Scheme 212 Synthesis of chlorooligosilanes via dearylation.

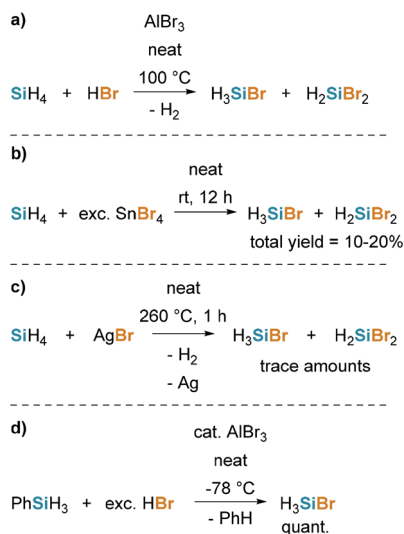
Similar to the preparation of chlorooligohydrogermanes, different bromooligohydrosilanes can be generated through the bromination of oligohydrosilanes (method i) using reagents like BBr₃^{271,272} (see Scheme 215, path a) HBr^{117,286} (see Scheme 215, path b), SnBr₄²⁹⁸ (see Scheme 215, path c), AgBr²⁸⁰ and Br₂^{288,300} (see Scheme 215, path d). These transformations typically proceed through non-selective halogen exchange leading to complex mixtures of mono- and oligobrominated silanes rather than single, well-defined products.

Also similar to the synthesis of chlorohydrosilanes, is the possibility of electrophilic cleavage of silicon–aryl bonds with HBr (method ii) (see Scheme 216).^{274,294,301}



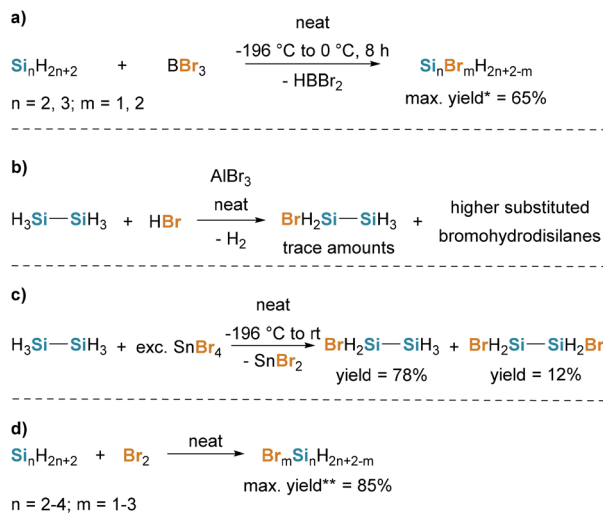


Scheme 213 Multi-step synthesis of chlorodisilanes by Uhlig *et al.*

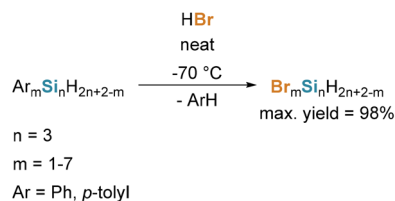


Scheme 214 Different methods for the synthesis of BrSiH_3 (path a–d). No reported yields for the bromination of SiH_4 with HBr (path a).

Iodohydrosilanes. Iodohydrosilanes have attracted increasing interest as highly reactive silicon precursors for CVD and LPD processes, owing to the weak Si–I bond, which enables low-temperature decomposition and efficient surface activation. Early synthetic and reactivity studies demonstrated that iodohydrosilanes exhibit significantly higher reactivity than their



Scheme 215 Methods for the synthesis of bromooligosilanes (path a–d). *Yield was not isolated. **Yield of the product mixture.



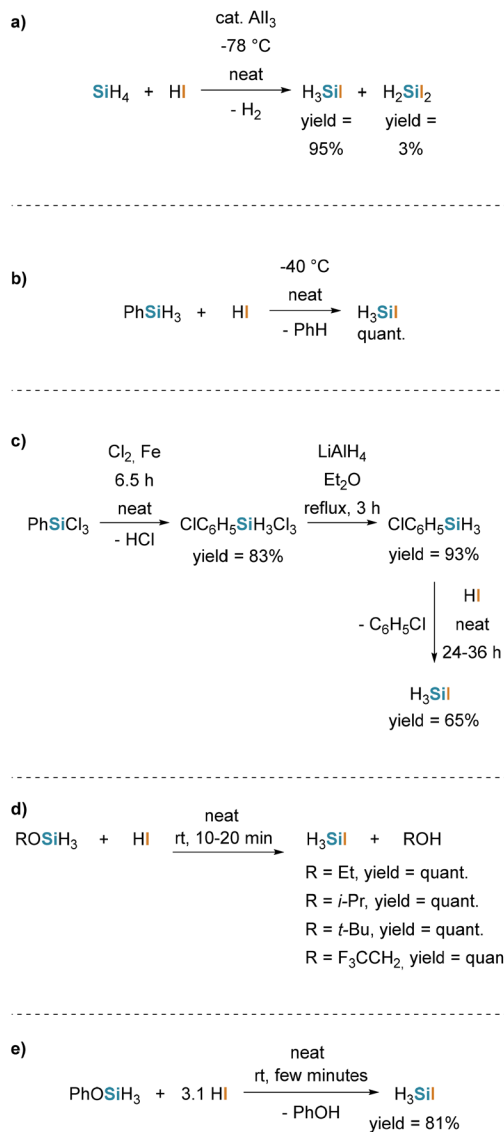
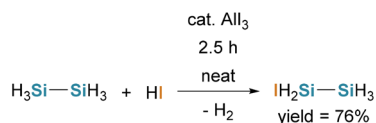
Scheme 216 Synthesis of bromooligosilanes *via* dearylation.

chloro- and bromo-analogues, making them particularly attractive for low-energy silicon deposition.¹⁶⁷ More recent work has highlighted their potential as single-source precursors, although their practical use remains limited by thermal instability and challenging handling properties.³⁰²

Maddock and co-workers first reported the preparation of monoiodosilane in 1939, describing its formation *via* the reaction of monosilane and hydrogen iodide in the presence of catalytic amounts of AlI_3 (method i) (Scheme 217, path a).^{167,303} An alternative efficient method towards monoiodosilane employs phenylsilane as the starting material (method ii) (Scheme 217, path b).^{281,304} Ward *et al.* further demonstrated that H_3SiI can be generated *via* the chlorination of phenylchlorosilane and subsequent hydration to form the chlorophenylsilane, which upon treatment with hydrogen iodide afforded monoiodosilane in yields of up to 65% (Scheme 217, path c).²⁹⁹ Across a range of silyl ethers, treatment with HI afforded H_3SiI in quantitative yield and the corresponding alcohol (ROH) as byproduct (Scheme 217, path d).²³⁸ It is also possible to convert PhOSiH_3 to H_3SiI by treatment with HI (Scheme 217, path e).²³⁶

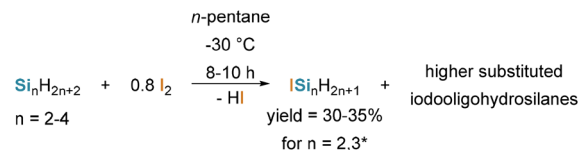
In 1960, Ward and MacDiamid extended these studies to iodohydrooligosilanes.²³¹ In their work, disilane was reacted with hydrogen iodide in the presence of catalytic amounts alu-



Scheme 217 Methods for the synthesis of ISiH_3 (path a–e).Scheme 218 Iodination of disilane with HI yielding in $\text{IH}_2\text{Si}-\text{SiH}_3$.

minium iodide, leading to the formation of iododisilane $\text{IH}_2\text{Si}-\text{SiH}_3$ (method i) (see Scheme 218).

Approximately a decade later Fehér *et al.* carried out intense studies to the synthesis of different iodoalcoholosilanes following an alternative approach applied to di-, tri- and tetrasilane, in which iodide serves as iodation reagent (see Scheme 219).^{305,306} These reactions consistently produced mixtures of mono- and diiodinated silanes. Nevertheless, individual isomers of iodinated di-, tri-, and tetrasilanes could be separated and identified by gas chromatographic methods.

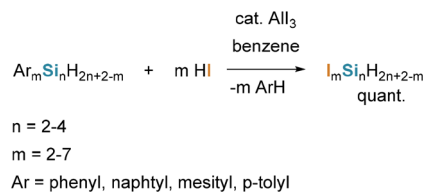
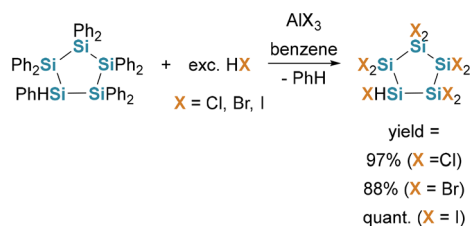
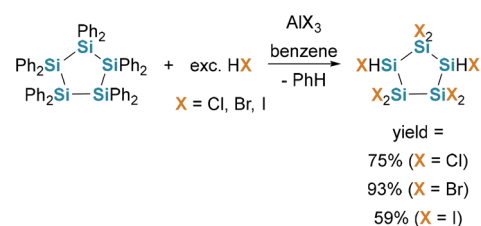
Scheme 219 Reaction of di-, tri- and *n*-tetrasilane with iodide. *Yield of the monoiodotetrasilane was not reported.

Nearly twenty years afterward, Hassler and co-workers reported significant progress in the synthesis of iodoalcoholosilanes. Analogous to strategies established for chloro- and bromohydrosilanes, their work demonstrated that electrophilic cleavage of silicon-aryl bonds with hydrogen iodide enables the selective introduction of iodine substituents (see Scheme 220). Using this approach, a broad range of iodoalcoholosilanes was prepared in high efficiency.^{294,307}

Cyclic halohydrosilanes

Nonahalocyclopentasilanes (HSi_5X_9) and octahalocyclopentasilanes (1,3- $\text{H}_2\text{Si}_5\text{X}_8$) (X = Cl, Br, I) can be prepared *via* dephenylation of the corresponding phenyl-substituted precursors HSi_5Ph_9 and $\text{H}_2\text{Si}_5\text{Ph}_8$ (see Scheme 221).^{35,308}

Partially chlorinated cyclopentasilanes were reported by Roewer and co-workers through the stepwise hydride reduction

Scheme 220 Synthesis of iodoalcoholosilanes *via* dearylation.

Scheme 221 Synthesis of cyclic halohydrosilanes.



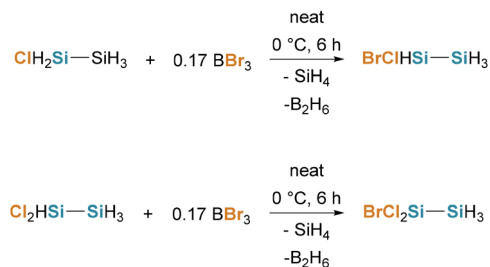
of decachlorocyclopentasilane using Me_3SnH (see Scheme 222). The reaction proceeds without detectable formation of SiHCl moieties. The major product observed was assigned to 1,1,3,3-tetrachlorocyclopentasilane, while 1,1-dihydrooctachlorocyclopentasilane was not detected. Structural assignments were based on ^{29}Si NMR spectroscopic data; the intermediates were not isolated.¹⁰⁷

Stueger *et al.* reported the partial hydrogenation of perchlorinated cyclopentasilane in 2012 in a three-step synthesis (see Scheme 223).²⁹⁰ The final yield of the product (Si_5HCl_9) could not be determined since it could not be separated from cyclopentasilane which was formed as byproduct.

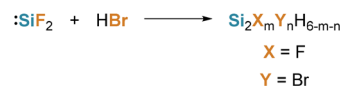
Mixed halohydrosilanes

The bromination of Si-H bonds using BBr_3 was employed to generate chlorobromohydrosilanes. Thus, $\text{ClH}_2\text{Si-SiH}_3$ and $\text{Cl}_2\text{HSi-SiH}_3$ were converted into HBrClSi-SiH_3 and $\text{BrCl}_2\text{Si-SiH}_3$, respectively (see Scheme 224). These products were detected by GC; however, no isolation was reported.²⁷¹

Mixed halohydrosilanes of the general formula $\text{Si}_2\text{X}_m\text{Y}_n\text{H}_{6-m-n}$ ($\text{X} = \text{F}$, $\text{Y} = \text{Br}$) are formed *via* co-condensation of SiF_2 with HBr . Upon warming the reaction mixture to room temperature, its composition changes, although the mixed



Scheme 224 Synthesis of mixed halosilanes; no yields reported.



Scheme 225 Synthesis of mixed halosilanes; no yields reported.

halohydrosilanes $\text{BrF}_2\text{Si-SiF}_2\text{H}$, $\text{F}_3\text{Si-SiF}_2\text{HBr}$ and $\text{F}_3\text{Si-SiHBr}_2$ could be isolated but no yields were reported (see Scheme 225). The compounds $\text{HBrFSi-SiF}_2\text{Br}$ and $\text{HBr}_2\text{Si-SiF}_2\text{Br}$ were identified in the final reaction mixture by ^{19}F NMR spectroscopy, but were not isolated. Subsequent chlorination of $\text{BrF}_2\text{Si-SiF}_2\text{H}$ and $\text{F}_3\text{Si-SiHBr}_2$ with SnCl_4 afforded $\text{F}_3\text{Si-SiHCl}_2$ and $\text{ClF}_2\text{Si-SiHF}_2$. Yields of the isolated products have not been reported.^{270,309}

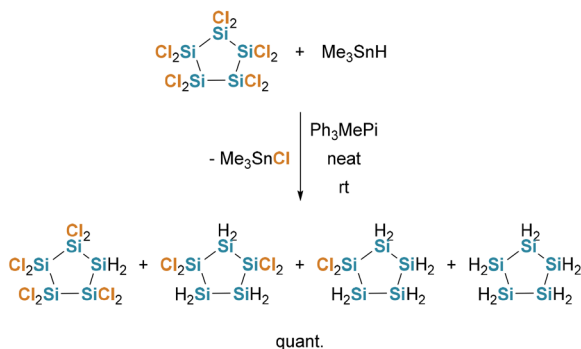
Key physical and chemical properties for the central hydrosilanes

In Table 8 the key physical and chemical properties for the central hydrosilanes are depicted.

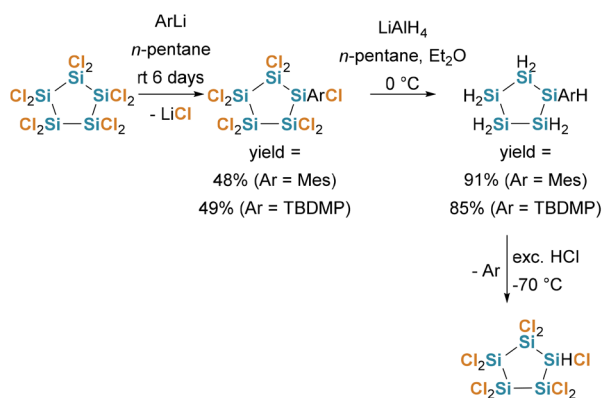
Deposition methods

Silicon (Si) is the second most abundant element in the Earth's crust constituting approximately 28%.³¹⁰ As a semiconductor, silicon plays a crucial part in the electronics industry. Depending on deposition method and process conditions silicon thin films can exhibit monocrystalline, polycrystalline or amorphous structures, which significantly influence the electronic properties and application potential. Monocrystalline silicon (c-Si) possesses a long-range ordered crystal lattice and high charge carrier mobility, making it the preferred material for microelectronic devices. Polycrystalline silicon (poly-Si) consists of crystalline grains separated by grain boundaries, which reduce carrier mobility but allow deposition at lower temperatures, enabling its use in thin film transistors (TFTs) and photovoltaic devices. Amorphous silicon (a-Si) lacks long-range order and exhibits a high density of dangling bonds.³¹¹⁻³¹³ The structural motifs are summarized in Fig. 16.

Early on, a-Si attracted scientific interest as a semiconductor, however, it exhibited significant drawbacks with respect to electrical conductivity. At the beginning of the 1970s, new deposition methods were developed, that enabled



Scheme 222 Synthesis of cyclic chlorohydrosilanes.

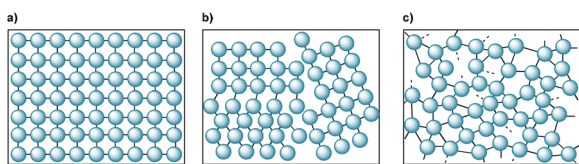


Scheme 223 Synthesis of nonachlorocyclopentasilane by Stueger *et al.* No yield of the final product reported.

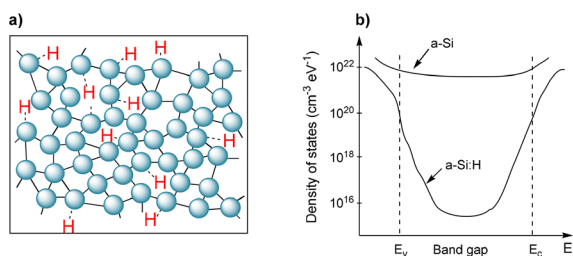


Table 8 Summary of key physical and chemical properties of central hydrosilanes

Silane	m.p. [°C]	b.p. [°C]	Physical/state	Solubility	Safety
SiH ₄	-185	-112	Gas	Slightly in all organic and inorganic solvents	Pyrophoric
Si ₂ H ₆	-133	-15	Gas	All organic and inorganic solvents	Pyrophoric
Si ₃ H ₈	-115	53	Liquid	All organic and inorganic solvents	Pyrophoric
<i>n</i> -Si ₄ H ₁₀	-89.9	108	Liquid	All organic and inorganic solvents	Pyrophoric
iso-Si ₄ H ₁₀	-99.4	102	Liquid	All organic and inorganic solvents	Pyrophoric
<i>n</i> -Si ₅ H ₁₂	-72.2	153	Liquid	All organic and inorganic solvents	Pyrophoric
<i>neo</i> -Si ₅ H ₁₂	-57.8	134	Liquid	All organic and inorganic solvents	Pyrophoric
<i>cyclo</i> -Si ₅ H ₁₀	-10.5	194	Liquid	All organic and inorganic solvents	Pyrophoric
<i>n</i> -Si ₆ H ₁₄	-44.7	194	Liquid	All organic and inorganic solvents	Pyrophoric
<i>cyclo</i> -Si ₆ H ₁₂	16.5	226	Liquid	All organic and inorganic solvents	Pyrophoric
<i>n</i> -Si ₇ H ₁₆	-30.1	227	Liquid	All organic and inorganic solvents	Pyrophoric
Si ₈ H ₁₈	28	<i>x</i>	Oil	All organic and inorganic solvents	Pyrophoric
N(SiH ₃) ₃	-106	52	Liquid	All organic and inorganic solvents	Pyrophoric
N(SiH ₂ SiH ₃) ₃	-97	176	Liquid	All organic and inorganic solvents	Pyrophoric
Et ₂ NSiH ₂ SiH ₂ NET ₂	<i>x</i>	23/0.05 Torr	Liquid	All organic and inorganic solvents	Pyrophoric
SiH ₃ SiH(NEt ₂) ₂	<i>x</i>	23/0.2 Torr	Liquid	All organic and inorganic solvents	Pyrophoric
iPr ₂ NSiH ₂ SiH ₂ NiPr ₂	<i>x</i>	68/0.05 Torr	Liquid	All organic and inorganic solvents	Pyrophoric
H ₃ SiPH ₂	<135	12.7	Gas	All organic and inorganic solvents	Pyrophoric, toxic
P(SiH ₃) ₃	-73	114	Liquid	All organic and inorganic solvents	Pyrophoric, toxic
O(SiH ₃) ₂	-144	-15.2	Gas	All organic and inorganic solvents	Not pyrophoric
S(SiH ₃) ₂	-70.0	58.8	Liquid	All organic and inorganic solvents	Pyrophoric, toxic
Se(SiH ₃) ₂	-68.0	85.2	Liquid	All organic and inorganic solvents	Toxic
Te(SiH ₃) ₂	<i>x</i>	49/50 Torr	Liquid	All organic and inorganic solvents	Toxic

**Fig. 16** Structural motifs of (a) monocrystalline silicon, (b) polycrystalline silicon and (c) amorphous silicon. Dangling bonds marked as dotted line.³¹⁴

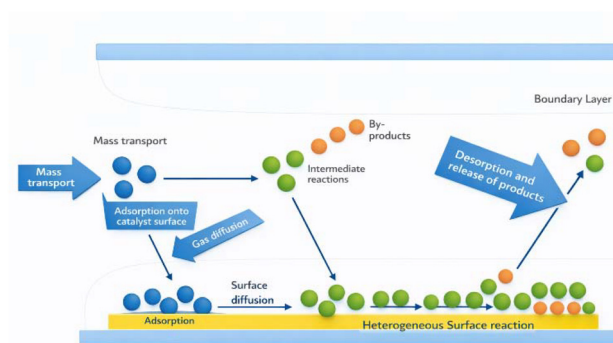
the preparation of amorphous silicon thin-films with improved electronic properties through the incorporating of hydrogen, resulting in hydrogenated amorphous silicon (a-Si:H).³¹⁵ As shown in Fig. 17, passivation of dangling bonds with hydrogen leads to a drastic reduction in defect density, thereby improving conductivity and carrier mobility. Furthermore, effective p- and n-type doping of a-Si:H can be achieved by incorporating appropriate dopant species, such as diborane or phosphine, during deposition, as dopant atoms are no longer compensated by dangling bond defects.³¹⁶

**Fig. 17** (a) Schematic passivation of dangling bonds by hydrogen and (b) schematic illustration of density of states in a-Si and a-Si:H. Graphic adapted from Vora.³¹⁷

Since then, several different deposition techniques have been employed to produce silicon thin films. These silicon thin films have a wide range of applications, including thin film transistors, flexible large area displays, and photovoltaics.^{318,319}

Chemical vapor deposition

Chemical vapor deposition describes the deposition of a solid component on the surface of a substrate from the vapor phase by means of a chemical reaction. The term was first introduced by J. M. Blocher in 1960 to distinguish the process from other deposition methods, that do not involve chemical reactions such as sputtering.³²⁰ During the CVD process, gaseous reactant species are supplied and transported into a reaction chamber, as schematically illustrated in Fig. 18. Upon entering the reactor, the reactant gases are conveyed toward the sub-

**Fig. 18** Schematic illustration of the CVD process. Graphic adapted from Sun et al.³²³ and Katsui et al.³²²

strate by mass transport and may either diffuse directly through the boundary layer to adsorb onto the heated substrate surface or participate in gas-phase reactions, forming intermediate species and gaseous byproducts. These intermediates can subsequently reach the substrate by diffusion and adsorption. On the substrate surface, adsorbed species undergo surface diffusion and heterogeneous chemical reactions, ultimately leading to thin-film growth. Any unreacted gaseous precursors or byproducts are subsequently desorbed from the surface and removed from the chamber in the gas phase.^{312,320–323}

A variety of CVD processes and techniques exist, including thermal CVD (TCVD), plasma-enhanced CVD (PECVD), photo-assisted CVD (PACVD), and hot-wire CVD (HWCVD). Depending on the deposition conditions such as temperature, pressure, and plasma environment, CVD can yield silicon films with different microstructures, including amorphous, microcrystalline, polycrystalline, or epitaxial silicon. The various CVD techniques therefore differ not only in deposition rate and defect concentration but also in the structural properties of the resulting films. A special form of CVD is atomic layer epitaxy (ALE), which enables the growth of monoatomic layers on a substrate surface. In the following section, these different methods are described in more detail.³¹⁵

Thermal chemical vapor deposition

The most common sub-technique of CVD is the thermal CVD. In this process, thermal energy is used to activate the chemical reactions. The required energy can be supplied by several different methods, such as radio-frequency heating, thermal radiation or resistance heating. A typical reactor configuration for TCVD, including gas delivery, substrate heating, and exhaust, is schematically illustrated in Fig. 19.

The industrial implementation of silicon chemical vapor deposition emerged in the early 1960s at Bell Telephone Laboratories, where Theuerer demonstrated controlled epitaxial growth of single-crystalline silicon *via* hydrogen reduction of SiCl_4 .³²⁵ This chlorosilane-based approach enabled precise control over film thickness, doping, and conductivity type, establishing CVD as a technologically viable route for device-grade epitaxial layers. However, these processes required elev-

ated substrate temperatures typically exceeding 1100 °C and involved kinetically demanding Si–Cl bond cleavage with concomitant HCl elimination. These limitations motivated the exploration of hydrosilanes as thermodynamically more labile alternatives for thermal silicon deposition. Lewis and co-workers demonstrated that monosilane undergoes efficient thermal decomposition to silicon and hydrogen, enabling high-purity silicon deposition at temperatures substantially lower than those required for chlorosilane reduction.³²⁶ Subsequent kinetic studies by Joyce and Bradley revealed two distinct growth regimes during silane-based epitaxy: a transport-limited regime above ~1100 °C and a reaction-controlled regime at lower temperatures. Together, these studies established silane as a kinetically tuneable and technologically viable precursor for thermal silicon CVD. Further experimental and kinetic studies have demonstrated that the initial step of silane pyrolysis is most likely the formation of highly reactive silylene species ($:\text{SiH}_2$), accompanied by the release of molecular hydrogen as illustrated in Scheme 226. These intermediates readily insert into Si–H bonds of silanes, leading to the formation of higher polysilanes and initiating silicon hydride cluster growth. Subsequent dehydrogenation and rearrangement reactions generate unsaturated intermediates, including silenes and additional silylenes, which further propagate the reaction network. With increasing cluster size, intramolecular reactions can promote ring formation, yielding cyclic silicon hydrides that represent important intermediates in the early stages of silicon cluster and particle formation during silane pyrolysis. Depending on the reaction conditions, particularly temperature, pressure, and residence time, these species either contribute to heterogeneous film growth on heated surfaces or undergo homogeneous reactions leading to particle and powder formation in the gas phase. While the general mechanistic framework of silane pyrolysis is well established, the detailed reaction network remains highly complex and

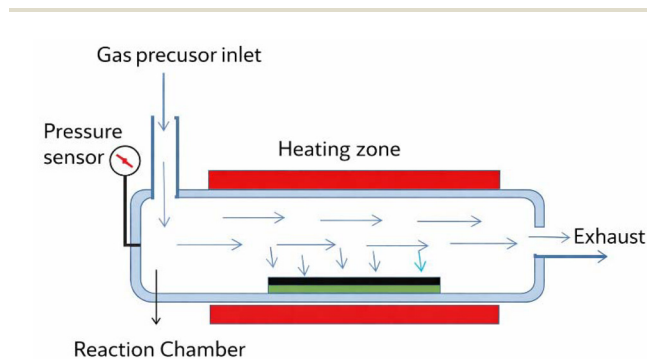
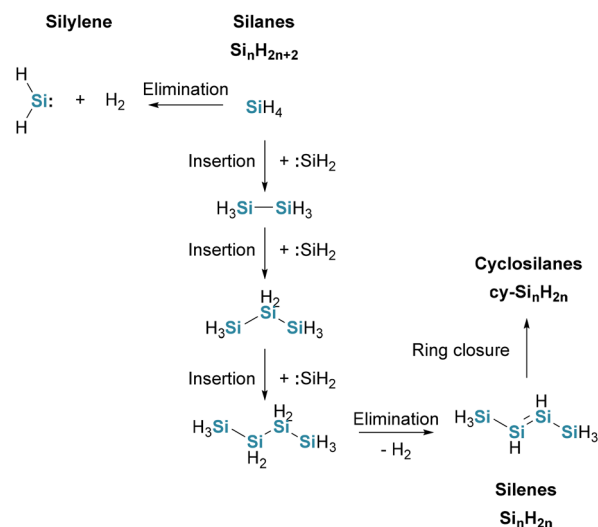


Fig. 19 Scheme of a typical reactor configuration for TCVD. Graphic adapted from Nnadozie *et al.*³²⁴



Scheme 226 Simplified mechanism of silane pyrolysis illustrating the formation of higher silanes and cyclic silicon hydrides.^{327,328}



continues to be investigated through experimental and theoretical studies.^{327–329}

Based on the operating pressure, TCVD can be further subdivided into atmospheric pressure CVD (APCVD), low-pressure CVD (LPCVD) and ultrahigh vacuum CVD (UHVCVD). In 1997, Sturm *et al.* demonstrated low-temperature LPCVD growth of β -SiC on Si using methylsilane as a single-source precursor, yielding polycrystalline, device-compatible SiC films.³³⁰ Two years later, Madaura *et al.* reported for the first time the APCVD of SiC films on a Si substrate using trimethylsilane as a single source precursor. Although trimethylsilane contains only a single Si–H bond and therefore falls outside the scope of classical hydrosilanes discussed in this review, this study is noteworthy as an early example of silicon deposition chemistry employing molecular silane precursors. The SEM microphotographs of the SiC/Si interface are shown in Fig. 20.³³¹

Hazbun *et al.* investigated the use of tetrasilane (Si_4H_{10}) as a precursor for ultra-high-vacuum CVD of silicon epitaxial layers. They demonstrated that tetrasilane enables significantly higher growth rates than monosilane and allows crystalline silicon deposition at temperatures as low as 400 °C, making it suitable for low-temperature epitaxy.³³² Furthermore, Byeon *et al.* investigated the epitaxial growth of Si and SiGe using high-order silanes such as disilane, trisilane, and tetrasilane under UHVCVD and LPCVD conditions without a carrier gas. They showed that higher-order silanes enable silicon epitaxy at reduced temperatures, with trisilane and tetrasilane providing significantly higher growth rates, while disilane yielded the highest crystal quality of the deposited films.³³³ Halogenated hydrosilanes were likewise employed as silicon precursors for both oxide and carbide thin films. In high-temperature thermal CVD, silicon tetrachloride in combination with propane enabled the growth of epitaxial SiC layers, where chlorine-containing species suppress gas-phase nucleation and improve stoichiometric control of Si:C ratios.³³⁴ In a related context, Sneh *et al.* reported atomic-layer controlled growth of SiO_2 using a binary reaction sequence with SiCl_4 and H_2O .³³⁵ Nitrogen-functionalized hydrosilanes subsequently

emerged as important precursors for the deposition of silicon nitride (Si_3N_4) thin films. Gumphier *et al.* demonstrated LPCVD of Si_3N_4 from di(*t*-butylamino)silane (BTBAS) and NH_3 at 550–600 °C, producing high-quality nitride films suitable for microelectronic applications.³³⁶ The incorporation of preformed Si–N bonds in these precursors enhances surface reactivity while avoiding corrosive halide byproducts, thereby improving film purity and conformality in advanced deposition schemes.³³⁷

Silylphosphanes and related phosphinosilanes were explored primarily in patent literature as single-source Si–P precursors for *in situ* phosphorus doping during silicon CVD. Although conceptually attractive as potential alternatives to PH_3 , limited thermal robustness and the maturity of established PH_3 -based processes curtailed their broader implementation.³³⁸ Silylgermanes containing preformed Si–Ge bonds were systematically developed as molecular single-source precursors for SiGe thin-film growth. Kouvetakis and co-workers first established the complete hydride series $(\text{H}_3\text{Ge})_x\text{SiH}_{4-x}$ ($x = 1-4$), including silylgermane H_3GeSiH_3 and tetrasilylgermane $\text{Ge}(\text{SiH}_3)_4$, and demonstrated their application in low-pressure deposition of epitaxial $\text{Si}_{1-x}\text{Ge}_x$ layers at 300–450 °C. Thermal activation proceeds *via* Si–H and Ge–H bond cleavage with H_2 elimination while preserving the intrinsic Si:Ge stoichiometry encoded in the precursor, enabling compositionally controlled alloy growth without separate silane and germane feeds. This molecular design strategy facilitates the preparation of a new class of Si-based semiconductors with Ge-rich stoichiometry. Fig. 21 shows a X-ray transmission electron microscopy (XTEM) image of a SiGe_2 layer on a Si substrate.¹²⁷

More recently, Wagner and co-workers introduced mixed-substituted Si–Ge hydrides such as $\text{H}_3\text{SiR}_2\text{GeSiH}_3$ ($\text{R} = \text{Ph}, n\text{-Bu}$), synthesized *via* Si_2Cl_6 -mediated coupling and subsequent hydride formation, and demonstrated their conversion by low-pressure CVD into predominantly amorphous $\text{Si}_{1-x}\text{Ge}_x$ coatings with predefined Si:Ge ratios and reduced pyrophoricity compared to purely hydridic systems.¹²⁸

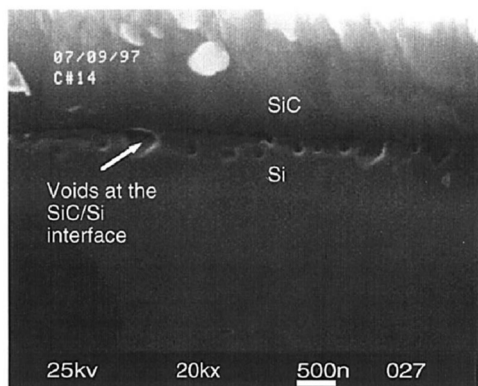


Fig. 20 Microphotographs of the SiC/Si interface as seen by cross-sectional SEM adapted from Madapura *et al.*³³¹ With permission from ECS – The Electrochemical Society, © 1999.

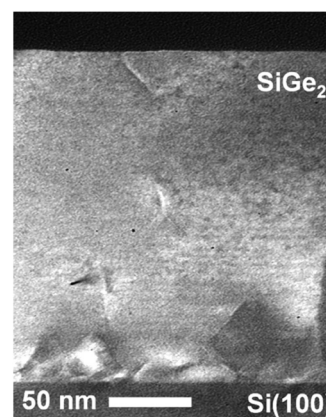


Fig. 21 XTEM micrograph of a SiGe_2 layer grown on Si(100) adapted from Kouvetakis *et al.*¹²⁷ With permission from American Chemical Society, © 2005.



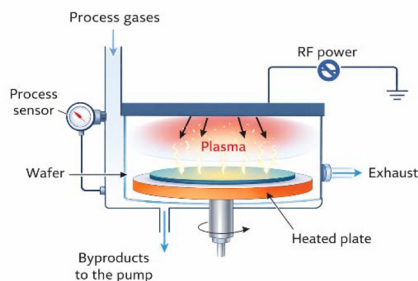


Fig. 24 Schematic illustration of a plasma-enhanced chemical vapor deposition (PECVD) reactor. Graphic adapted from Verma *et al.*³⁵³ and altered with the help of AI. With permission from Springer Nature Singapore Pte Ltd., © 2023.

A key advantage of PACVD is the absence of plasma, which eliminates ion-induced damage to both the substrate and the growing film. Furthermore, in contrast to TCVD, which relies on pyrolytic mechanisms and requires high substrate temperatures, PACVD enables deposition at significantly lower temperatures, in some cases at room temperature. As a result, the choice of substrate material is not restricted by thermal stability. PACVD also has limitations, including the requirement that precursor molecules exhibit sufficient absorption within the emission spectrum of the light source, as well as relatively low deposition rates.^{339,354}

PACVD is often discussed together with laser-assisted CVD (LACVD), also known as laser chemical CVD, and the two processes are not always strictly distinguished terminologically in literature, as both rely on photonic activation. The crucial difference, however, lies in the method of energy input. In contrast to PACVD, LACVD uses coherent, high-intensity laser radiation. LACVD can generate very high local energy densities and induce both photolytic and locally pyrolytic processes, for example, through targeted heating of the substrate surface. Laser-CVD is therefore particularly suitable for locally confined deposition or structuring processes.^{220,339,357} A typical schematic of the LACVD process is shown in Fig. 25.

Hot-wire chemical vapor deposition

Hot-wire chemical vapor deposition (HWCVD), also known as catalytic CVD (Cat-CVD), is a plasma-free CVD process in

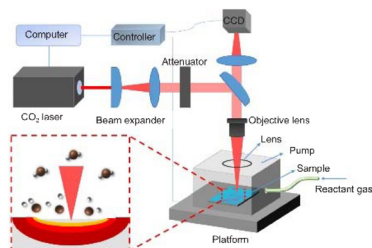


Fig. 25 Schematic illustration of a LACVD reactor. With permission from the Institute of Optics and Electronics, Chinese Academy of Science³⁵⁸ © 2022.

which the decomposition of precursor gases occurs on a highly heated metal filament. Tungsten or tantalum are typically used as the filament material, which can be heated to temperatures of approximately 1400 to 2100 °C. At the surface of the hot wire, gaseous silane can be efficiently dissociated, with an almost complete separation into its atomic components. The reactive species generated subsequently undergo further reactions with SiH₄ in the gas phase, forming various secondary precursors that diffuse to the substrate surface and contribute to thin-film deposition.^{359,360} The following Fig. 26 gives a schematic view of a HWCVD reactor.

A characteristic feature of HWCVD is the spatial separation of precursor decomposition and layer growth. Since the generation of reactive species occurs exclusively on the filament, the process is often referred to as a remote decomposition method. The temperatures of the filament and substrate can be adjusted independently, enabling deposition at comparatively low substrate temperatures while simultaneously achieving high deposition rates.

The basic principle of HWCVD was first published and patented in 1979 by Wiesmann *et al.* under the name thermal vapor deposition.³⁶¹ In the mid-1980s, Matsumura *et al.* first demonstrated the deposition of amorphous silicon using this method and introduced the term catalytic CVD.³⁶² Independently, Doyle *et al.* described a comparable concept under the name evaporative surface decomposition (ESD).³⁶³

A significant milestone was achieved in 1991 with the work of Mahan *et al.*, who demonstrated that amorphous silicon layers deposited using HWCVD can exhibit higher material quality than comparable films produced by PECVD.³⁶⁴ The high quality of the deposited layers is attributed to the efficient decomposition of the precursor gases at filament temperatures above approximately 1500 °C. Typical deposition rates for amorphous silicon range from 10 to 50 Å s⁻¹, significantly exceeding those of conventional RF-PECVD processes.

Due to the absence of a plasma, ion-induced structural damage to the growing layer, that can be caused by ion bombardment or high-energy radiation, is largely avoided. The

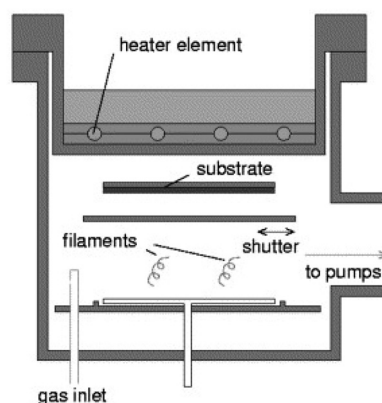


Fig. 26 Illustration of a schematic HWCVD reactor adapted from Schropp.³⁶⁰ With permission from ECS – The Electrochemical Society, © 2009.



term Cat-CVD refers to the catalytic effect of the hot wire in the dissociation of the precursor gases, although the filament is not an ideal catalyst in the strict chemical sense, as it undergoes aging and erosion during the process.³⁶⁵ In the literature, the term HWCVD is predominantly used in physical and photovoltaic contexts, while Cat-CVD is particularly common in chemical research and Japanese literature. Current research is investigating, among other things, the application of HWCVD for the production of TFTs and thin-film solar cells.³⁶⁰

Atomic layer deposition

Atomic layer deposition is a thin film deposition technique, that can be classified as a special modification of CVD. In the literature, it is also referred to as atomic layer epitaxy or Atomic Layer Chemical Vapor Deposition (ALCVD). A key characteristic of ALD is the deposition of inorganic thin films with thicknesses down to a range of single monolayers, which is enabled by sequential, self-limiting surface reactions. As a result, highly homogeneous and conformal layers with excellent thickness control can be deposited.^{131,366}

In ALD, gaseous precursors are introduced into the reactor in a strictly sequential manner. Each precursor reacts exclusively with the available reactive sites on the substrate surface until a saturated adsorption level is reached. The reactor is purged with inert gas between the individual precursor pulses to remove excess precursor molecules and volatile byproducts. This procedure effectively suppresses gas-phase reactions, such that the film growth is governed almost entirely by surface reactions.^{133,367} The scheme of a sequential ALD cycle is shown in Fig. 27. Hirose *et al.* demonstrated the use of monosilane for room temperature ALD.³⁶⁸ Matsunami *et al.* established epitaxial growth of β -SiC (3C-SiC) on Si substrates by reacting SiH_4 with hydrocarbons such as propane at temperatures above 1000 °C, enabling crystalline SiC layers for electronic applications and demonstrating *in situ* doping with nitrogen donors and aluminium or boron acceptors.³⁶⁹ Halogenated hydrosilanes were also employed for SiC epitaxy:

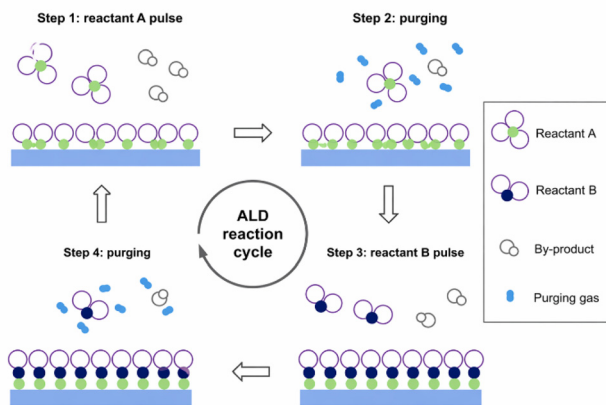


Fig. 27 Scheme of a sequential ALD cycle adapted from George.¹³¹ With permission from American Chemical Society, © 2009.

Pedersen *et al.* employed methyltrichlorosilane in a hot-wall CVD reactor to obtain high-quality 4H-SiC layers.³⁷⁰ Additional chlorinated silanes, including trichlorosilane, dichlorosilane, and hexachlorodisilane (Si_2Cl_6), have likewise been utilized for high-quality SiC epitaxial growth.³⁷¹

Nitrogen-functionalized hydrosilanes became important precursors for the deposition of silicon dioxide (SiO_2) thin films. Bis(dimethylamino)silane (BDMAS) was introduced for atomic layer deposition of SiO_2 with H_2O ³³⁷ or O_3 ³⁷² as oxidants, where ligand-exchange reactions with surface OH groups followed by ozone or oxygen plasma oxidation yield SiO_2 .³⁷² Furthermore Faraz *et al.* reported the deposition of silicon nitride layer through plasma-enhanced atomic layer deposition of di(*sec*-butylamino)silane (DSBAS) on planar and on high aspect ratio 3D trench nanostructures. Fig. 28 shows a TEM image of the layer as-deposited and post wet-etch with dilute hydrofluoric acid.³⁷³

In contrast to hydrosilanes, oxygen-functionalized silicon precursors such as tetraethyl orthosilicate (TEOS, $\text{Si}(\text{OEt})_4$) are widely used for the deposition of SiO_2 thin films in LPCVD, PECVD, and sub-atmospheric CVD processes.³⁷⁴

Liquid phase deposition

A viable alternative to established vapour-based deposition techniques is solution-based processing of silicon, commonly referred to as liquid phase deposition. In contrast to CVD methods, which require pyrophoric precursor gases, elaborate vacuum or plasma infrastructure, and often elevated deposition temperatures, LPD can generally be carried out at lower temperatures and under atmospheric pressure. This reduces equipment complexity as well as operating costs. Furthermore, LPD is compatible with flexible, large-area, and temperature-sensitive substrates and can enable higher throughput, particularly when combined with coating or printing techniques. Such approaches also facilitate direct patterning of materials and may reduce the number of required processing steps. Consequently, LPD is considered a promising route for applications in printable electronics, including large-area flexible displays, thin-film solar cells, TFTs and silicon-based anode

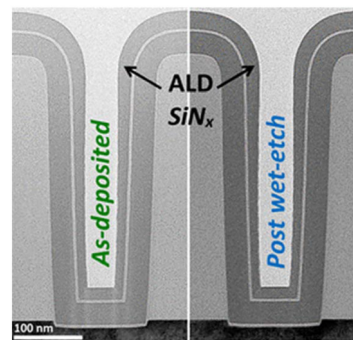


Fig. 28 TEM image of the silicon nitride layer as-deposited (left) and post wet-etch with dilute hydrofluoric acid (right) adapted from Faraz *et al.*³⁷³ With permission from American Chemical Society, © 2017.



materials in lithium-ion batteries. The following section discusses the underlying chemical mechanisms of hydrosilane-based LPD and summarizes the key contributions in this field.^{19,375,376}

The conceptual foundations of hydrosilane-based liquid processing date back to the late 1980s. West and Wolff³⁷⁷ as well as Miller and Michl³⁷⁸ demonstrated that organopolysilanes can be deposited as thin films and subsequently converted into silicon-rich amorphous networks by thermal or photochemical treatment, thereby establishing the processing and photochemistry toolkit for later hydrosilanes routes. However, true hydrosilanes themselves were only mentioned in passing in these studies, and a dedicated liquid-phase deposition strategy based explicitly on hydrosilane precursors had not been established. A decisive step toward practical implementation was achieved by Shimoda *et al.* in 2006,¹⁹ who established $\text{cy-Si}_5\text{H}_{10}$ as a molecular precursor for solution-processed silicon films. $\text{Cy-Si}_5\text{H}_{10}$ was selected due to its favourable properties: it exhibits comparatively high stability and good availability making it suitable for handling and processing under inert conditions, and also exhibiting a high photo-reactivity upon irradiation with ultraviolet light. In Shimoda's LPD approach $\text{cy-Si}_5\text{H}_{10}$ is first irradiated with UV light with a wavelength of 365 nm leading to a ring-opening polymerization and the formation of polydihydrosilane. The resulting polyhydrosilane can be dissolved in organic solvents to yield a processable liquid silicon material, often referred to as "silicon ink". The silicon ink is deposited by spin-coating on a substrate forming a uniform precursor. Subsequently thermal treatment induces the conversion of the polysilane network into a *a-Si* film. During initial heating, volatile components such as the solvent and $\text{cy-Si}_5\text{H}_{10}$ evaporate. At a temperature below approximately 280 °C cleavage of Si-Si bonds begins, leading to a release of SiH_2 and SiH_3 species. Above a temperature of around 300 °C the Si-H bonds break resulting in the formation of the amorphous silicon film.^{19,376,379-381} Fig. 29 illustrates the colour changes associated with variations in the chemical composition of the thin film at different annealing temperatures.

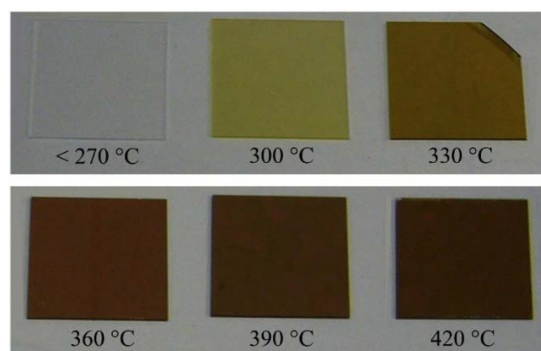


Fig. 29 Photographic image of the solution-processed polysilane films coated on quartz glass adapted from Trifunovic *et al.*³⁸¹ With permission from American Institute of Physics, © 2015.

The material can subsequently be further processed by additional thermal treatment or laser annealing to obtain polycrystalline silicon. Fig. 30 depicts a scheme for the solution-based formation of amorphous and polycrystalline silicon films.

In comparison to *a-Si* thin films formed through PECVD, the LPD produced films show a significantly lower mobility which is connected to a low concentration of hydrogen atoms. Films processed at temperatures below 300 °C exhibit charge carrier mobilities comparable to those obtained by PECVD. However, under these conditions the material can no longer be unambiguously classified as amorphous silicon and shows increased susceptibility to oxidation. Shimoda *et al.* therefore emphasizes the necessity of balancing low processing temperatures with sufficient structural stabilization and oxidation resistance in order to achieve device-relevant film quality.³⁸⁰

Beyond the preparation of intrinsic silicon inks, Shimoda and co-workers also developed n-type and p-type silicon inks by incorporating suitable dopant precursors, such as white phosphorus and decaborane, into the $\text{cy-Si}_5\text{H}_{10}$ -derived system prior to film deposition. During subsequent thermal conversion, the dopant species are incorporated into the forming silicon network. These developments were later summarized under the term "liquid silicon family materials" (LSFMs), describing a materials platform in which $\text{cy-Si}_5\text{H}_{10}$ acts as a common precursor for different silicon-based functional layers. In this concept, intrinsic, n-type, and p-type silicon films as well as device structures such as TFTs and solar cells can be fabricated using entirely liquid-based processing routes.

Subsequent studies expanded the precursor chemistry, the available activation strategies as well as the deposition

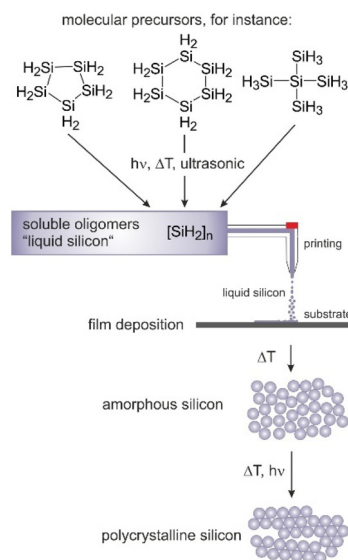


Fig. 30 Scheme for the solution-based formation of amorphous and polycrystalline silicon films adapted from Gerwig *et al.*⁵ With permission from Chemistry – A European Journal published by Wiley-VCH GmbH, © 2024.



methods for hydrosilane-based LPD. Following Shimoda's initial work, $\text{cy-Si}_5\text{H}_{10}$ remained the dominant hydrosilane precursor, and numerous studies focused on refining its processing and activation. In contrast to the spin-coated polysilane ink approach described by Shimoda, Frey *et al.* employed an aerosol-assisted spray deposition technique using neat $\text{cy-Si}_5\text{H}_{10}$ as precursor. The $\text{cy-Si}_5\text{H}_{10}$ was atomized and deposited onto heated substrates under inert atmosphere, while ultraviolet irradiation was applied within the deposition chamber to promote precursor activation. Film formation proceeded primarily *via* thermally assisted decomposition of the liquid precursor during and after deposition, followed by high-temperature annealing (700–950 °C) to obtain polycrystalline silicon.³⁸² Trifunovic *et al.* employed doctor-blade coating of $\text{cy-Si}_5\text{H}_{10}$, followed by ultraviolet curing at 365 nm and subsequent excimer laser at crystallization at 308 nm to obtain poly-Si at a maximum process temperature of 150 °C. In this approach, the solution-deposited precursor was directly transformed into crystalline silicon without requiring intermediate high-temperature annealing above 350 °C or a separate amorphous silicon conversion step. Therefore, this process is suitable for deposition on temperature-sensitive substrates like paper or polymer and facilitating low-cost electronics. Fig. 31 shows a poly Si film fabricated on paper.³⁸¹

In parallel, alternative activation methods for $\text{cy-Si}_5\text{H}_{10}$ were investigated. Cádiz Bedini *et al.* reported on ring-opening polymerisation induced by ultrasonic irradiation at a frequency of 26 kHz. The temperature was maintained below 75 °C, and it was confirmed, that no thermal activation of the precursor occurred under these conditions.

Masuda *et al.* demonstrated that $\text{cy-Si}_5\text{H}_{10}$ -derived liquid silicon can be employed for solution-based silicon patterning using both inkjet printing and nanoimprinting strategies. In both approaches, $\text{cy-Si}_5\text{H}_{10}$ was first photochemically polymerised at 365 nm to yield a processable polysilane precursor. In the inkjet printing approach, the polysilane solution was deposited in a digitally defined, maskless manner onto the substrate. Subsequent thermal conversion at approximately 380–400 °C yielded hydrogenated amorphous silicon, while additional annealing at 1000 °C enabled crystallisation to polycrystalline silicon. The method further allowed the incorporation of p- and n-type dopants directly into the printed structures. Fig. 32 shows a printed silicon pattern on a glass substrate.³⁸³

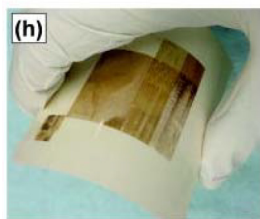


Fig. 31 Poly Si film fabricated on paper adapted from Trifunovic *et al.*³⁸¹ With permission from American Institute of Physics, © 2015.

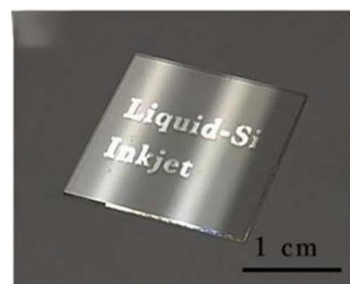


Fig. 32 Inkjet printed silicon pattern on a glass substrate adapted from Masuda *et al.*³⁸³ With permission from Wiley-VCH GmbH, © 2020.

In contrast, the nanoimprinting approach consisted of spin-coating the $\text{cy-Si}_5\text{H}_{10}$ -derived Liq-Si precursor onto the substrate. The deposited film was subsequently pre-cured at 140–220 °C, which initiated partial crosslinking of the polysilane network. Successful pattern replication was achieved only within this temperature window under an applied pressure of 10 MPa. At lower temperatures, insufficient crosslinking prevented stable feature transfer, whereas at higher temperatures the film lost its deformability. Crosslinking proceeds *via* thermally activated 1,2-hydrogen shift reactions, accompanied by the release of SiH_4 and H_2 , leading to progressive solidification of the film. After imprinting and controlled cooling, post-annealing at approximately 380 °C completed the conversion to amorphous silicon. Despite significant volumetric shrinkage during polymer-to-silicon transformation, nanoscale patterns were retained. Fig. 33 shows a nanoimprinted pattern of a-Si.³⁸⁴

These studies demonstrate that $\text{cy-Si}_5\text{H}_{10}$ -derived polysilanes are suitable precursors for lithography-free micro- and nanostructured silicon fabrication.

Gerwig *et al.* investigated the oligomerisation of $\text{cy-Si}_5\text{H}_{10}$ using electron spin resonance (ESR), NMR, and Raman spectroscopy supported by DFT and molecular dynamics simulations. Their results showed that $\text{cy-Si}_5\text{H}_{10}$ does not undergo a classical ring-opening polymerisation. Instead, short-lived silyl radicals are formed, which recombine to generate highly branched hydroooligosilanes. Silylene intermediates were found not to play a significant role. Competing decomposition and

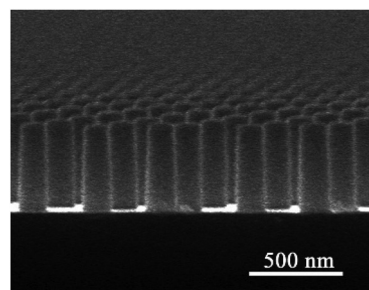


Fig. 33 Nanoimprinted pattern of a-Si adapted from Masuda *et al.*³⁸⁴ With permission from American Chemical Society, © 2016.



disproportionation reactions produce volatile fragments, reducing hydrogen content and overall yield. ESR measurements confirmed the presence of tertiary silyl radicals as reactive intermediates.⁵

The influence of solvent and processing parameters on film formation was further examined. Optimised spin-coating and UV irradiation conditions yielded homogeneous silicon films, which were subsequently passivated by hydrogen plasma. The resulting thin films and TFT devices exhibited performance comparable to PECVD-processed materials.

Shen *et al.* introduced a liquid-source vapor deposition (LVD), where $\text{cy-Si}_5\text{H}_{10}$ thermally decomposes between two parallel hot substrates at atmospheric pressure. In this configuration, a fraction of the precursor is directly converted into amorphous silicon on the substrate surface, while volatile silicon hydride radicals are simultaneously generated. These reactive intermediates diffuse within the confined deposition space and act as secondary growth species, thereby sustaining further film formation. This allows for the formation of denser amorphous silicon layers with reduced oxygen incorporation compared to conventional spin-coated films. The schematic set-up for LVD is shown in Fig. 34.³⁸⁵

However, the demanding synthesis and purification of $\text{cy-Si}_5\text{H}_{10}$ highlight the need to consider alternative precursors such as cyclohexasilane (CHS) and NPS.^{5,376} Iyer *et al.* investigated CHS as an alternative cyclic hydrosilane precursor. The CHS solution was spin-coated onto the substrate under simultaneous UV irradiation to induce ring-opening polymerisation and network formation. Subsequent thermal annealing and excimer laser treatment enabled the transformation of the amorphous intermediate into crystalline silicon. Furthermore, hydrogen plasma exposure was applied to passivate residual defect states and improve the structural and electronic quality of the films.³⁸⁶ The following Fig. 35 shows SEM images of the surface of the thin film after different points in the formation process.

Cadiz Bedini *et al.* demonstrated the preparation of silicon ink from trisilane using ultrasonic irradiation. After subsequent UV irradiation, they used the resulting oligomeric mixture deposit a a-Si-H thin film *via* spin coating. Furthermore, the authors also reported on the deposition of Si nanoparticles from the sonicated silicon ink.³⁸⁷

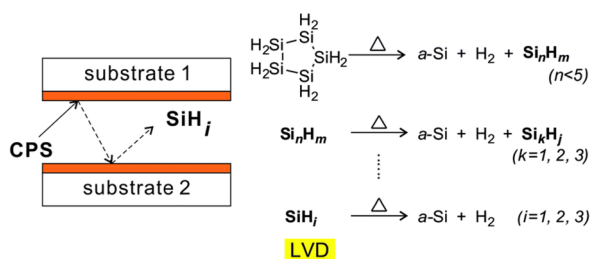


Fig. 34 Schematic set-up of the LVD process with $\text{cy-Si}_5\text{H}_{10}$ as the precursor adapted from Shen *et al.*³⁸⁵ Published by Royal Society of Chemistry under CC-BY 4.0, © 2015.

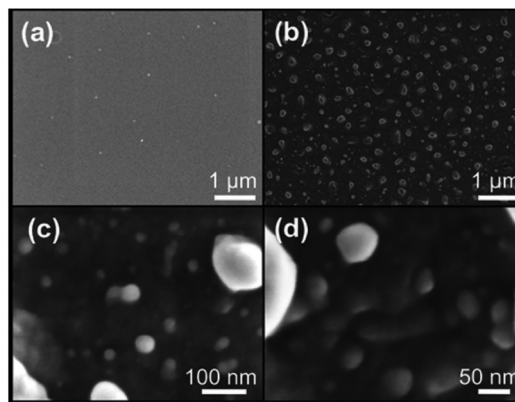


Fig. 35 SEM images of the thin film surface of (a) the amorphous silicon film, (b) the thermally treated silicon film, (c) the laser treated silicon film and (d) the laser treated silicon film at higher magnification adapted from Iyer *et al.*³⁸⁶ With permission from American Chemical Society, © 2012.

Bronger *et al.* were the first to introduce neopentasilane in solution-based silicon processing. Using spin-coating and slot-die coating as deposition techniques, they showed that the branched molecular structure and increased Si-Si bond content of NPS significantly influence the thin film formation. Compared to $\text{cy-Si}_5\text{H}_{10}$, NPS exhibits improved solubility, which results in enhanced film homogeneity and uniformity. In addition, they reported an improved p-type doping efficiency for NPS-derived films relative to $\text{cy-Si}_5\text{H}_{10}$. The electronic performance approached that of comparable PECVD-deposited materials.³¹⁹ The working group of Haase executed further research to determine the usability of liquid silicon ink based on NPS for local n- and p-doping of solar cells.³⁸⁸

Further development explored hydrosilanes beyond simple cyclic or small branched molecules. Haas *et al.* introduced highly branched perhydrosilanes, namely 2,2,3,3-tetra-silyltetra-silane and 2,2,3,3,4,4-hexa-silylpentasilane, which show a reduced pyrophoric character and a bathochromically shifted UV-absorption. After photolysis the obtained oligomeric poly-hydrosilane mixture was spin-coated on glass substrates and thermally treated at 500 °C resulting in a homogeneous a-Si:H layer. Fig. 36 shows a photographic image and an optical micrograph of the solution processed a-Si:H film.²¹

In this context, Christopoulos *et al.* reported the synthesis and structural characterisation of highly branched hydrogen-

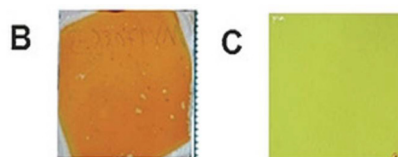


Fig. 36 Photographic image (B) and optical micrograph (C) of the solution processed a-Si:H film adapted from Haas *et al.*²¹ With permission from Wiley-VCH, © 2017.



ated nonasilanes and decasilanes. Although no thin-film deposition experiments were performed, the study provided detailed information on molecular structure, bonding motifs, and stability of higher nuclearity hydrosilanes. Compared to smaller cyclic precursors, these compounds exhibit modified volatility and decomposition behaviour due to their increased silicon content and branching degree. The work therefore contributes to the understanding of structure–property relationships in hydrosilanes and identifies potential candidates for future liquid-phase silicon deposition studies.⁴⁹

The increasing focus on precursor structure is also reflected in patent literature. Several patents disclose synthetic routes toward branched and doped hydrosilanes intended for thin-film deposition applications. These developments address precursor stability, controlled oligomerisation, and reduced pyrophoric character, highlighting the technological relevance of structure-tailored hydrosilanes for liquid-phase silicon processing.³⁸⁹ More recently, precursor-engineered strategies have focused on single-source hydrosilane-based precursors that contain one or more heteroatoms covalently linked to silicon to enable controlled Si–C network formation. Matsuda and co-workers developed a polymeric polydihydrosilane precursor with pendant hexyl groups (PSH), which was deposited by solution-based methods and subsequently pyrolyzed to form an a-SiC coating. Fig. 37 shows a photographic image of PSH films coated on glass substrates and pyrolyzed at different temperatures.³⁹⁰

In a related molecular design approach, Haas and co-workers reported the systematic functionalization of higher silicon hydrides with carbon-containing substituents and demonstrated their application in LPD, where spin-coated precursor films were thermally converted into homogeneous Si/C thin films. Fig. 38 exemplarily shows a picture and a light microscopy image of a thin layer formed from the precursor 1,1,1-trimethyl-2,2-disilyltrisilane.²²

Structure–property–application relationships

Across CVD and LPD, recent work clarifies how structure–property–application relationships are essential to fully exploit the

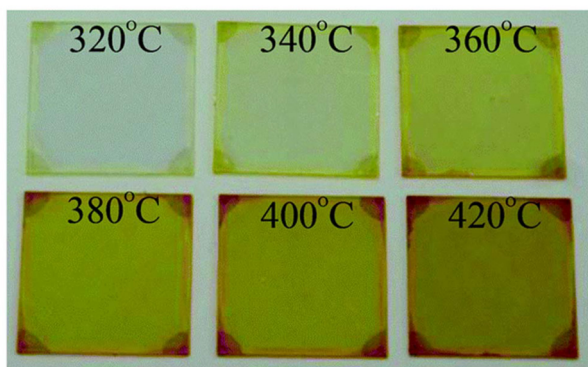


Fig. 37 Photographic image of PSH films coated on glass substrates and pyrolyzed at different temperatures adapted from Masuda *et al.*³⁹⁰ With permission from Royal Society of Chemistry, © 2015.

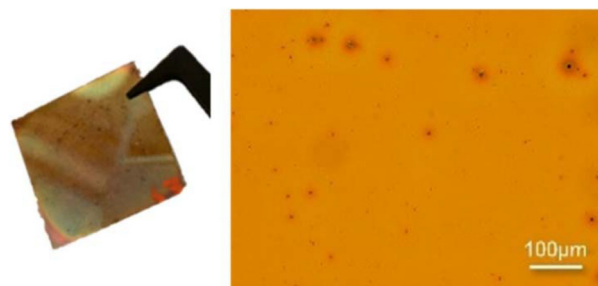


Fig. 38 A picture and a light microscopy image of a thin layer formed from the precursor 1,1,1-trimethyl-2,2-disilyltrisilane on glass adapted from Haas *et al.*²² Published by American Chemical Society under CC-BY 4.0, © 2023.

potential of hydrosilanes in modern materials science. The molecular structure of hydrosilanes governs their activation routes, processing windows, and ultimately film properties. In CVD, high volatility and clean gas-phase decomposition are structure-dependent parameters. Small, volatile hydrides such as SiH₄ or Si₂H₆ dissociate cleanly under plasma, hot-wire, or photon activation and remain advantageous for transport-limited growth formation of high-purity films. This includes hydrosilanes, where the incorporation of a Si–heteroatom bond can enhance surface reactivity, thereby improving the purity and conformality of a film. These attributes are particularly critical, as reduced impurity incorporation minimizes defect-mediated recombination, while improved conformality ensures uniform coverage and consistent electronic properties across complex device architectures. Consequently, both factors directly contribute to enhanced device performance and reliability in both microelectronics and thin-film solar cells.

In LPD, the balance shifts toward solubility, manageable reactivity, and photochemical responsiveness: higher and especially branched hydrosilanes exhibit superior solubility, reduced pyrophoricity, and bathochromically shifted UV absorption, enabling efficient photochemical activation and yielding homogeneous a-Si:H films. These features promote homogeneous film formation and improved control over hydrogen incorporation and network structure in a-Si:H materials. For example, branched hydrosilanes support more uniform coating behavior and facilitate dopant incorporation, while cyclic precursors follow distinct radical-mediated pathways that yield highly branched intermediates, influencing film densification and defect evolution. Thus, precursor structure directly governs the resulting microstructure and optoelectronic properties of the deposited films.

Across both deposition regimes, molecular functionalization (*e.g.*, preformed Si–N, Si–C, or Si–Ge bonds) provides a direct handle to encode composition and doping at the molecular level, linking precursor design directly to device-relevant properties. In the context of thin-film solar cells, such tailored precursors can influence key properties such as crystallinity, electronic structure, and impurity incorporation, thereby



directly affecting device performance. These examples clearly demonstrate that the rational design of hydrosilane precursors-linking molecular structure to decomposition behavior and ultimately to material properties-represents a central strategy for advancing silicon-based technologies encoding film stoichiometry and network chemistry at the molecular level.

Conclusions

Over more than a century of research, the chemistry of hydrosilane has evolved from the early isolation of simple silanes to a sophisticated field spanning synthetic inorganic chemistry, materials science, and semiconductor technology. The development of reliable synthetic methodologies-from classical silicide hydrolysis to chlorosilane reduction, catalytic coupling reactions, and silanide-based strategies-has enabled access to a broad spectrum of linear, branched, cyclic, and cluster-type hydrosilanes. These advances have revealed the remarkable structural diversity of silicon hydrides and highlighted the different reactivity of Si-H and Si-Si bonds compared to their carbon analogues.

A central theme emerging from recent research is the pivotal role of silanide intermediates and Si-H bond activation processes in hydrosilane functionalization. Alkali-metal silanides and related species provide powerful synthetic entry points to a wide range of silicon-element bonds, enabling the preparation of silyl derivatives with elements across the periodic table. In parallel, dehydrogenative coupling reactions have emerged as a particularly powerful methodology for the controlled construction of Si-Si bonds, allowing the transformation of simple monosilanes into higher oligohydrosilanes and polysilane frameworks through catalytic hydrogen elimination. Together with advances in silicon cluster chemistry, including the synthesis of silafullerenes and higher branched hydrosilanes, these developments have significantly expanded the conceptual and structural landscape of molecular silicon hydride chemistry.

Beyond their fundamental chemical interest, hydrosilanes have become indispensable precursors for the preparation of silicon-containing materials and thin films. Chemical vapour deposition represents the most widely employed industrial technique for silicon film formation, where simple hydrosilanes such as monosilane and disilane serve as key feedstocks for the growth of polycrystalline, amorphous, or epitaxial silicon layers used in semiconductor devices and photovoltaic technologies. The controlled thermal or plasma-assisted decomposition of these molecules enables the deposition of high-purity silicon films with precisely tuneable properties. Building on this established technology, recent research has increasingly explored molecularly defined higher hydrosilanes and functionalized derivatives as advanced precursors. In particular, solution-based approaches such as liquid-phase deposition has emerged as attractive complementary strategy that offers advantages in terms of processability, scalability, and compatibility with emerging device architectures.

Outlook and challenges

The chemistry of hydrosilanes has evolved from a largely academic field into a key enabling technology for semiconductor processing and silicon-based materials. As highlighted throughout this review, hydrosilanes represent highly versatile molecular precursors that bridge fundamental silicon chemistry with industrially relevant applications such as chemical vapor deposition (CVD) and liquid phase deposition (LPD).

Building on this progress, future developments are expected to focus on improving synthetic accessibility, scalability, and the targeted functionalization of hydrosilane derivatives.

From an application perspective, hydrosilanes and especially higher oligomeric species offer significant potential as tailored single-source precursors for advanced materials. Their tunable reactivity and decomposition behavior enable precise control over film growth, composition, and doping in semiconductor fabrication. In particular, the development of functionalized hydrosilanes that incorporate heteroatoms directly into the molecular backbone represents a promising strategy toward cleaner and more efficient deposition processes, avoiding the need for co-feeding multiple gaseous precursors.

However, several key challenges currently limit the broader industrial implementation of these compounds. A major bottleneck is the economic feasibility, as the high cost of polysilanes has so far prevented their widespread use in large-scale applications such as solar cell manufacturing. Despite their attractive properties as solution-processable silicon precursors, their synthesis often involves multi-step procedures, low overall yields, and demanding purification protocols, all of which significantly increase production costs.

In addition, synthetic limitations remain a critical issue. For many technologically relevant doping elements, no scalable and robust synthetic routes to suitable hydrosilane-based precursors are currently available. While initial approaches toward Si-B, Si-P, or other heteroatom-functionalized systems have been reported, these methods often suffer from limited selectivity, stability issues, or poor scalability.

This lack of general and efficient synthetic strategies restricts the systematic exploration of doped silicon materials derived from hydrosilanes.

Another challenge lies in the control of reactivity and stability. The intrinsic reactivity of Si-H and Si-Si bonds, while advantageous for materials synthesis, can lead to undesired side reactions such as polymerization or decomposition, complicating handling and processing. This is particularly relevant for higher hydrosilanes, where competing reaction pathways often result in complex product mixtures and reduced selectivity.

Looking forward, addressing these challenges will require integrated efforts in synthesis, mechanistic understanding, and process development. Advances in catalytic methodologies, improved precursor design, and the development of scalable production routes will be essential to unlock the full potential of hydrosilanes in industrial applications. In this



context, the continued interplay between fundamental research and applied process engineering will be crucial for translating laboratory-scale discoveries into viable technologies.

Author contributions

D. G., M. Hx., M. P. and P. V.: were responsible for visualization, data presentation and writing original draft (lead). M. H. was in charge for methodology and conceptualization, review and editing of the manuscript (lead), project administration and funding acquisition.

Conflicts of interest

There are no conflicts to declare.

Data availability

This article is a review and does not report any original data. Therefore, no datasets were generated or analyzed during the current study.

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